User's Manual

16

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R7F0C020M2DFB

User's Manual: Hardware

16-Bit Single-Chip Microcontrollers

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General Precautions in the Handling of Microprocessing Unit and Microcontroller Unit Products

The following usage notes are applicable to all Microprocessing unit and Microcontroller unit products from Renesas. For detailed usage notes on the products covered by this document, refer to the relevant sections of the document as well as any technical updates that have been issued for the products.

1. Precaution against Electrostatic Discharge (ESD)
   A strong electrical field, when exposed to a CMOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop the generation of static electricity as much as possible, and quickly dissipate it when it occurs. Environmental control must be adequate. When it is dry, a humidifier should be used. This is recommended to avoid using insulators that can easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors must be grounded. The operator must also be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions must be taken for printed circuit boards with mounted semiconductor devices.
2. Processing at power-on
   The state of the product is undefined at the time when power is supplied. The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the time when power is supplied. In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the time when power is supplied until the reset process is completed. In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the time when power is supplied until the power reaches the level at which resetting is specified.
3. Input of signal during power-off state
   Do not input signals or an I/O pull-up power supply while the device is powered off. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Follow the guideline for input signal during power-off state as described in your product documentation.
4. Handling of unused pins
   Handle unused pins in accordance with the directions given under handling of unused pins in the manual. The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of the LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible.
5. Clock signals
   After applying a reset, only release the reset line after the operating clock signal becomes stable. When switching the clock signal during program execution, wait until the target clock signal is stabilized. When the clock signal is generated with an external resonator or from an external oscillator during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Additionally, when switching to a clock signal produced with an external resonator or by an external oscillator while program execution is in progress, wait until the target clock signal is stable.
6. Voltage application waveform at input pin
   Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (Max.) and V_{IH} (Min.) due to noise, for example, the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{IL} (Max.) and V_{IH} (Min.).
7. Prohibition of access to reserved addresses
   Access to reserved addresses is prohibited. The reserved addresses are provided for possible future expansion of functions. Do not access these addresses as the correct operation of the LSI is not guaranteed.
8. Differences between products
   Before changing from one product to another, for example to a product with a different part number, confirm that the change will not lead to problems. The characteristics of a microprocessing unit or microcontroller unit products in the same group but having a different part number might differ in terms of internal memory capacity, layout pattern, and other factors, which can affect the ranges of electrical characteristics, such as characteristic values, operating margins, immunity to noise, and amount of radiated noise. When changing to a product with a different part number, implement a system-evaluation test for the given product.

How to Use This Manual

Readers This manual is intended for user engineers who wish to understand the functions of the R7F0C020 and design and develop application systems and programs for these devices.

Purpose This manual is intended to give users an understanding of the functions described in the **Organization** below.

Organization The R7F0C020 manual is separated into three parts: this manual, the hardware edition of the user's manual for the R7F0C003M2DFB and R7F0C004M2DFB, and the software edition (common to the RL78 family).

R7F0C020M2DFB User's Manual (This Manual)	RL78 family User's Manual Software
R7F0C003M2DFB, R7F0C004M2DFB User's Manual	
● Pin functions ● Internal block functions ● Interrupts ● Other on-chip peripheral functions ● Electrical specifications	● CPU functions ● Instruction set ● Explanation of each instruction

How to Read This Manual It is assumed that the readers of this manual have general knowledge of electrical engineering, logic circuits, and microcontrollers.

- To gain a general understanding of functions:
  → Read this manual in the order of the **CONTENTS**. The mark "<R>" shows major revised points. The revised points can be easily searched by copying an "<R>" in the PDF file and specifying it in the "Find what:" field.
- How to interpret the register format:
  → For a bit number enclosed in angle brackets, the bit name is defined as a reserved word in the assembler, and is defined as an sfr variable using the #pragma sfr directive in the compiler.
- To know details of the R7F0C020 Microcontroller instructions:
  → Refer to the separate document **RL78 family User's Manual: Software (R01US0015E)**.

Conventions	Data significance:	Higher digits on the left and lower digits on the right
	Active low representations:	$\overline{\times\times\times}$ (overscore over pin and signal name)
	Note:	Footnote for item marked with **Note** in the text
	Caution:	Information requiring particular attention
	Remark:	Supplementary information
	Numerical representations:	Binary ···×××× or ××××B
		Decimal ···××××
		Hexadecimal ···××××H

Related Documents The related documents indicated in this publication may include preliminary versions. However, preliminary versions are not marked as such.

Documents Related to Devices

Document Name	Document No.
R7F0C020M2DFB User's Manual: Hardware	This manual
R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware	R01UH0393E
RL78 family User's Manual: Software	R01US0015E

Documents Related to Flash Memory Programming

Document Name		Document No.
PG-FP5 Flash Memory Programmer User's Manual		—
	RL78, 78K, V850, RX100, RX200, RX600 (Except RX64x), R8C, SH	R20UT2923E
	Common	R20UT2922E
	Setup Manual	R20UT0930E

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Other Documents

Document Name	Document No.
RENESAS Microcontrollers RL78 Family	R01CP0003E
Semiconductor Package Mount Manual	R50ZZ0003E
Semiconductor Reliability Handbook	R51ZZ0001E

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CHAPTER 1 OUTLINE

This chapter of the manual only consists of 1.1, 1.2, 1.3, and 1.6. For all other material on the outline, see the other parts of CHAPTER 1 of R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E).

1.1 Features

Ultra-low power consumption technology

- V_{DD} = single power supply voltage of 1.6 to 5.5 V which can operate a 1.8 V device at a low voltage
- HALT mode
- STOP mode
- SNOOZE mode

RL78 CPU core

- CISC architecture with 3-stage pipeline
- Minimum instruction execution time: Can be changed from high speed (0.04167 μs: @ 24 MHz operation with high-speed on-chip oscillator) to ultra-low speed (30.5 μs: @ 32.768 kHz operation with subsystem clock)
- Address space: 1 MB
- General-purpose registers: (8-bit register × 8) × 4 banks
- On-chip RAM: 24 KB

Flash memory

- Flash memory: 256 KB
- Block size: 1 KB
- Prohibition of block erase and rewriting (security function)
- On-chip debug function
- Self-programming (with boot swap function/flash shield window function)

High-speed on-chip oscillator

- Select from 24 MHz, 16 MHz, 12 MHz, 8 MHz, 6 MHz, 4 MHz, 3 MHz, 2 MHz, and 1 MHz
- High accuracy: ±1.0 % (V_{DD} = 1.8 to 5.5 V, T_A = –20 to +85°C)

Operating ambient temperature

- T_A = -40 to +85°C

Power management and reset function

- On-chip power-on-reset (POR) circuit
- On-chip voltage detector (LVD) (Select interrupt and reset from 14 levels)

DMA (Direct Memory Access) controller

- 4 channels
- Number of clocks during transfer between 8/16-bit SFR and internal RAM: 2 clocks

Multiplier and divider/multiply-accumulator

- 16 bits × 16 bits = 32 bits (Unsigned or signed)
- 32 bits ÷ 32 bits = 32 bits (Unsigned)
- 16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed)

Serial interface

- Simplified SPI (CSI[Note 1]): 1 channel
- UART/UART (LIN-bus supported): 4 channels/1 channel
- I^2C/Simplified I^2C communication: 1 channel/2 channels
- Smart card interface (SMCI): 2 channels

Timer

- 16-bit timer: 8 channels
- 12-bit interval timer: 1 channel
- Real-time clock 2: 1 channel (calendar for 99 years, alarm function, and clock correction function)
- Watchdog timer: 1 channel (operable with the dedicated low-speed on-chip oscillator)

A/D converter

- 8/10-bit resolution A/D converter (V_{DD} = 1.6 to 5.5 V)
- Analog input: 4 channels
- Internal reference voltage (1.45 V) and temperature sensor[Note 2]

Comparator

- 2 channels
- Operation mode: Comparator high-speed mode, comparator low-speed mode, or window mode
- External reference voltage and internal reference voltage are selectable

LCD controller/driver

- Segment signal output: 51 (47)[Note 3]
- Common signal output: 4 (8)[Note 3]
- Internal voltage boosting method and external resistance division method are switchable

I/O port

- I/O port: 65 (N-ch open drain I/O [withstand voltage of 6 V]: 2,
  N-ch open drain I/O [V_{DD} withstand voltage]: 18)
- Can be set to N-ch open drain, TTL input buffer, and on-chip pull-up resistor
- Different potential interface: Can connect to a 1.8/2.5/3 V device
- On-chip clock output/buzzer output controller

Others

- On-chip BCD (binary-coded decimal) correction circuit

<R> **Notes 1.** Although the CSI function is generally called SPI, it is also called CSI in this product, so it is referred to as such in this manual.

2. Can be selected only in HS (high-speed main) mode

3. The values in parentheses are the number of signal outputs when 8 com is used.

○ ROM, RAM capacities

Flash ROM	Data flash	RAM	Part number
256 KB	–	24 KB[Note]	R7F0C020M2DFB

Note This is about 23 KB when the self-programming function is used. (For details, see **CHAPTER 3**.)

1.2 List of Part Numbers

Figure 1-1. Part Number, Memory Size, and Package

<R>

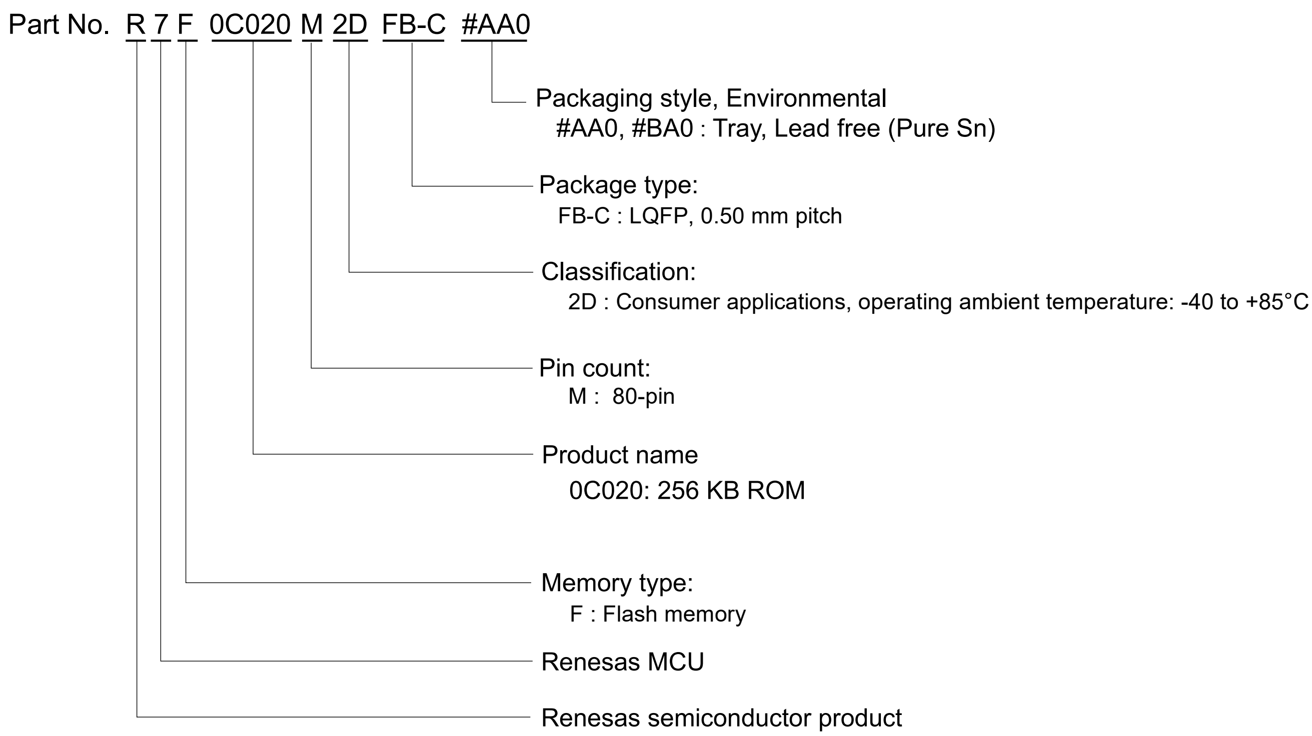
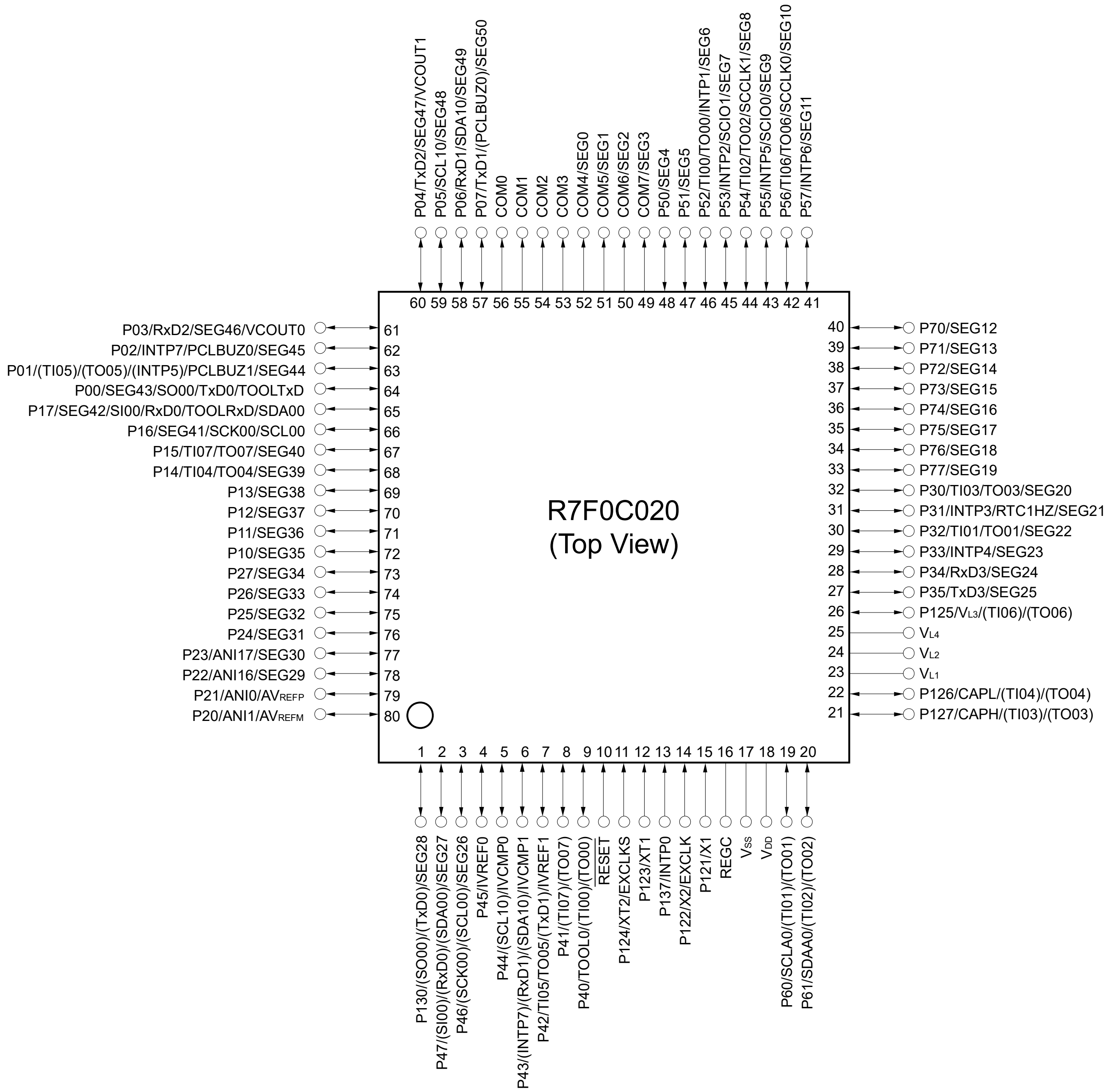


Table 1-1. List of Ordering Part Numbers

Pin Count	Package	Data Flash	Packaging Style, Environmental	Part Number
80 pins	80-pin plastic LQFP (fine pitch) (12 × 12)	Not mounted	Tray, Lead Free (Pure Sn)	R7F0C020M2DFB-C#AA0 R7F0C020M2DFB-C#BA0

<R>

1.3 Pin Configuration (Top View)



Caution Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μF).

Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See **Figure 4-42 Format of Peripheral I/O Redirection Register (PIOR)**.

1.6 Outline of Functions

(1/2)

Item		R7F0C020M2DFB
Code flash memory		256 KB
Data flash memory		–
RAM		24 KB[Note 1]
Address space		1 MB
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode: 1 to 20 MHz (V_{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)
	High-speed on-chip oscillator	HS (High-speed main) mode: 1 to 24 MHz (V_{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)
Subsystem clock		XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz (TYP.): V_{DD} = 1.6 to 5.5 V
Low-speed on-chip oscillator		15 kHz (TYP.)
General-purpose register		(8-bit register × 8) × 4 banks
Minimum instruction execution time		0.04167 μs (High-speed on-chip oscillator: f_{IH} = 24 MHz operation)
		0.05 μs (High-speed system clock: f_{MX} = 20 MHz operation)
		30.5 μs (Subsystem clock: f_{SUB} = 32.768 kHz operation)
Instruction set		● Data transfer (8/16 bits) ● Adder and subtractor/logical operation (8/16 bits) ● Multiplication (8 bits × 8 bits) ● Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.
I/O port	Total	65
	CMOS I/O	58 (N-ch O.D. I/O [V_{DD} withstand voltage]: 18)
	CMOS input	5
	CMOS output	–
	N-ch O.D I/O (withstand voltage: 6 V)	2
Timer	16-bit timer TAU	8 channels (timer outputs 8, PWM outputs: 7[Note 2])
	Watchdog timer	1 channel
	12-bit interval timer (IT)	1 channel
	Real-time clock 2	1 channel
	RTC output	1 ● 1 Hz (subsystem clock: f_{SUB} = 32.768 kHz)

Notes **1.** In the case of the 24 KB, this is about 23 KB when the self-programming function is used.

2. The number of outputs varies depending on the setting of the channels in use and the number of master channels (see **6.9.3 Operation as multiple PWM output function**).

(2/2)

Item		R7F0C020M2DFB
Subsystem clock frequency measurement circuit		Measure the frequency of the subsystem clock by inputting the high accuracy reference clock externally. (for clock error correction of real-time clock 2)
Clock output/buzzer output controller		2
		● 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: f_{MAIN} = 20 MHz operation) ● 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: f_{SUB} = 32.768 kHz operation)
8/10-bit resolution A/D converter		4 channels
Comparator		2 channels
Serial interface		●Simplified SPI (CSI): 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified I^2C: 1 channel ● UART: 1 channel/simplified I^2C: 1 channel ● UART: 2 channels
	I^2C bus	1 channel
	Smart card interface (SMCI)	2 channels
LCD controller/driver		Internal voltage boosting method and external resistance division method are switchable.
	Segment signal output	51 (47)Note 1
	Common signal output	4 (8)Note 1
Multiplier and divider/multiply-accumulator		● 16 bits × 16 bits = 32 bits (Unsigned or signed) ● 32 bits ÷ 32 bits = 32 bits (Unsigned) ● 16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed)
DMA controller		4 channels
Vectored interrupt sources	Internal	41
	External	10
Reset		● Reset by $\overline{RESET}$ pin ● Internal reset by watchdog timer ● Internal reset by power-on-reset ● Internal reset by voltage detector ● Internal reset by illegal instruction executionNote 2 ● Internal reset by RAM parity error ● Internal reset by illegal-memory access
Power-on-reset circuit		● Power-on-reset: 1.51 V (TYP.) ● Power-down-reset: 1.50 V (TYP.)
Voltage detector		● Rising edge: 1.67 V to 4.06 V (14 steps) ● Falling edge: 1.63 V to 3.98 V (14 steps)
On-chip debug function		Provided
Power supply voltage		V_{DD} = 1.6 to 5.5 V
Operating ambient temperature		T_A = –40 to +85°C

Notes **1.** The values in parentheses are the number of signal outputs when 8 com is used.

2. This reset occurs when instruction code FFH is executed.
This reset does not occur during emulation using an in-circuit emulator or an on-chip debugging emulator.

CHAPTER 2 PIN FUNCTIONS

The contents of this chapter are omitted from this manual because the information is the same as in the R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E). See CHAPTER 2 of the latter document for information on the pin functions.

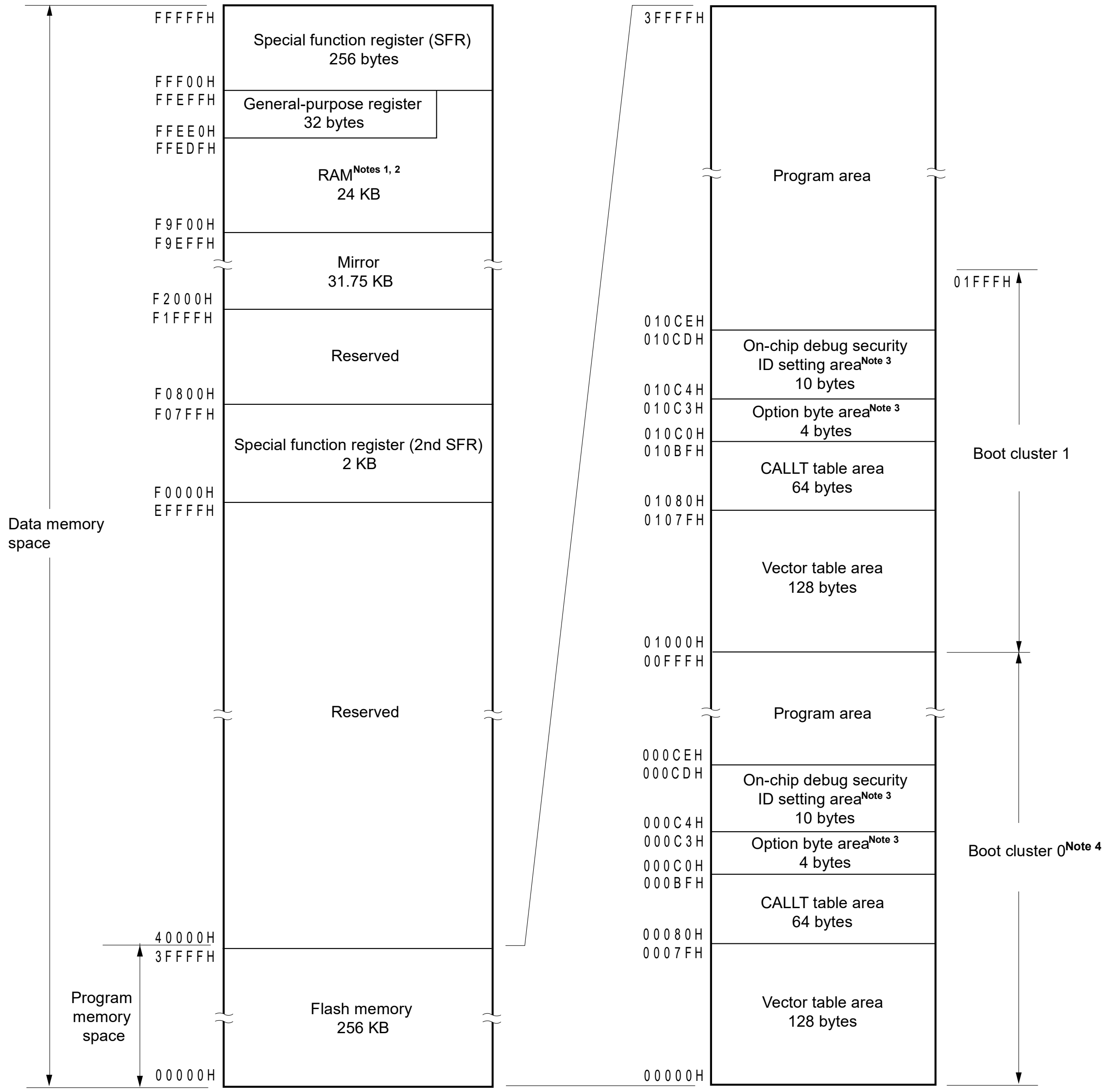
CHAPTER 3 CPU ARCHITECTURE

This chapter of the manual only consists of 3.1, 3.1.1, 3.1.2, 3.1.3, 3.1.6, 3.2, and 3.2.1. For all other material on the CPU architecture, see the other parts of CHAPTER 3 of R7F0C003M2DFB, R7F0C004M2DFB User’s Manual: Hardware (R01UH0393E).
Note that references to “R7F0C003M2DFB” and “R7F0C004M2DFB” should be read as R7F0C020M2DFB.

3.1 Memory Space

Products in the R7F0C020 can access a 1 MB memory space. Figure 3-1 shows the memory map.

Figure 3-1. Memory Map (R7F0C020)



Notes 1. Do not allocate RAM addresses which are used as a stack area, a data buffer, a branch destination of vector interrupt processing, and a DMA transfer destination/transfer source to the area FFE20H to FFEDFH when performing self-programming. Also, use of the area F9F00H to FA309H is prohibited, because this area is used for library.

2. Instructions can be executed from the RAM area excluding the general-purpose register area.

3. When boot swap is not used: Set the option bytes to 000C0H to 000C3H, and the on-chip debug security IDs to 000C4H to 000CDH.

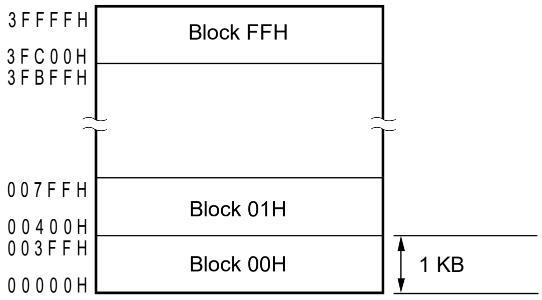
When boot swap is used: Set the option bytes to 000C0H to 000C3H and 010C0H to 010C3H, and the on-chip debug security IDs to 000C4H to 000CDH and 010C4H to 010CDH.

4. Writing boot cluster 0 can be prohibited depending on the setting of security (see **28.6 Security Setting**).

Caution While RAM parity error resets are enabled (RPERDIS = 0), be sure to initialize RAM areas where data access is to proceed and the RAM area + 10 bytes when instructions are fetched from RAM areas, respectively.

Reset signal generation sets RAM parity error resets to enabled (RPERDIS = 0). For details, see 25.3.3 RAM parity error detection function.

Remark The flash memory is divided into blocks (one block = 1 KB). For the address values and block numbers, see **Table 3-1 Correspondence Between Address Values and Block Numbers in Flash Memory**.



(R7F0C020)

Correspondence between the address values and block numbers in the flash memory are shown below.

Table 3-1. Correspondence Between Address Values and Block Numbers in Flash Memory (1/2)

Address Value	Block Number	Address Value	Block Number	Address Value	Block Number	Address Value	Block Number
00000H to 003FFH	00H	08000H to 083FFH	20H	10000H to 103FFH	40H	18000H to 183FFH	60H
00400H to 007FFH	01H	08400H to 087FFH	21H	10400H to 107FFH	41H	18400H to 187FFH	61H
00800H to 00BFFH	02H	08800H to 08BFFH	22H	10800H to 10BFFH	42H	18800H to 18BFFH	62H
00C00H to 00FFFH	03H	08C00H to 08FFFH	23H	10C00H to 10FFFH	43H	18C00H to 18FFFH	63H
01000H to 013FFH	04H	09000H to 093FFH	24H	11000H to 113FFH	44H	19000H to 193FFH	64H
01400H to 017FFH	05H	09400H to 097FFH	25H	11400H to 117FFH	45H	19400H to 197FFH	65H
01800H to 01BFFH	06H	09800H to 09BFFH	26H	11800H to 11BFFH	46H	19800H to 19BFFH	66H
01C00H to 01FFFH	07H	09C00H to 09FFFH	27H	11C00H to 11FFFH	47H	19C00H to 19FFFH	67H
02000H to 023FFH	08H	0A000H to 0A3FFH	28H	12000H to 123FFH	48H	1A000H to 1A3FFH	68H
02400H to 027FFH	09H	0A400H to 0A7FFH	29H	12400H to 127FFH	49H	1A400H to 1A7FFH	69H
02800H to 02BFFH	0AH	0A800H to 0ABFFH	2AH	12800H to 12BFFH	4AH	1A800H to 1ABFFH	6AH
02C00H to 02FFFH	0BH	0AC00H to 0AFFFH	2BH	12C00H to 12FFFH	4BH	1AC00H to 1AFFFH	6BH
03000H to 033FFH	0CH	0B000H to 0B3FFH	2CH	13000H to 133FFH	4CH	1B000H to 1B3FFH	6CH
03400H to 037FFH	0DH	0B400H to 0B7FFH	2DH	13400H to 137FFH	4DH	1B400H to 1B7FFH	6DH
03800H to 03BFFH	0EH	0B800H to 0BBFFH	2EH	13800H to 13BFFH	4EH	1B800H to 1BBFFH	6EH
03C00H to 03FFFH	0FH	0BC00H to 0BFFFH	2FH	13C00H to 13FFFH	4FH	1BC00H to 1BFFFH	6FH
04000H to 043FFH	10H	0C000H to 0C3FFH	30H	14000H to 143FFH	50H	1C000H to 1C3FFH	70H
04400H to 047FFH	11H	0C400H to 0C7FFH	31H	14400H to 147FFH	51H	1C400H to 1C7FFH	71H
04800H to 04BFFH	12H	0C800H to 0CBFFH	32H	14800H to 14BFFH	52H	1C800H to 1CBFFH	72H
04C00H to 04FFFH	13H	0CC00H to 0CFFFH	33H	14C00H to 14FFFH	53H	1CC00H to 1CFFFH	73H
05000H to 053FFH	14H	0D000H to 0D3FFH	34H	15000H to 153FFH	54H	1D000H to 1D3FFH	74H
05400H to 057FFH	15H	0D400H to 0D7FFH	35H	15400H to 157FFH	55H	1D400H to 1D7FFH	75H
05800H to 05BFFH	16H	0D800H to 0DBFFH	36H	15800H to 15BFFH	56H	1D800H to 1DBFFH	76H
05C00H to 05FFFH	17H	0DC00H to 0DFFFH	37H	15C00H to 15FFFH	57H	1DC00H to 1DFFFH	77H
06000H to 063FFH	18H	0E000H to 0E3FFH	38H	16000H to 163FFH	58H	1E000H to 1E3FFH	78H
06400H to 067FFH	19H	0E400H to 0E7FFH	39H	16400H to 167FFH	59H	1E400H to 1E7FFH	79H
06800H to 06BFFH	1AH	0E800H to 0EBFFH	3AH	16800H to 16BFFH	5AH	1E800H to 1EBFFH	7AH
06C00H to 06FFFH	1BH	0EC00H to 0EFFFH	3BH	16C00H to 16FFFH	5BH	1EC00H to 1EFFFH	7BH
07000H to 073FFH	1CH	0F000H to 0F3FFH	3CH	17000H to 173FFH	5CH	1F000H to 1F3FFH	7CH
07400H to 077FFH	1DH	0F400H to 0F7FFH	3DH	17400H to 177FFH	5DH	1F400H to 1F7FFH	7DH
07800H to 07BFFH	1EH	0F800H to 0FBFFH	3EH	17800H to 17BFFH	5EH	1F800H to 1FBFFH	7EH
07C00H to 07FFFH	1FH	0FC00H to 0FFFFH	3FH	17C00H to 17FFFH	5FH	1FC00H to 1FFFFH	7FH

Table 3-1. Correspondence Between Address Values and Block Numbers in Flash Memory (2/2)

Address Value	Block Number	Address Value	Block Number	Address Value	Block Number	Address Value	Block Number
20000H to 203FFH	80H	28000H to 283FFH	A0H	30000H to 303FFH	C0H	38000H to 383FFH	E0H
20400H to 207FFH	81H	28400H to 287FFH	A1H	30400H to 307FFH	C1H	38400H to 387FFH	E1H
20800H to 20BFFH	82H	28800H to 28BFFH	A2H	30800H to 30BFFH	C2H	38800H to 38BFFH	E2H
20C00H to 20FFFH	83H	28C00H to 28FFFH	A3H	30C00H to 30FFFH	C3H	38C00H to 38FFFH	E3H
21000H to 213FFH	84H	29000H to 293FFH	A4H	31000H to 313FFH	C4H	39000H to 393FFH	E4H
21400H to 217FFH	85H	29400H to 297FFH	A5H	31400H to 317FFH	C5H	39400H to 397FFH	E5H
21800H to 21BFFH	86H	29800H to 29BFFH	A6H	31800H to 31BFFH	C6H	39800H to 39BFFH	E6H
21C00H to 21FFFH	87H	29C00H to 29FFFH	A7H	31C00H to 31FFFH	C7H	39C00H to 39FFFH	E7H
22000H to 223FFH	88H	2A000H to 2A3FFH	A8H	32000H to 323FFH	C8H	3A000H to 3A3FFH	E8H
22400H to 227FFH	89H	2A400H to 2A7FFH	A9H	32400H to 327FFH	C9H	3A400H to 3A7FFH	E9H
22800H to 22BFFH	8AH	2A800H to 2ABFFH	AAH	32800H to 32BFFH	CAH	3A800H to 3ABFFH	EAH
22C00H to 22FFFH	8BH	2AC00H to 2AFFFH	ABH	32C00H to 32FFFH	CBH	3AC00H to 3AFFFH	EBH
23000H to 233FFH	8CH	2B000H to 2B3FFH	ACH	33000H to 333FFH	CCH	3B000H to 3B3FFH	ECH
23400H to 237FFH	8DH	2B400H to 2B7FFH	ADH	33400H to 337FFH	CDH	3B400H to 3B7FFH	EDH
23800H to 23BFFH	8EH	2B800H to 2BBFFH	AEH	33800H to 33BFFH	CEH	3B800H to 3BBFFH	EEH
23C00H to 23FFFH	8FH	2BC00H to 2BFFFH	AFH	33C00H to 33FFFH	CFH	3BC00H to 3BFFFH	EFH
24000H to 243FFH	90H	2C000H to 2C3FFH	B0H	34000H to 343FFH	D0H	3C000H to 3C3FFH	F0H
24400H to 247FFH	91H	2C400H to 2C7FFH	B1H	34400H to 347FFH	D1H	3C400H to 3C7FFH	F1H
24800H to 24BFFH	92H	2C800H to 2CBFFH	B2H	34800H to 34BFFH	D2H	3C800H to 3CBFFH	F2H
24C00H to 24FFFH	93H	2CC00H to 2CFFFH	B3H	34C00H to 34FFFH	D3H	3CC00H to 3CFFFH	F3H
25000H to 253FFH	94H	2D000H to 2D3FFH	B4H	35000H to 353FFH	D4H	3D000H to 3D3FFH	F4H
25400H to 257FFH	95H	2D400H to 2D7FFH	B5H	35400H to 357FFH	D5H	3D400H to 3D7FFH	F5H
25800H to 25BFFH	96H	2D800H to 2DBFFH	B6H	35800H to 35BFFH	D6H	3D800H to 3DBFFH	F6H
25C00H to 25FFFH	97H	2DC00H to 2DFFFH	B7H	35C00H to 35FFFH	D7H	3DC00H to 3DFFFH	F7H
26000H to 263FFH	98H	2E000H to 2E3FFH	B8H	36000H to 363FFH	D8H	3E000H to 3E3FFH	F8H
26400H to 267FFH	99H	2E400H to 2E7FFH	B9H	36400H to 367FFH	D9H	3E400H to 3E7FFH	F9H
26800H to 26BFFH	9AH	2E800H to 2EBFFH	BAH	36800H to 36BFFH	DAH	3E800H to 3EBFFH	FAH
26C00H to 26FFFH	9BH	2EC00H to 2EFFFH	BBH	36C00H to 36FFFH	DBH	3EC00H to 3EFFFH	FBH
27000H to 273FFH	9CH	2F000H to 2F3FFH	BCH	37000H to 373FFH	DCH	3F000H to 3F3FFH	FCH
27400H to 277FFH	9DH	2F400H to 2F7FFH	BDH	37400H to 377FFH	DDH	3F400H to 3F7FFH	FDH
27800H to 27BFFH	9EH	2F800H to 2FBFFH	BEH	37800H to 37BFFH	DEH	3F800H to 3FBFFH	FEH
27C00H to 27FFFH	9FH	2FC00H to 2FFFFH	BFH	37C00H to 37FFFH	DFH	3FC00H to 3FFFFH	FFH

3.1.1 Internal program memory space

The internal program memory space stores the program and table data. The R7F0C020 products incorporate internal ROM (flash memory), as shown below.

Table 3-2. Internal ROM Capacity

Part Number	Internal ROM	
	Structure	Capacity
R7F0C020M2DFB	Flash memory	262144 × 8 bits (00000H to 3FFFFH)

The internal program memory space is divided into the following areas.

(1) Vector table area

The 128-byte area 00000H to 0007FH is reserved as a vector table area. The program start addresses for branch upon reset or generation of each interrupt request are stored in the vector table area. Furthermore, the interrupt jump address is a 64 K address of 00000H to 0FFFFH, because the vector code is assumed to be 2 bytes.

Of the 16-bit address, the lower 8 bits are stored at even addresses and the higher 8 bits are stored at odd addresses.

To use the boot swap function, set a vector table also at 01000H to 0107FH.

Table 3-3. Vector Table (1/2)

Vector Table Address	Interrupt Source
00000H	RESET, POR, LVD, WDT, TRAP, IAW, RPE
00004H	INTWDTI
00006H	INTLVI
00008H	INTP0
0000AH	INTP1
0000CH	INTP2
0000EH	INTP3
00010H	INTP4
00012H	INTP5
00014H	INTST2
00016H	INTSR2
00018H	INTSRE2
0001AH	INTDMA0
0001CH	INTDMA1
0001EH	INTST0/INTCSI00/INTIIC00
00020H	INTTM00
00022H	INTSR0
00024H	INTSRE0
	INTTM01H
00026H	INTST1/INTIIC10
00028H	INTSR1
0002AH	INTSRE1
	INTTM03H
0002CH	INTIICA0
0002EH	INTRTIT
00030H	INTFM
00032H	INTTM01
00034H	INTTM02
00036H	INTTM03
00038H	INTAD
0003AH	INTRTC
0003CH	INTIT
00040H	INTST3
00042H	INTSR3

Table 3-3. Vector Table (2/2)

Vector Table Address	Interrupt Source
00046H	INTTM04
00048H	INTTM05
0004AH	INTP6
0004CH	INTP7
00050H	INTCMP0
00052H	INTCMP1
00054H	INTTM06
00056H	INTTM07
00058H	INTSCT0
0005AH	INTSCR0
0005CH	INTSRE3
0005EH	INTMD
00060H	INTSCE0
00062H	INTFL
00064H	INTDMA2
00066H	INTDMA3
00068H	INTSCT1
0006AH	INTSCR1
0006CH	INTSCE1
0007EH	BRK

(2) CALLT instruction table area

The 64-byte area 00080H to 000BFH can store the subroutine entry address of a 2-byte call instruction (CALLT). Set the subroutine entry address to a value in a range of 00000H to 0FFFFH (because an address code is of 2 bytes).
To use the boot swap function, set a CALLT instruction table also at 01080H to 010BFH.

(3) Option byte area

A 4-byte area of 000C0H to 000C3H can be used as an option byte area. Set the option byte at 010C0H to 010C3H when the boot swap is used. For details, see **CHAPTER 27 OPTION BYTE**.

(4) On-chip debug security ID setting area

A 10-byte area of 000C4H to 000CDH and 010C4H to 010CDH can be used as an on-chip debug security ID setting area. Set the on-chip debug security ID of 10 bytes at 000C4H to 000CDH when the boot swap is not used and at 000C4H to 000CDH and 010C4H to 010CDH when the boot swap is used. For details, see **CHAPTER 29 ON-CHIP DEBUG FUNCTION**.

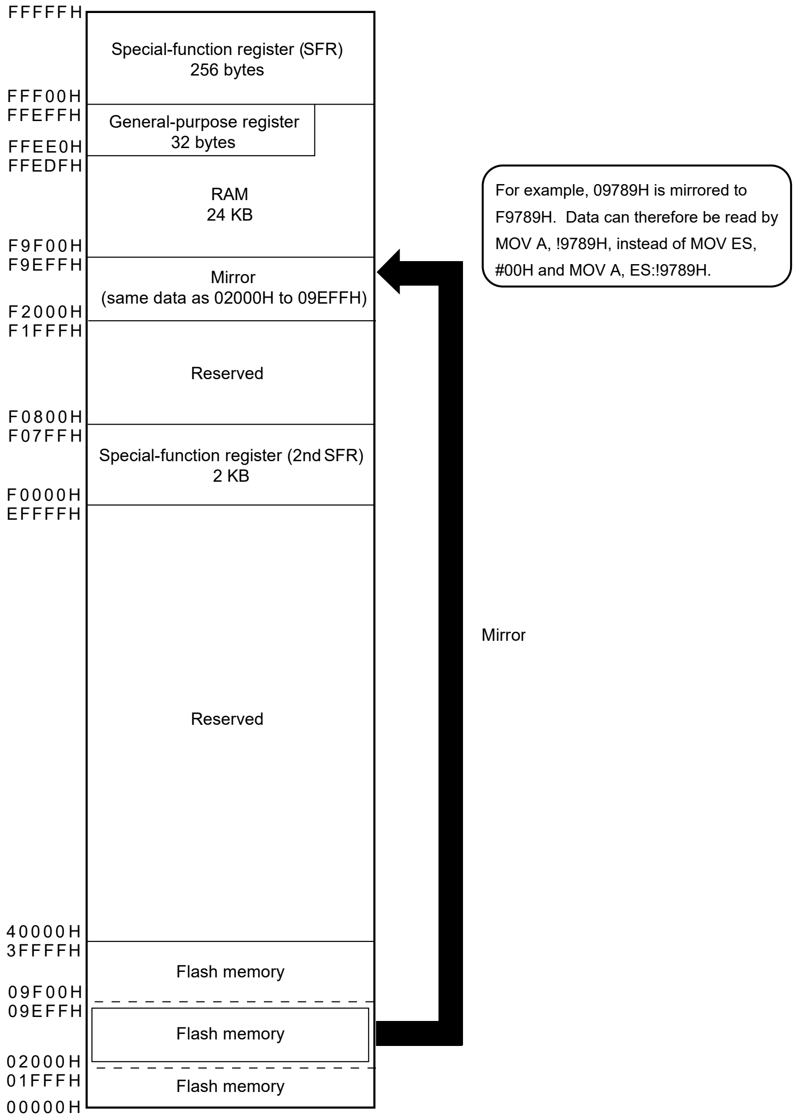
3.1.2 Mirror area

The R7F0C020 mirrors the flash area of 00000H to 0FFFFH or 10000H to 1FFFFH, to F0000H to FFFFFH (the flash area to be mirrored is set by the processor mode control register (PMC)).

By reading data from F0000H to FFFFFH, an instruction that does not have the ES register as an operand can be used, and thus the contents of the flash can be read with the shorter code. However, the flash area is not mirrored to the SFR, extended SFR, RAM area, and use prohibited areas.

See **3.1 Memory Space** for the mirror area of each product.
The mirror area can only be read and no instruction can be fetched from this area.
The following show examples.

Example R7F0C020 (Flash memory: 256 KB, RAM: 24 KB)



The PMC register is described below.

- **Processor mode control register (PMC)**

  This register sets the flash memory space for mirroring to area from F0000H to FFFFFH.
  The PMC register can be set by a 1-bit or 8-bit memory manipulation instruction.
  Reset signal generation sets this register to 00H.

Figure 3-3. Format of **Configuration of Processor Mode Control Register (PMC)**

Address: FFFFEH After reset: 00H R/W

Symbol	7	6	5	4	3	2	1	<0>
PMC	0	0	0	0	0	0	0	MAA

MAA	Selection of flash memory space for mirroring to area from F0000H to FFFFFH
0	00000H to 0FFFFH is mirrored to F0000H to FFFFFH
1	10000H to 1FFFFH is mirrored to F0000H to FFFFFH

Caution After setting the PMC register, wait for at least one instruction and access the mirror area.

3.1.3 Internal data memory space

The R7F0C020 product incorporates the following RAMs.

Table 3-4. Internal RAM Capacity

Part Number	Internal RAM
R7F0C020	24576 × 8 bits (F9F00H to FFEFFH)

The internal RAM can be used as a data area and a program area where instructions are written and executed. Four general-purpose register banks consisting of eight 8-bit registers per bank are assigned to the 32-byte area of FFEE0H to FFEFFH of the internal RAM area. However, instructions cannot be executed by using the general-purpose registers.

The internal RAM is used as stack memory.

Cautions 1. The space (FFEE0H to FFEFFH) that the general-purpose registers are allocated cannot be used for fetching instructions or as a stack area.

2. Do not allocate RAM addresses which are used as a stack area, a data buffer, a branch destination of vector interrupt processing, and a DMA transfer destination/transfer source to the area FFE20H to FFEDFH when performing self-programming.

3. Use of the RAM areas of the following products is prohibited when performing self-programming, because these areas are used for library.

R7F0C020: F9F00H to FA309H

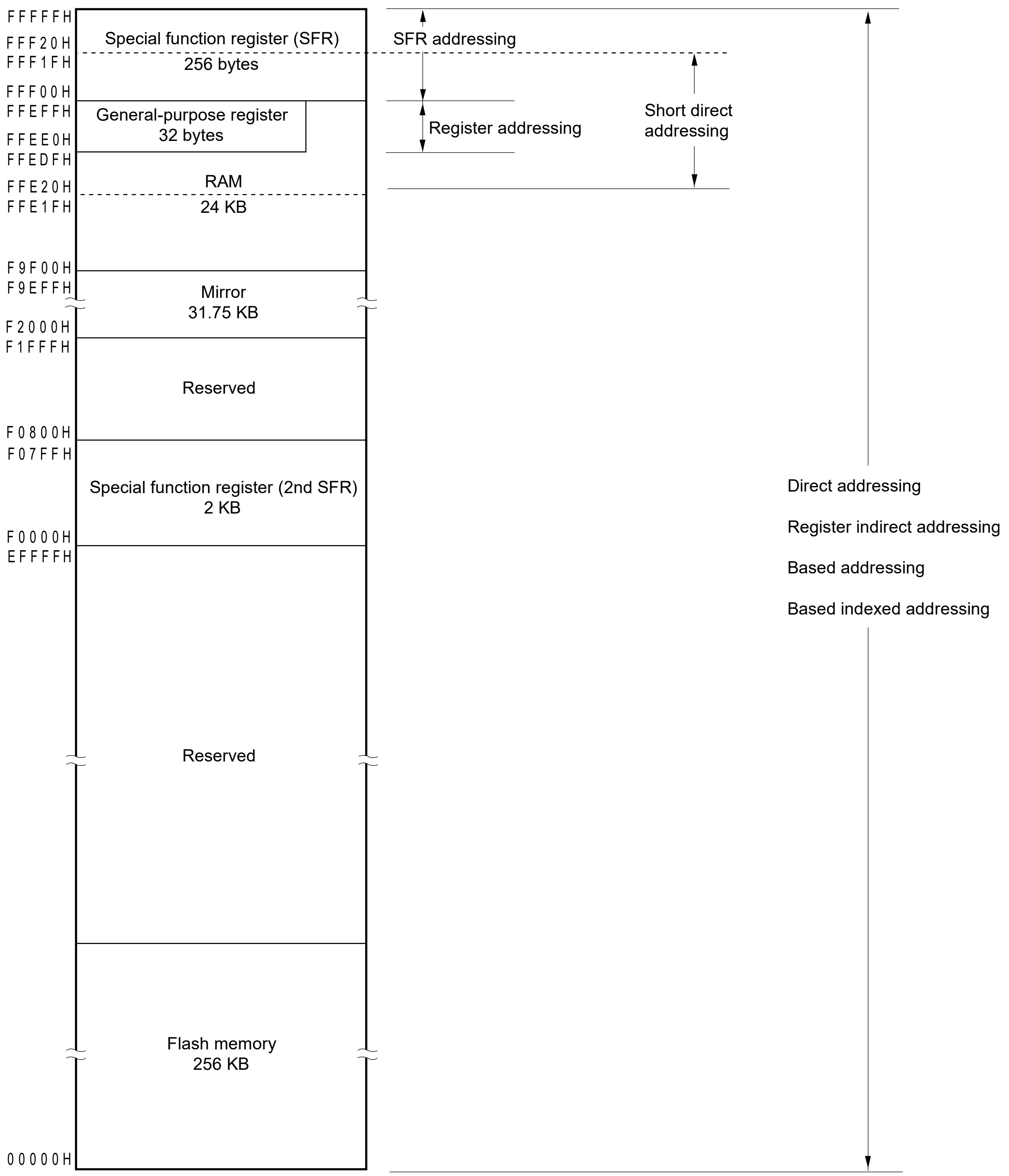
3.1.6 Data memory addressing

Addressing refers to the method of specifying the address of the instruction to be executed next or the address of the register or memory relevant to the execution of instructions.

Several addressing modes are provided for addressing the memory relevant to the execution of instructions for the R7F0C020, based on operability and other considerations. In particular, special addressing methods designed for the functions of the special function registers (SFR) and general-purpose registers are available for use. Figure 3-4 shows correspondence between data memory and addressing.

For details of each addressing, see **3.4 Addressing for Processing Data Addresses**.

Figure 3-4. Correspondence Between Data Memory and Addressing



3.2 Processor Registers

The R7F0C020 product incorporates the following processor registers.

3.2.1 Control registers

The control registers control the program sequence, statuses and stack memory. The control registers consist of a program counter (PC), a program status word (PSW) and a stack pointer (SP).

(1) Program counter (PC)

The program counter is a 20-bit register that holds the address information of the next program to be executed.
In normal operation, PC is automatically incremented according to the number of bytes of the instruction to be fetched.
When a branch instruction is executed, immediate data and register contents are set.
Reset signal generation sets the reset vector table values at addresses 00000H and 00001H to the program counter.

Figure 3-5. Format of Program Counter

	19 … 0
PC	

(2) Program status word (PSW)

The program status word is an 8-bit register consisting of various flags set/reset by instruction execution.
Program status word contents are stored in the stack area upon vectored interrupt request is acknowledged or PUSH PSW instruction execution and are restored upon execution of the RETB, RETI and POP PSW instructions. Reset signal generation sets the PSW register to 06H.

Figure 3-6. Format of Program Status Word

	7							0
PSW	IE	Z	RBS1	AC	RBS0	ISP1	ISP0	CY

(a) Interrupt enable flag (IE)

This flag controls the interrupt request acknowledge operations of the CPU.
When 0, the IE flag is set to the interrupt disabled (DI) state, and all maskable interrupt requests are disabled.
When 1, the IE flag is set to the interrupt enabled (EI) state and maskable interrupt request acknowledgment is controlled with an in-service priority flag (ISP1, ISP0), an interrupt mask flag for various interrupt sources, and a priority specification flag.
The IE flag is reset (0) upon DI instruction execution or interrupt acknowledgment and is set (1) upon EI instruction execution.

(b) Zero flag (Z)

When the operation result is zero or equal, this flag is set (1). It is reset (0) in all other cases.

(c) Register bank select flags (RBS0, RBS1)

These are 2-bit flags to select one of the four register banks.
In these flags, the 2-bit information that indicates the register bank selected by SEL RBn instruction execution is stored.

(d) Auxiliary carry flag (AC)

If the operation result has a carry from bit 3 or a borrow at bit 3, this flag is set (1). It is reset (0) in all other cases.

(e) In-service priority flags (ISP1, ISP0)

This flag manages the priority of acknowledgeable maskable vectored interrupts. Vectored interrupt requests specified lower than the value of ISP0 and ISP1 flags by the priority specification flag registers (PRn0L, PRn0H, PRn1L, PRn1H, PRn2L, PRn2H) (see **20.3.3**) can not be acknowledged. Actual vectored interrupt request acknowledgment is controlled by the interrupt enable flag (IE).

Remark n = 0, 1

(f) Carry flag (CY)

This flag stores overflow and underflow upon add/subtract instruction execution. It stores the shift-out value upon rotate instruction execution and functions as a bit accumulator during bit operation instruction execution.

(3) Stack pointer (SP)

This is a 16-bit register to hold the start address of the memory stack area. Only the internal RAM area can be set as the stack area.

Figure 3-7. Format of Stack Pointer

	15															0
SP	SP15	SP14	SP13	SP12	SP11	SP10	SP9	SP8	SP7	SP6	SP5	SP4	SP3	SP2	SP1	0

In stack addressing through a stack pointer, the SP is decremented ahead of write (save) to the stack memory and is incremented after read (restore) from the stack memory.

Cautions 1. Since reset signal generation makes the SP contents undefined, be sure to initialize the SP before using the stack.

2. It is prohibited to use the general-purpose register (FFEE0H to FFEFFH) space for fetching instructions or a stack area.

3. Do not allocate RAM addresses which are used as a stack area, a data buffer, a branch destination of vector interrupt processing, and a DMA transfer destination/transfer source to the area FFE20H to FFEDFH when performing self-programming.

4. Use of the RAM areas of the following products is prohibited when performing self-programming, because these areas are used for library.

R7F0C020: F9F00H to FA309H

CHAPTER 4 PORT FUNCTIONS

The contents of this chapter are omitted from this manual because the information is the same as in the R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E). See CHAPTER 4 of the latter document for information on the port functions.
Note that references to "R7F0C003M2DFB" and "R7F0C004M2DFB" should be read as R7F0C020M2DFB.

CHAPTER 5 CLOCK GENERATOR

The contents of this chapter are omitted from this manual because the information is the same as in the R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E). See CHAPTER 5 of the latter document for information on the clock generator.
Note that references to "R7F0C003M2DFB" and "R7F0C004M2DFB" should be read as R7F0C020M2DFB.

CHAPTER 6 TIMER ARRAY UNIT

The contents of this chapter are omitted from this manual because the information is the same as in the R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E). See CHAPTER 6 of the latter document for information on the timer array unit.

CHAPTER 7 REAL-TIME CLOCK 2

The contents of this chapter are omitted from this manual because the information is the same as in the R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E). See CHAPTER 7 of the latter document for information on the real-time clock 2.

CHAPTER 8 SUBSYSTEM CLOCK FREQUENCY MEASUREMENT CIRCUIT

The contents of this chapter are omitted from this manual because the information is the same as in the R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E). See CHAPTER 8 of the latter document for information on the subsystem clock frequency measurement circuit.

CHAPTER 9 12-BIT INTERVAL TIMER

The contents of this chapter are omitted from this manual because the information is the same as in the R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E). See CHAPTER 9 of the latter document for information on the 12-bit interval timer.

CHAPTER 10 CLOCK OUTPUT/BUZZER OUTPUT CONTROLLER

The contents of this chapter are omitted from this manual because the information is the same as in the R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E). See CHAPTER 10 of the latter document for information on the clock output/buzzer output controller.

CHAPTER 11 WATCHDOG TIMER

The contents of this chapter are omitted from this manual because the information is the same as in the R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E). See CHAPTER 11 of the latter document for information on the watchdog timer.

CHAPTER 12 A/D CONVERTER

The contents of this chapter are omitted from this manual because the information is the same as in the R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E). See CHAPTER 12 of the latter document for information on the A/D converter.

CHAPTER 13 COMPARATOR

The contents of this chapter are omitted from this manual because the information is the same as in the R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E). See CHAPTER 13 of the latter document for information on the comparator.

CHAPTER 14 SERIAL ARRAY UNIT

The contents of this chapter are omitted from this manual because the information is the same as in the R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E). See CHAPTER 14 of the latter document for information on the serial array unit.
Note that references to "R7F0C003M2DFB" and "R7F0C004M2DFB" should be read as R7F0C020M2DFB.

CHAPTER 15 SERIAL INTERFACE IICA

The contents of this chapter are omitted from this manual because the information is the same as in the R7F0C003M2DFB, R7F0C004M2DFB User’s Manual: Hardware (R01UH0393E). See CHAPTER 15 of the latter document for information on the serial interface IICA.

CHAPTER 16 SMART CARD INTERFACE (SMCI)

The contents of this chapter are omitted from this manual because the information is the same as in the R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E). See CHAPTER 16 of the latter document for information on the smart card interface.
Note that references to "R7F0C003M2DFB" and "R7F0C004M2DFB" should be read as R7F0C020M2DFB.

CHAPTER 17 LCD CONTROLLER/DRIVER

The contents of this chapter are omitted from this manual because the information is the same as in the R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E). See CHAPTER 17 of the latter document for information on the LCD controller/driver.
Note that references to "R7F0C003M2DFB" and "R7F0C004M2DFB" should be read as R7F0C020M2DFB.

CHAPTER 18 MULTIPLIER AND DIVIDER/MULTIPLY-ACCUMULATOR

The contents of this chapter are omitted from this manual because the information is the same as in the R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E). See CHAPTER 18 of the latter document for information on the multiplier and divider/multiply-accumulator.

CHAPTER 19 DMA CONTROLLER

This chapter of the manual only consists of 19.2.2. For all other material on the DMA controller, see the other parts of CHAPTER 19 of R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E).

Note that references to "R7F0C003M2DFB" and "R7F0C004M2DFB" should be read as R7F0C020M2DFB.

19.2.2 DMA RAM address register n (DRAn)

This is a 16-bit register that is used to set a RAM address that is the transfer source or destination of DMA channel n.

Addresses of the internal RAM area other than the general-purpose registers (see **Table 19-2**) can be set to this register.

Set the lower 16 bits of the RAM address.

This register is automatically incremented when DMA transfer has been started. It is incremented by +1 in the 8-bit transfer mode and by +2 in the 16-bit transfer mode. DMA transfer is started from the address set to this DRAn register. When the data of the last address has been transferred, the DRAn register stops with the value of the last address +1 in the 8-bit transfer mode, and the last address +2 in the 16-bit transfer mode.

In the 16-bit transfer mode, the least significant bit is ignored and is treated as an even address.

The DRAn register can be read or written in 8-bit or 16-bit units. However, it cannot be written during DMA transfer.

Reset signal generation clears this register to 0000H.

Figure 19-2. Format of DMA RAM Address Register n (DRAn)

Address: FFFB2H, FFFB3H (DRA0), FFFB4H, FFFB5H (DRA1) , F0202H, F0203H (DRA2), F0204H, F0205H (DRA3) After reset: 0000H R/W

DRA0H: FFFB3H
DRA1H: FFFB5H
DRA2H: F0203H
DRA3H: F0205H

DRA0L: FFFB2H
DRA1L: FFFB4H
DRA2L: F0202H
DRA3L: F0204H

	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
DRAn (n = 0 to 3)																

Table 19-2. Internal RAM Area other than the General-purpose Registers

Part Number	Internal RAM Area Other than the General-purpose Registers
R7F0C020	F9F00H to FFEDFH

Remark n: DMA channel number (n = 0 to 3)

CHAPTER 20 INTERRUPT FUNCTIONS

The contents of this chapter are omitted from this manual because the information is the same as in the R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E). See CHAPTER 20 of the latter document for information on the interrupt functions.

CHAPTER 21 STANDBY FUNCTION

The contents of this chapter are omitted from this manual because the information is the same as in the R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E). See CHAPTER 21 of the latter document for information on the standby function.

CHAPTER 22 RESET FUNCTION

The contents of this chapter are omitted from this manual because the information is the same as in the R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E). See CHAPTER 22 of the latter document for information on the reset function.

CHAPTER 23 POWER-ON-RESET CIRCUIT

The contents of this chapter are omitted from this manual because the information is the same as in the R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E). See CHAPTER 23 of the latter document for information on the power-on reset circuit.
Note that references to "R7F0C003M2DFB" and "R7F0C004M2DFB" should be read as R7F0C020M2DFB.

CHAPTER 24 VOLTAGE DETECTOR

The contents of this chapter are omitted from this manual because the information is the same as in the R7F0C003M2DFB, R7F0C004M2DFB User’s Manual: Hardware (R01UH0393E). See CHAPTER 24 of the latter document for information on the voltage detector.

CHAPTER 25 SAFETY FUNCTIONS

This chapter of the manual only consists of 25.3.1.1, 25.3.1.2, 25.3.4.1, and 25.3.6. For all other material on the safety functions, see the other parts of CHAPTER 25 of R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E).

Note that references to "R7F0C003M2DFB" and "R7F0C004M2DFB" should be read as R7F0C020M2DFB.

25.3.1.1 Flash memory CRC control register (CRC0CTL)

This register is used to control the operation of the high-speed CRC ALU, as well as to specify the operation range.
The CRC0CTL register can be set by a 1-bit or 8-bit memory manipulation instruction.
Reset signal generation clears this register to 00H.

Figure 25-1. Format of Flash Memory CRC Control Register (CRC0CTL)

Address: F02F0H After reset: 00H R/W

Symbol	<7>	6	5	4	3	2	1	0
CRC0CTL	CRC0EN	0	0	0	FEA3	FEA2	FEA1	FEA0

CRC0EN	Control of CRC ALU operation
0	Stop the operation.
1	Start the operation according to HALT instruction execution.

FEA3	FEA2	FEA1	FEA0	High-speed CRC operation range
0	0	0	0	00000H to 03FFBH (16 K – 4 bytes)
0	0	0	1	00000H to 07FFBH (32 K – 4 bytes)
0	0	1	0	00000H to 0BFFBH (48 K – 4 bytes)
0	0	1	1	00000H to 0FFFBH (64 K – 4 bytes)
0	1	0	0	00000H to 13FFBH (80 K – 4 bytes)
0	1	0	1	00000H to 17FFBH (96 K – 4 bytes)
0	1	1	0	00000H to 1BFFBH (112 K – 4 bytes)
0	1	1	1	00000H to 1FFFBH (128 K – 4 bytes)
1	0	0	0	00000H to 23FFBH (144K – 4 bytes)
1	0	0	1	00000H to 27FFBH (160K – 4 bytes)
1	0	1	0	00000H to 2BFFBH (176K – 4 bytes)
1	0	1	1	00000H to 2FFFBH (192K – 4 bytes)
1	1	0	0	00000H to 33FFBH (208K – 4 bytes)
1	1	0	1	00000H to 37FFBH (224K – 4 bytes)
1	1	1	0	00000H to 3BFFBH (240K – 4 bytes)
1	1	1	1	00000H to 3FFFBH (256K – 4 bytes)

Remark Input the expected CRC operation result value to be used for comparison in the lowest 4 bytes of the flash memory. Note that the operation range will thereby be reduced by 4 bytes.

25.3.1.2 Flash memory CRC operation result register (PGCRCL)

This register is used to store the high-speed CRC operation results.

The PGCRCL register can be set by a 16-bit memory manipulation instruction.

Reset signal generation clears this register to 0000H.

Figure 25-2. Format of Flash Memory CRC Operation Result Register (PGCRCL)

Address: F02F2H After reset: 0000H R/W

Symbol	15	14	13	12	11	10	9	8
PGCRCL	PGCRC15	PGCRC14	PGCRC13	PGCRC12	PGCRC11	PGCRC10	PGCRC9	PGCRC8
	7	6	5	4	3	2	1	0
	PGCRC7	PGCRC6	PGCRC5	PGCRC4	PGCRC3	PGCRC2	PGCRC1	PGCRC0

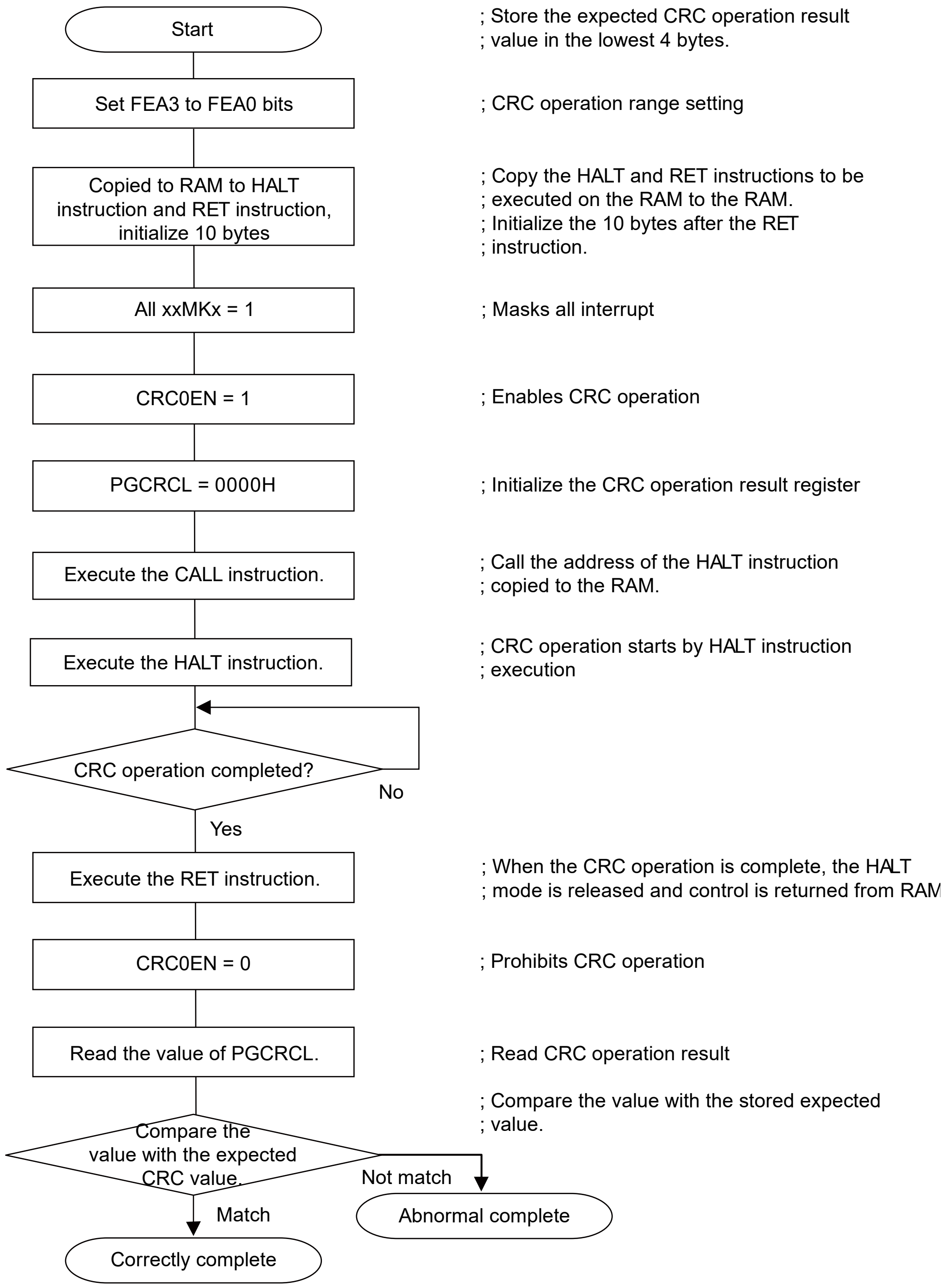
PGCRC15 to 0	High-speed CRC operation results
0000H to FFFFH	Store the high-speed CRC operation results.

Caution The PGCRCL register can only be written if CRC0EN (bit 7 of the CRC0CTL register) = 1.

Figure 25-3 shows the flowchart of flash memory CRC operation function (high-speed CRC).

<Operation flow>

Figure 25-3. Flowchart of Flash Memory CRC Operation Function (High-speed CRC)



Cautions 1. The CRC operation is executed only on the flash.

2. Store the expected CRC operation value in the area below the operation range in the flash.

3. The CRC operation is enabled by executing the HALT instruction in the RAM area.
Be sure to execute the HALT instruction in RAM area.

The expected CRC value can be calculated by using the Integrated Development Environment CubeSuite+. See the **Integrated Development Environment CubeSuite+ User's Manual** for details.

25.3.4.1 Invalid memory access detection control register (IAWCTL)

This register is used to control detection of invalid memory access and the RAM/SFR guard function.
The GRAM1 and GRAM0 bits are used for the RAM guard function.
The IAWCTL register can be set by an 8-bit memory manipulation instruction.
Reset signal generation clears this register to 00H.

Figure 25-9. Format of Invalid Memory Access Detection Control Register (IAWCTL)

Address: F0078H After reset: 00H R/W

Symbol	7	6	5	4	3	2	1	0
IAWCTL	IAWEN	0	GRAM1	GRAM0	0	GPORT	GINT	GCSC

GRAM1	GRAM0	RAM guard space[Note]
0	0	Disabled. RAM can be written to.
0	1	The 128 bytes of space starting at the start address in the RAM
1	0	The 256 bytes of space starting at the start address in the RAM
1	1	The 512 bytes of space starting at the start address in the RAM

Note The RAM start address is F9F00H.

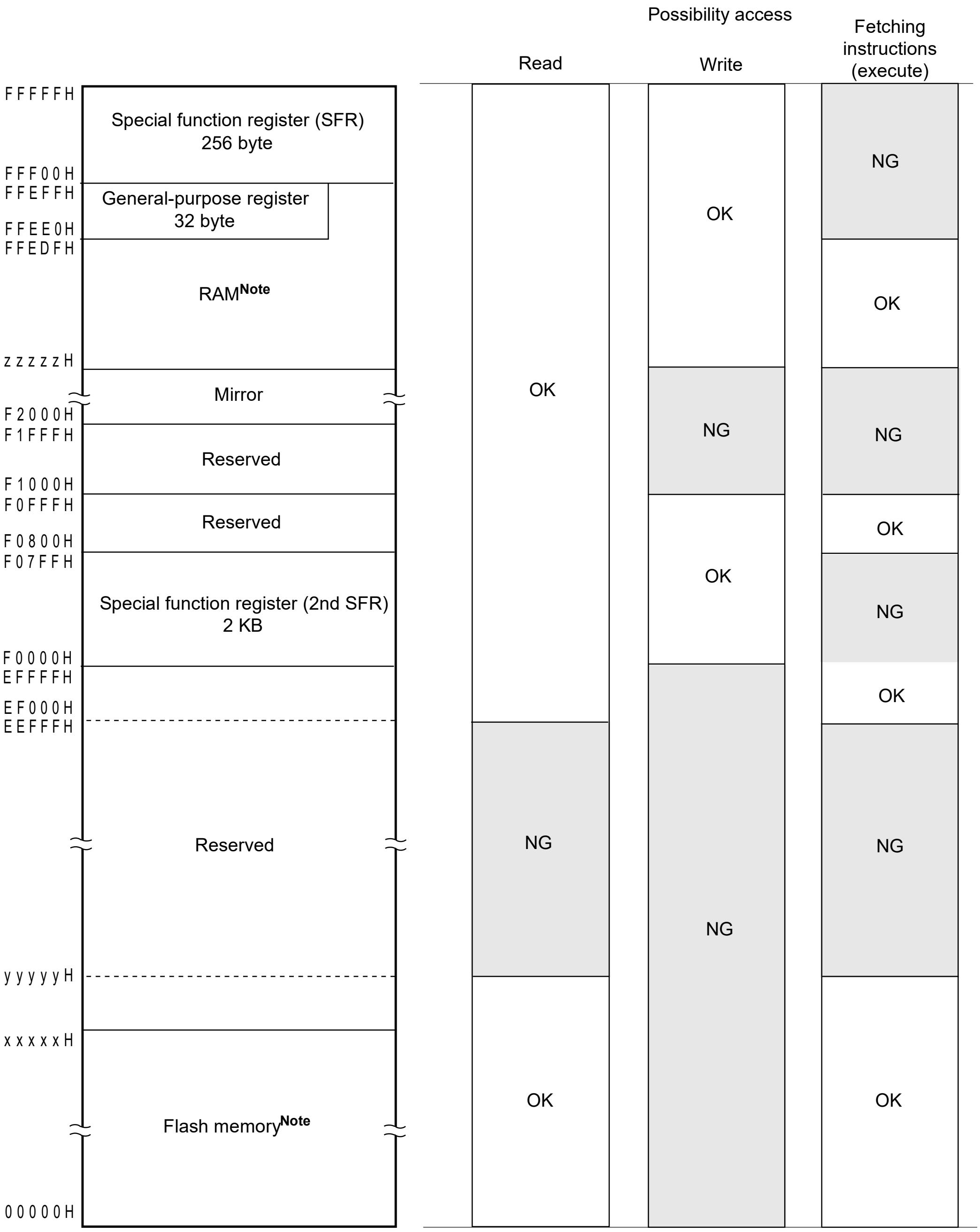
25.3.6 Invalid memory access detection function

The IEC60730 standard mandates checking that the CPU and interrupts are operating correctly.

The illegal memory access detection function triggers a reset if a memory space specified as access-prohibited is accessed.

The illegal memory access detection function applies to the areas indicated by NG in Figure 25-11.

Figure 25-11. Invalid Access Detection Area



Note The following table lists the flash memory, RAM, and lowest detection address for this product:

Products	Flash memory (00000H to xxxxxH)	RAM (zzzzzH to FFEFFH)	Detected lowest address for read/ instruction fetch (execution) (yyyyyH)
R7F0C020	262144 × 8 bit (00000H to 3FFFFH)	24576 × 8 bit (F9F00H to FFEFFH)	40000H

CHAPTER 26 REGULATOR

The contents of this chapter are omitted from this manual because the information is the same as in the R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E). See CHAPTER 26 of the latter document for information on the regulator.
Note that references to "R7F0C003M2DFB" and "R7F0C004M2DFB" should be read as R7F0C020M2DFB.

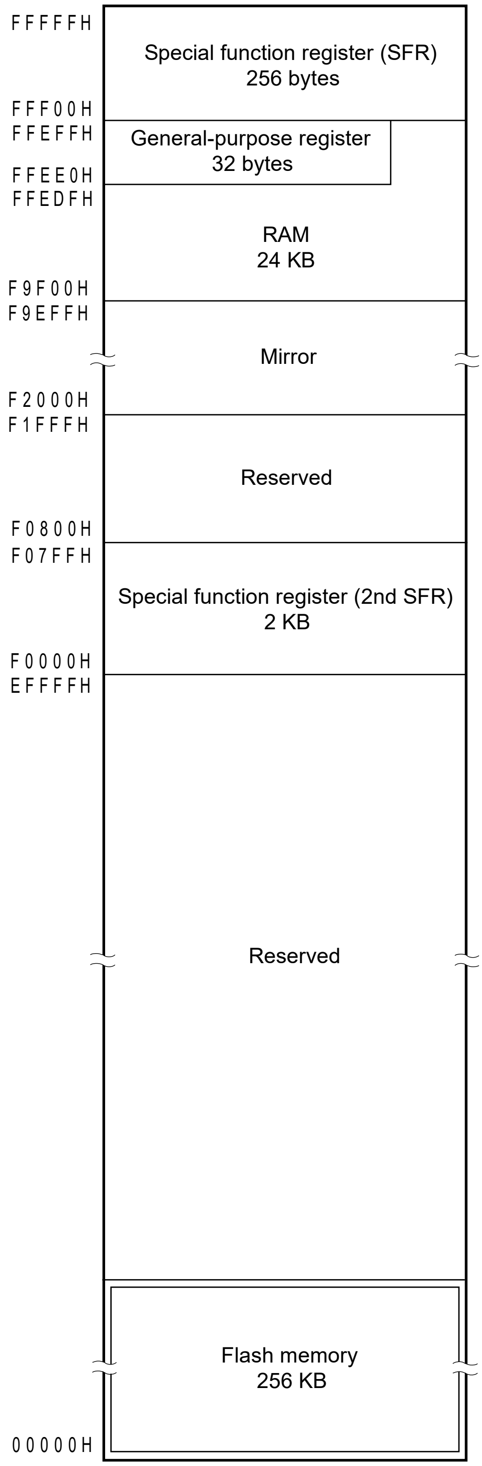
CHAPTER 27 OPTION BYTE

The contents of this chapter are omitted from this manual because the information is the same as in the R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E). See CHAPTER 27 of the latter document for information on the option byte.
Note that references to "R7F0C003M2DFB" and "R7F0C004M2DFB" should be read as R7F0C020M2DFB.

CHAPTER 28 FLASH MEMORY

This chapter of the manual only consists of 28.4.4 and 28.5.3. For all other material on the flash memory, see the other parts of CHAPTER 28 of R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E).

The RL78 microcontroller incorporates the flash memory to which a program can be written, erased, and overwritten.



The following methods for programming the flash memory are available.

The flash memory can be rewritten to through serial programming using a flash memory programmer or an external device (UART communication), or through self-programming.

● Serial programming using flash memory programmer (see **28.1**)
Data can be written to the flash memory on-board or off-board by using a dedicated flash memory programmer.

● Serial programming using external device (UART communication) (see **28.2**)
Data can be written to the flash memory on-board through UART communication with an external device (microcontroller or ASIC).

● Self-programming (see **28.5**)
The user application can execute self-programming of the flash memory by using the flash self-programming library.

28.4.4 Communication commands

The RL78 microcontroller executes serial programming through the commands listed in **Table 28-7.**

The signals sent from the dedicated flash memory programmer or external device to the RL78 microcontroller are called commands, and programming functions corresponding to the commands are executed. For details, refer to the **RL78 Microcontrollers (RL78 Protocol A) Programmer Edition Application Note (R01AN0815)**.

Table 28-7. Flash Memory Control Commands

Classification	Command Name	Function
Verify	Verify	Compares the contents of a specified area of the flash memory with data transmitted from the programmer.
Erase	Block Erase	Erases a specified area in the flash memory.
Blank check	Block Blank Check	Checks if a specified block in the flash memory has been correctly erased.
Write	Programming	Writes data to a specified area in the flash memory[Note].
Getting information	Silicon Signature	Gets the RL78 microcontroller information (such as the part number, flash memory configuration, and programming firmware version).
	Checksum	Gets the checksum data for a specified area.
Security	Security Set	Sets security information.
	Security Get	Gets security information.
	Security Release	Release setting of prohibition of writing.
Others	Reset	Used to detect synchronization status of communication.
	Baud Rate Set	Sets baud rate when UART communication mode is selected.

Note Confirm that no data has been written to the write area. Because data cannot be erased after block erase is prohibited, do not write data if the data has not been erased.

Product information (such as product name and firmware version) can be obtained by executing the “Silicon Signature” command.

Table 28-8 is a list of signature data and **Table 28-9** shows an example of signature data.

Table 28-8. Signature Data List

Field Name	Description	Number of Transmit Data
Device code	The serial number assigned to the device	3 bytes
Device name	Device name (ASCII code)	10 bytes
Flash memory area last address	Last address of flash memory area (Sent from lower address. Example: 00000H to 3FFFFH (256 KB) → FFH, FFH, 03H)	3 bytes
Firmware version	Version information of firmware for programming (Sent from upper address. Example: From Ver. 1.23 → 01H, 02H, 03H)	3 bytes

Table 28-9. Example of Signature Data

Field Name	Description	Number of Transmit Data	Data (Hexadecimal)
Device code	RL78 protocol A	3 bytes	10 00 06
Device name	R7F0C020	10 bytes	52 = "R" 37 = "7" 46 = "F" 30 = "0" 43 = "C" 30 = "0" 32 = "2" 30 = "0" 4D = "M" 20 = " "
Flash memory area last address	Flash memory area 00000H to 3FFFFH (256 KB)	3 bytes	FF FF 03
Firmware version	Ver.1.23	3 bytes	01 02 03

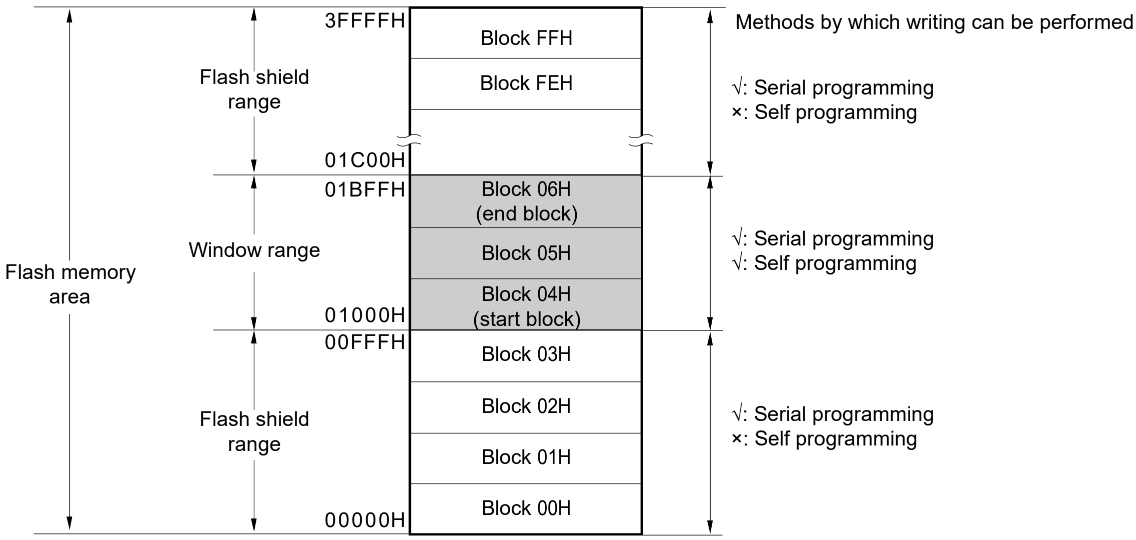
28.5.3 Flash shield window function

The flash shield window function is provided as one of the security functions for self programming. It disables writing to and erasing areas outside the range specified as a window only during self programming.

The window range can be set by specifying the start and end blocks. The window range can be set or changed during both serial programming and self-programming.

Writing to and erasing areas outside the window range are disabled during self programming. During serial programming, however, areas outside the range specified as a window can be written and erased.

Figure 28-11. Flash Shield Window Setting Example
(Target Devices: R7F0C020, Start Block: 04H, End Block: 06H)



Caution If the rewrite-prohibited area of the boot cluster 0 overlaps with the flash shield window range, prohibition to rewrite the boot cluster 0 takes priority.

Table 28-10. Relationship Between Flash Shield Window Function Setting/Change Methods and Commands

Programming Conditions	Window Range Setting/Change Methods	Execution Commands	
		Block Erase	Write
Self-programming	Specify the starting and ending blocks by the flash self-programming library.	Block erasing is enabled only within the window range.	Writing is enabled only within the range of window range.
Serial programming	Specify the starting and ending blocks on GUI of dedicated flash memory programmer, etc.	Block erasing is enabled also outside the window range.	Writing is enabled also outside the window range.

Remark See **28.6 Security Settings** to prohibit writing/erasing during serial programming.

CHAPTER 29 ON-CHIP DEBUG FUNCTION

This chapter of the manual only consists of 29.3. For all other material on the on-chip debug function, see the other parts of CHAPTER 29 of R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E).

29.3 Securing of User Resources

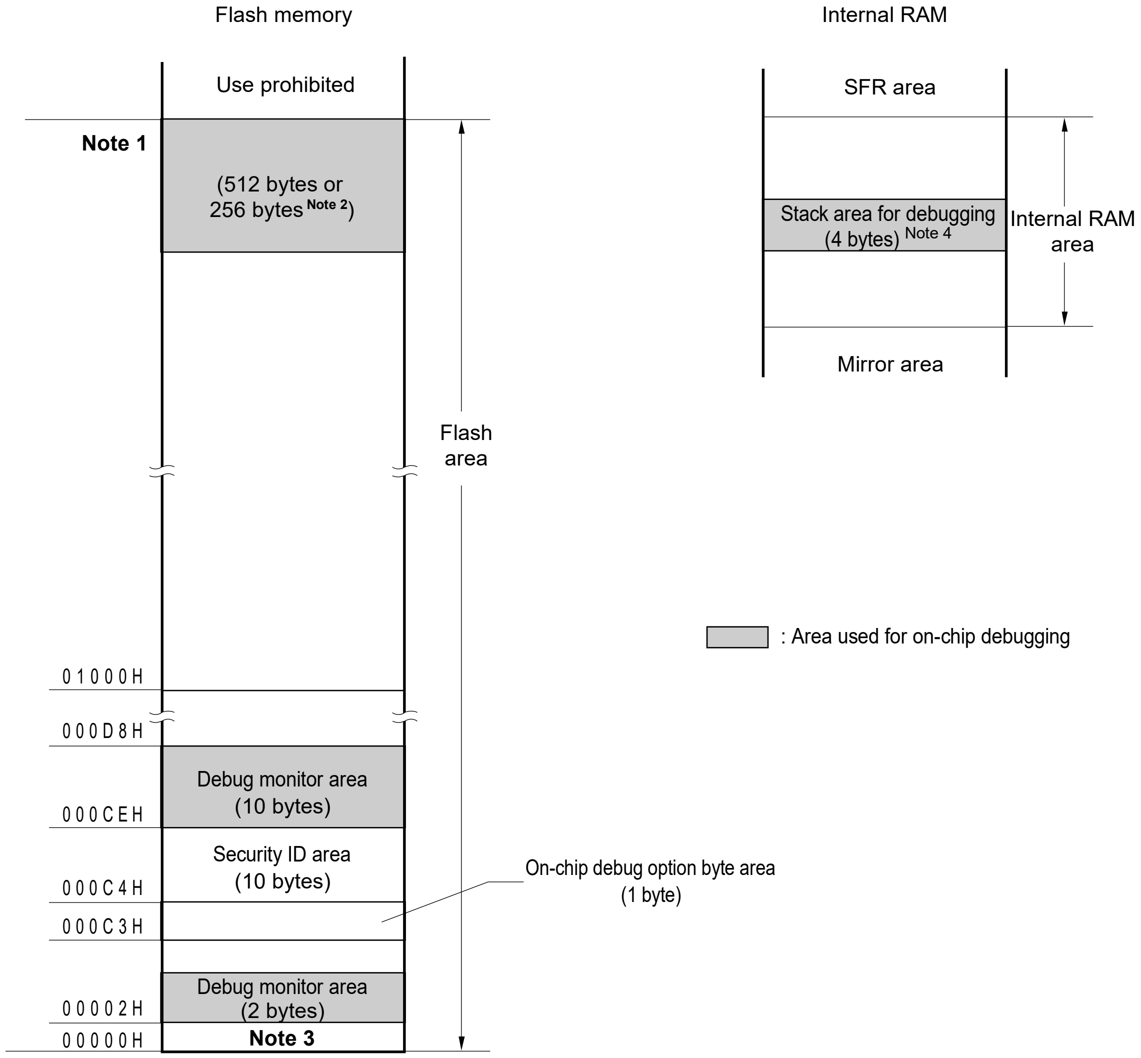
To perform communication between the RL78 microcontroller and E1 on-chip debugging emulator, as well as each debug function, the securing of memory space must be done beforehand.

If Renesas Electronics assembler or compiler is used, the items can be set by using link options.

(1) Securement of memory space

The shaded portions in Figure 29-2 are the areas reserved for placing the debug monitor program, so user programs or data cannot be allocated in these spaces. When using the on-chip debug function, these spaces must be secured so as not to be used by the user program. Moreover, this area must not be rewritten by the user program.

Figure 29-2. Memory Spaces Where Debug Monitor Programs Are Allocated



Notes 1. Address differs depending on products as follows.

Product Name	Address of **Note 1**
R7F0C020	3FFFFH

2. When real-time RAM monitor (RRM) function and dynamic memory modification (DMM) function are not used, it is 256 bytes.

3. In debugging, reset vector is rewritten to address allocated to a monitor program.

4. Since this area is allocated immediately before the stack area, the address of this area varies depending on the stack increase and decrease. That is, 4 extra bytes are consumed for the stack area used. When using self-programming, 12 extra bytes are consumed for the stack area used.

CHAPTER 30 BCD CORRECTION CIRCUIT

The contents of this chapter are omitted from this manual because the information is the same as in the R7F0C003M2DFB, R7F0C004M2DFB User's Manual: Hardware (R01UH0393E). See CHAPTER 30 of the latter document for information on the BCD correction circuit.

CHAPTER 31 INSTRUCTION SET

The contents of this chapter are omitted from this manual because the information is the same as in the R7F0C003M2DFB, R7F0C004M2DFB User’s Manual: Hardware (R01UH0393E). See CHAPTER 31 of the latter document for information on the instruction set.

CHAPTER 32 ELECTRICAL SPECIFICATIONS

Caution **The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.**

32.1 Absolute Maximum Ratings

Absolute Maximum Ratings (1/3)

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage	V_{DD}		–0.5 to +6.5	V
REGC pin input voltage	V_{IREGC}	REGC	–0.3 to +2.8 and –0.3 to V_{DD} +0.3 Note 1	V
Input voltage	V_{I1}	P00 to P07, P10 to P17, P20 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P121 to P127, P130, P137	–0.3 to V_{DD} +0.3 Note 2	V
	V_{I2}	P60 and P61 (N-ch open-drain)	–0.3 to +6.5	V
	V_{I3}	EXCLK, EXCLKS, $\overline{\text{RESET}}$	–0.3 to V_{DD} +0.3 Note 2	V
Output voltage	V_{O1}	P00 to P07, P10 to P17, P20 to P27, P30 to P35, P40 to P47, P50 to P57, P60, P61, P70 to P77, P121 to P127, P130, P137	–0.3 to V_{DD} +0.3 Note 2	V
Analog input voltage	V_{AI1}	ANI0, ANI1, ANI16, ANI17	–0.3 to V_{DD} +0.3 and –0.3 to $AV_{REF(+)}$ +0.3 Notes 2, 3	V

Notes 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.

2. Must be 6.5 V or lower.

3. Do not exceed $AV_{REF(+)}$ + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remarks 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2. $AV_{REF (+)}$: + side reference voltage of the A/D converter.

3. V_{SS}: Reference voltage

Absolute Maximum Ratings (2/3)

Parameter	Symbol	Conditions		Ratings	Unit
LCD voltage	V_{L1}	V_{L1} voltage[Note 1]		–0.3 to +2.8 and –0.3 to V_{L4} +0.3	V
	V_{L2}	V_{L2} voltage[Note 1]		–0.3 to V_{L4} +0.3[Note 2]	V
	V_{L3}	V_{L3} voltage[Note 1]		–0.3 to V_{L4} +0.3[Note 2]	V
	V_{L4}	V_{L4} voltage[Note 1]		–0.3 to +6.5	V
	V_{LCAP}	CAPL, CAPH voltage[Note 1]		–0.3 to V_{L4} +0.3[Note 2]	V
	V_{OUT}	COM0 to COM7 SEG0 to SEG50 output voltage	External resistance division method	–0.3 to V_{DD} +0.3[Note 2]	V
			Internal voltage boosting method	–0.3 to V_{L4} +0.3[Note 2]	V

Notes 1. This value only indicates the absolute maximum ratings when applying voltage to the V_{L1}, V_{L2}, V_{L3}, and V_{L4} pins; it does not mean that applying voltage to these pins is recommended. When using the internal voltage boosting method, connect these pins to V_{SS} via a capacitor (0.47 μF ± 30%) and connect a capacitor (0.47 μF ± 30%) between the CAPL and CAPH pins.

2. Must be 6.5 V or lower.

Caution **Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.**

Remark V_{SS}: Reference voltage

Absolute Maximum Ratings (3/3)

Parameter	Symbol	Conditions		Ratings	Unit
Output current, high	I_{OH1}	Per pin	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P60, P61, P70 to P77, P125 to P127, P130	–40	mA
		Total of all pins –170 mA	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P60, P61, P70 to P77, P125 to P127, P130	–170	mA
	I_{OH2}	Per pin	P20, P21	–0.5	mA
		Total of all pins		–1	mA
Output current, low	I_{OL1}	Per pin	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P60, P61, P70 to P77, P125 to P127, P130	40	mA
		Total of all pins 170 mA	P40 to P47, P130	70	mA
			P00 to P07, P10 to P17, P22 to P27, P30 to P35, P50 to P57, P60, P61, P70 to P77, P125 to P127	100	mA
	I_{OL2}	Per pin	P20, P21	1	mA
		Total of all pins		2	mA
Operating ambient temperature	T_A	In normal operation mode		–40 to +85	°C
		In flash memory programming mode			
Storage temperature	T_{stg}			–65 to +150	°C

Caution **Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.**

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

32.2 Oscillator Characteristics

32.2.1 X1 and XT1 oscillator characteristics

(T_A = –40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (f_X)Note	Ceramic resonator/ crystal resonator	2.7 V ≤ V_{DD} ≤ 5.5 V	1.0		20.0	MHz
		2.4 V ≤ V_{DD} < 2.7 V	1.0		16.0	
		1.8 V ≤ V_{DD} < 2.4 V	1.0		8.0	
		1.6 V ≤ V_{DD} < 1.8 V	1.0		4.0	
XT1 clock oscillation frequency (f_{XT})Note	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to **AC Characteristics** for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, see **5.4 System Clock Oscillator**.

32.2.2 On-chip oscillator characteristics

(T_A = –40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency[Notes 1, 2]	f_{IH}			1		24	MHz
High-speed on-chip oscillator clock frequency accuracy		–20 to +85°C	1.8 V ≤ V_{DD} ≤ 5.5 V	–1.0		+1.0	%
			1.6 V ≤ V_{DD} < 1.8 V	–5.0		+5.0	%
		–40 to –20°C	1.8 V ≤ V_{DD} ≤ 5.5 V	–1.5		+1.5	%
			1.6 V ≤ V_{DD} < 1.8 V	–5.5		+5.5	%
Low-speed on-chip oscillator clock frequency	f_{IL}				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				–15		+15	%

Notes1. The high-speed on-chip oscillator frequency is selected by bits 0 to 4 of the option byte (000C2H/010C2H) and bits 0 to 2 of the HOCODIV register.

2. This indicates the oscillator characteristics only. Refer to **AC Characteristics** for the instruction execution time.

32.3 DC Characteristics

32.3.1 Pin characteristics

(T_A = –40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high[Note 1]	I_{OH1}	Per pin for P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130	1.6 V ≤ V_{DD} ≤ 5.5 V			–10.0[Note 2]	mA
		Total of P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130 (When duty = 70% [Note 3])	4.0 V ≤ V_{DD} ≤ 5.5 V			–90.0	mA
			2.7 V ≤ V_{DD} < 4.0 V			–15.0	mA
			1.8 V ≤ V_{DD} < 2.7 V			–7.0	mA
			1.6 V ≤ V_{DD} < 1.8 V			–3.0	mA
	I_{OH2}	Per pin for P20 and P21	1.6 V ≤ V_{DD} ≤ 5.5 V			–0.1[Note 2]	mA
		Total of all pins (When duty = 70%[Note 3])	1.6 V ≤ V_{DD} ≤ 5.5 V			–0.2	mA

Notes 1. Value of the current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin

2. Do not exceed the total current value.

3. Output current value under conditions where the duty factor ≤ 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (I_{OH} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OH} = –90.0 mA

Total output current of pins = (–90.0 × 0.7)/(80 × 0.01) ≈ –78.75 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P00, P04 to P07, P16, P17, P35, P42 to P44, P46, P47, P53 to P56, and P130 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = –40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low[Note 1]	I_{OL1}	Per pin for P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130				20.0[Note 2]	mA
		Per pin for P60 and P61				15.0[Note 2]	mA
		Total of P40 to P47, P130 (When duty = 70%[Note 3])	4.0 V ≤ V_{DD} ≤ 5.5 V			70.0	mA
			2.7 V ≤ V_{DD} < 4.0 V			15.0	mA
			1.8 V ≤ V_{DD} < 2.7 V			9.0	mA
			1.6 V ≤ V_{DD} < 1.8 V			4.5	mA
		Total of P00 to P07, P10 to P17, P22 to P27, P30 to P35, P50 to P57, P70 to P77, P125 to P127 (When duty = 70% [Note 3])	4.0 V ≤ V_{DD} ≤ 5.5 V			90.0	mA
			2.7 V ≤ V_{DD} < 4.0 V			35.0	mA
			1.8 V ≤ V_{DD} < 2.7 V			20.0	mA
			1.6 V ≤ V_{DD} < 1.8 V			10.0	mA
		Total of all pins (When duty = 70%[Note 3])				160.0	mA
	I_{OL2}	Per pin for P20 and P21				0.4[Note 2]	mA
		Total of all pins (When duty = 70%[Note 3])	1.6 V ≤ V_{DD} ≤ 5.5 V			0.8	mA

Notes1. Value of the current at which the device operation is guaranteed even if the current flows from an output pin to the V_{SS} pin

2. Do not exceed the total current value.

3. Output current value under conditions where the duty factor ≤ 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (I_{OL} × 0.7)/(n × 0.01)

  <Example> Where n = 80% and I_{OL} = 70.0 mA

  Total output current of pins = (70.0 × 0.7)/(80 × 0.01) ≈ 61.25 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = –40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V_{IH1}	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130	Normal input buffer	0.8V_{DD}		V_{DD}	V
	V_{IH2}	P03, P05, P06, P16, P17, P34, P43, P44, P46, P47, P53, P55	TTL input buffer 4.0 V ≤ V_{DD} ≤ 5.5 V	2.2		V_{DD}	V
			TTL input buffer 3.3 V ≤ V_{DD} < 4.0 V	2.0		V_{DD}	V
			TTL input buffer 1.6 V ≤ V_{DD} < 3.3 V	1.5		V_{DD}	V
	V_{IH3}	P20, P21		0.7V_{DD}		V_{DD}	V
	V_{IH4}	P60, P61		0.7V_{DD}		6.0	V
	V_{IH5}	P121 to P124, P137, EXCLK, EXCLKS, $\overline{RESET}$		0.8V_{DD}		V_{DD}	V
Input voltage, low	V_{IL1}	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130	Normal input buffer	0		0.2V_{DD}	V
	V_{IL2}	P03, P05, P06, P16, P17, P34, P43, P44, P46, P47, P53, P55	TTL input buffer 4.0 V ≤ V_{DD} ≤ 5.5 V	0		0.8	V
			TTL input buffer 3.3 V ≤ V_{DD} < 4.0 V	0		0.5	V
			TTL input buffer 1.6 V ≤ V_{DD} < 3.3 V	0		0.32	V
	V_{IL3}	P20, P21		0		0.3V_{DD}	V
	V_{IL4}	P60, P61		0		0.3V_{DD}	V
	V_{IL5}	P121 to P124, P137, EXCLK, EXCLKS, $\overline{RESET}$		0		0.2V_{DD}	V

Caution The maximum value of V_{IH} of pins P00, P04 to P07, P16, P17, P35, P42 to P44, P46, P47, P53 to P56, and P130 is V_{DD}, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = –40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V_{OH1}	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130	4.0 V ≤ V_{DD} ≤ 5.5 V, I_{OH1} = –10.0 mA	V_{DD} – 1.5			V
			4.0 V ≤ V_{DD} ≤ 5.5 V, I_{OH1} = –3.0 mA	V_{DD} – 0.7			V
			2.7 V ≤ V_{DD} ≤ 5.5 V, I_{OH1} = –2.0 mA	V_{DD} – 0.6			V
			1.8 V ≤ V_{DD} ≤ 5.5 V, I_{OH1} = –1.5 mA	V_{DD} – 0.5			V
			1.6 V ≤ V_{DD} ≤ 5.5 V, I_{OH1} = –1.0 mA	V_{DD} – 0.5			V
	V_{OH2}	P20 and P21	1.6 V ≤ V_{DD} ≤ 5.5 V, I_{OH2} = –100 μA	V_{DD} – 0.5			V
Output voltage, low	V_{OL1}	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130	4.0 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 20 mA			1.3	V
			4.0 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 8.5 mA			0.7	V
			2.7 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 3.0 mA			0.6	V
			2.7 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 1.5 mA			0.4	V
			1.8 V ≤ V_{DD} ≤ 5.5 V, I_{OL1} = 0.6 mA			0.4	V
			1.6 V ≤ V_{DD} < 1.8 V, I_{OL1} = 0.3 mA			0.4	V
	V_{OL2}	P20 and P21	1.6 V ≤ V_{DD} ≤ 5.5 V, I_{OL2} = 400μA			0.4	V
	V_{OL3}	P60 and P61	4.0 V ≤ V_{DD} ≤ 5.5 V, I_{OL3} = 15.0 mA			2.0	V
			4.0 V ≤ V_{DD} ≤ 5.5 V, I_{OL3} = 5.0 mA			0.4	V
			2.7 V ≤ V_{DD} ≤ 5.5 V, I_{OL3} = 3.0 mA			0.4	V
			1.8 V ≤ V_{DD} ≤ 5.5 V, I_{OL3} = 2.0 mA			0.4	V
			1.6 V ≤ V_{DD} < 1.8 V, I_{OL3} = 1.0 mA			0.4	V

Caution P00, P04 to P07, P16, P17, P35, P42 to P44, P46, P47, P53 to P56, and P130 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = –40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Input leakage current, high	I_{LIH1}	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130, P137	$V_I = V_{DD}$				1	μA
	I_{LIH2}	P20 and P21, $\overline{RESET}$	$V_I = V_{DD}$				1	μA
	I_{LIH3}	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	$V_I = V_{DD}$	In input port mode and when external clock is input			1	μA
				Resonator connected			10	μA
Input leakage current, low	I_{LIL1}	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130, P137	$V_I = V_{SS}$				–1	μA
	I_{LIL2}	P20 and P21, $\overline{RESET}$	$V_I = V_{SS}$				–1	μA
	I_{LIL3}	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	$V_I = V_{SS}$	In input port mode and when external clock is input			–1	μA
				Resonator connected			–10	μA
On-chip pull-up resistance	R_{U1}	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P46, P47, P50 to P57, P70 to P77, P125 to P127, P130	$V_I = V_{SS}$	2.4 V ≤ V_{DD} < 5.5 V	10	20	100	kΩ
				1.6 V ≤ V_{DD} < 2.4 V	10	30	100	kΩ
	R_{U2}	P40 to P45	$V_I = V_{SS}$		10	20	100	kΩ

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

32.3.2 Supply current characteristics

(T_A = –40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) (1/2)

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current[Note 1]	I_{DD1}	Operating mode	HS (high-speed main) mode[Note 5]	f_{IH} = 24 MHz[Note 3]	Basic operation	V_{DD} = 5.0 V		1.7		mA
						V_{DD} = 3.0 V		1.7		mA
					Normal operation	V_{DD} = 5.0 V		3.6	6.1	mA
						V_{DD} = 3.0 V		3.6	6.1	mA
				f_{IH} = 16 MHz[Note 3]	Normal operation	V_{DD} = 5.0 V		2.7	4.7	mA
						V_{DD} = 3.0 V		2.7	4.7	mA
			LS (low-speed main) mode[Note 5]	f_{IH} = 8 MHz[Note 3]	Normal operation	V_{DD} = 3.0 V		1.2	2.1	mA
						V_{DD} = 2.0 V		1.2	2.1	mA
			LV (low-voltage main) mode[Note 5]	f_{IH} = 4 MHz[Note 3]	Normal operation	V_{DD} = 3.0 V		1.2	1.8	mA
						V_{DD} = 2.0 V		1.2	1.8	mA
			HS (high-speed main) mode[Note 5]	f_{MX} = 20 MHz[Note 2], V_{DD} = 5.0 V	Normal operation	Square wave input		3.0	5.1	mA
						Resonator connection		3.2	5.2	mA
				f_{MX} = 20 MHz[Note 2], V_{DD} = 3.0 V	Normal operation	Square wave input		2.9	5.1	mA
						Resonator connection		3.2	5.2	mA
				f_{MX} = 16 MHz[Note 2], V_{DD} = 5.0 V	Normal operation	Square wave input		2.5	4.4	mA
						Resonator connection		2.7	4.5	mA
				f_{MX} = 16 MHz[Note 2], V_{DD} = 3.0 V	Normal operation	Square wave input		2.5	4.4	mA
						Resonator connection		2.7	4.5	mA
				f_{MX} = 10 MHz[Note 2], V_{DD} = 5.0 V	Normal operation	Square wave input		1.9	3.0	mA
						Resonator connection		1.9	3.0	mA
				f_{MX} = 10 MHz[Note 2], V_{DD} = 3.0 V	Normal operation	Square wave input		1.9	3.0	mA
						Resonator connection		1.9	3.0	mA
			LS (low-speed main) mode[Note 5]	f_{MX} = 8 MHz[Note 2], V_{DD} = 3.0 V	Normal operation	Square wave input		1.1	2.0	mA
						Resonator connection		1.1	2.0	mA
				f_{MX} = 8 MHz[Note 2], V_{DD} = 2.0 V	Normal operation	Square wave input		1.1	2.0	mA
						Resonator connection		1.1	2.0	mA
			Subsystem clock operation	f_{SUB} = 32.768 kHz[Note 4], T_A = –40°C	Normal operation	Square wave input		4.0	5.4	μA
						Resonator connection		4.3	5.4	μA
				f_{SUB} = 32.768 kHz[Note 4], T_A = +25°C	Normal operation	Square wave input		4.0	5.4	μA
						Resonator connection		4.3	5.4	μA
				f_{SUB} = 32.768 kHz[Note 4], T_A = +50°C	Normal operation	Square wave input		4.1	7.1	μA
						Resonator connection		4.4	7.1	μA
				f_{SUB} = 32.768 kHz[Note 4], T_A = +70°C	Normal operation	Square wave input		4.3	8.7	μA
						Resonator connection		4.7	8.7	μA
				f_{SUB} = 32.768 kHz[Note 4], T_A = +85°C	Normal operation	Square wave input		4.7	12.0	μA
						Resonator connection		5.2	12.0	μA

(**Notes** and **Remarks** are listed on the next page.)

Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed
<R> to V_{DD} or V_{SS}. The following points apply in the HS (high-speed main), LS (low-speed main), and LV (low-voltage main) modes.

- The currents in the “TYP.” column do not include the operating currents of the peripheral modules.
- The currents in the “MAX.” column include the operating currents of the peripheral modules, except for those flowing into the LCD controller/driver, A/D converter, LVD circuit, comparator, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the “TYP.” and “MAX.” columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into the real-time clock 2.

2. When high-speed on-chip oscillator and subsystem clock are stopped.

3. When high-speed system clock and subsystem clock are stopped.

4. When high-speed on-chip oscillator and high-speed system clock are stopped. When setting ultra-low power
<R> consumption oscillation (AMPHS1 = 1).

5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 24 MHz
2.4 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 16 MHz
LS (low-speed main) mode: 1.8 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 8 MHz
LV (low-voltage main) mode: 1.6 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 4 MHz

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: High-speed on-chip oscillator clock frequency

3. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

4. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

(T_A = –40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) (2/2)

	Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
	Supply current [Note 1]	I_{DD2} [Note 2]	HALT mode	HS (high-speed main) mode [Note 6]	f_{IH} = 24 MHz [Note 4]	V_{DD} = 5.0 V		0.49	1.64	mA
<R>						V_{DD} = 3.0 V		0.49	1.64	
					f_{IH} = 16 MHz [Note 4]	V_{DD} = 5.0 V		0.43	1.11	mA
						V_{DD} = 3.0 V		0.43	1.11	
				LS (low-speed main) mode [Note 6]	f_{IH} = 8 MHz [Note 4]	V_{DD} = 3.0 V		280	770	μA
<R>						V_{DD} = 2.0 V		280	770	
<R>				LV (low-voltage main) mode [Note 6]	f_{IH} = 4 MHz [Note 4]	V_{DD} = 3.0 V		430	700	μA
						V_{DD} = 2.0 V		430	700	
				HS (high-speed main) mode [Note 6]	f_{MX} = 20 MHz [Note 3], V_{DD} = 5.0 V	Square wave input		0.31	1.42	mA
<R>						Resonator connection		0.48	1.42	
					f_{MX} = 20 MHz [Note 3], V_{DD} = 3.0 V	Square wave input		0.29	1.42	mA
						Resonator connection		0.48	1.42	
					f_{MX} = 16 MHz [Note 3], V_{DD} = 5.0 V	Square wave input		0.26	0.86	mA
						Resonator connection		0.45	1.15	
					f_{MX} = 16 MHz [Note 3], V_{DD} = 3.0 V	Square wave input		0.25	0.86	mA
						Resonator connection		0.44	1.15	
					f_{MX} = 10 MHz [Note 3], V_{DD} = 5.0 V	Square wave input		0.20	0.63	mA
						Resonator connection		0.28	0.71	
					f_{MX} = 10 MHz [Note 3], V_{DD} = 3.0 V	Square wave input		0.19	0.63	mA
						Resonator connection		0.28	0.71	
				LS (low-speed main) mode [Note 6]	f_{MX} = 8 MHz [Note 3], V_{DD} = 3.0 V	Square wave input		100	560	μA
<R>						Resonator connection		160	560	
					f_{MX} = 8 MHz [Note 3], V_{DD} = 2.0 V	Square wave input		100	560	μA
						Resonator connection		160	560	
				Subsystem clock operation	f_{SUB} = 32.768 kHz [Note 5], T_A = –40°C	Square wave input		0.34	0.62	μA
						Resonator connection		0.51	0.80	
					f_{SUB} = 32.768 kHz [Note 5], T_A = +25°C	Square wave input		0.38	0.62	μA
						Resonator connection		0.57	0.80	
					f_{SUB} = 32.768 kHz [Note 5], T_A = +50°C	Square wave input		0.46	2.30	μA
						Resonator connection		0.67	2.49	
					f_{SUB} = 32.768 kHz [Note 5], T_A = +70°C	Square wave input		0.65	4.03	μA
						Resonator connection		0.91	4.22	
					f_{SUB} = 32.768 kHz [Note 5], T_A = +85°C	Square wave input		1.00	8.04	μA
						Resonator connection		1.31	8.23	
<R>		I_{DD3}	STOP mode [Note 7]	T_A = –40°C				0.18	0.52	μA
<R>				T_A = +25°C				0.24	0.52	
				T_A = +50°C				0.33	2.21	
				T_A = +70°C				0.53	3.94	
				T_A = +85°C				0.93	7.95	

(**Notes** and **Remarks** are listed on the next page.)

Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed
<R> to V_{DD} or V_{SS}. The following points apply in the HS (high-speed main), LS (low-speed main), and LV (low-voltage main) modes.

- The currents in the "TYP." column do not include the operating currents of the peripheral modules.
- The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the LCD controller/driver, A/D converter, LVD circuit, comparator, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into the real-time clock 2.

In the STOP mode, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules.

2. During HALT instruction execution by flash memory.

3. When high-speed on-chip oscillator and subsystem clock are stopped.

4. When high-speed system clock and subsystem clock are stopped.

5. When high-speed on-chip oscillator and high-speed system clock are stopped.
<R> When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1).

<R> **6.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 24 MHz
2.4 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 16 MHz
LS (low-speed main) mode: 1.8 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 8 MHz
LV (low-voltage main) mode: 1.6 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 4 MHz

<R> **7.** Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: High-speed on-chip oscillator clock frequency

3. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is T_A = 25°C

(T_A = –40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	I_{FIL} [Note 1]						0.20		μA
RTC2 operating current	I_{RTC} [Notes 1, 2, 3]	f_{SUB} = 32.768 kHz					0.02		μA
12-bit interval timer operating current	I_{TMKA} [Notes 1, 2, 4]						0.04		μA
Watchdog timer operating current	I_{WDT} [Notes 1, 2, 5]	f_{IL} = 15 kHz					0.22		μA
A/D converter operating current	I_{ADC} [Notes 1, 6]	When conversion at maximum speed	Normal mode, AV_{REFP} = V_{DD} = 5.0 V				1.3	1.7	mA
			Low voltage mode, AV_{REFP} = V_{DD} = 3.0 V				0.5	0.7	
A/D converter reference voltage current	I_{ADREF} [Note 1]						75.0		μA
Temperature sensor operating current	I_{TMPS} [Note 1]						75.0		μA
LVD operating current	I_{LVD} [Notes 1, 7]						0.08		μA
Comparator operating current	I_{CMP} [Notes 1, 10]	V_{DD} = 5.0 V, Regulator output voltage = 2.1 V	Window mode				12.5		μA
			Comparator high-speed mode				6.5		μA
			Comparator low-speed mode				1.7		μA
		V_{DD} = 5.0 V, Regulator output voltage = 1.8 V	Window mode				8.0		μA
			Comparator high-speed mode				4.0		μA
			Comparator low-speed mode				1.3		μA
Self-programming operating current	I_{FSP} [Notes 1, 8]						2.00	12.20	mA
SNOOZE operating current	I_{SNOZ} [Note 1]	ADC operation	While the mode is shifting [Note 9]				0.50	0.60	mA
			During A/D conversion, in low voltage mode, AV_{REFP} = V_{DD} = 3.0 V				1.20	1.44	
		Simplified SPI (CSI)/UART operation					0.70	0.84	μA
LCD operating current	I_{LCD1} [Notes 1, 11, 12]	External resistance division method	f_{LCD} = f_{SUB} LCD clock = 128 Hz	1/3 bias, four time slices	V_{DD} = 5.0 V, V_{L4} = 5.0 V		0.04	0.20	μA
	I_{LCD2} [Note 1, 11]	Internal voltage boosting method	f_{LCD} = f_{SUB} LCD clock = 128 Hz	1/3 bias, four time slices	V_{DD} = 3.0 V, V_{L4} = 3.0 V (V_{LCD} = 04H)		0.85	2.20	μA
					V_{DD} = 5.0 V, V_{L4} = 5.1 V (V_{LCD} = 12H)		1.55	3.70	

(**Notes** and **Remarks** are listed on the next page.)

Notes 1. Current flowing to V_{DD}.

2. When high speed on-chip oscillator and high-speed system clock are stopped.

3. Current flowing only to the real-time clock 2 (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The value of the current for the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{RTC}, when the real-time clock 2 operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added. I_{DD2} subsystem clock operation includes the operational current of real-time clock 2.

4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The value of the current for the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{TMKA}, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added.

5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{WDT} when the watchdog timer operates.

6. Current flowing only to the A/D converter. The current value of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC} when the A/D converter operates in an operation mode or the HALT mode.

7. Current flowing only to the LVD circuit. The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{LVD} when the LVD circuit operates.

8. Current flowing only during self programming.

9. For shift time to the SNOOZE mode, see **21.3.3 SNOOZE mode.**

10. Current flowing only to the comparator circuit. The current value of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{CMP} when the comparator circuit operates.

11. Current flowing only to the LCD controller/driver. The value of the current for the RL78 microcontrollers is the sum of the supply current (I_{DD1} or I_{DD2}) and LCD operating current (I_{LCD1}, I_{LCD2}, or I_{LCD3}), when the LCD controller/driver operates in operation mode or HALT mode. However, not including the current flowing into the LCD panel. Conditions of the TYP. value and MAX. value are as follows.

- Setting 20 pins as the segment function and blinking all
- Selecting f_{SUB} for system clock when LCD clock = 128 Hz (LCDC0 = 07H)
- Setting four time slices and 1/3 bias

12. Not including the current flowing into the external division resistor when using the external resistance division method.

Remarks 1. f_{IL}: Low-speed on-chip oscillator clock frequency

2. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

3. f_{CLK}: CPU/peripheral hardware clock frequency

4. The temperature condition for the TYP. value is T_A = 25°C.

32.4 AC Characteristics

(T_A = –40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

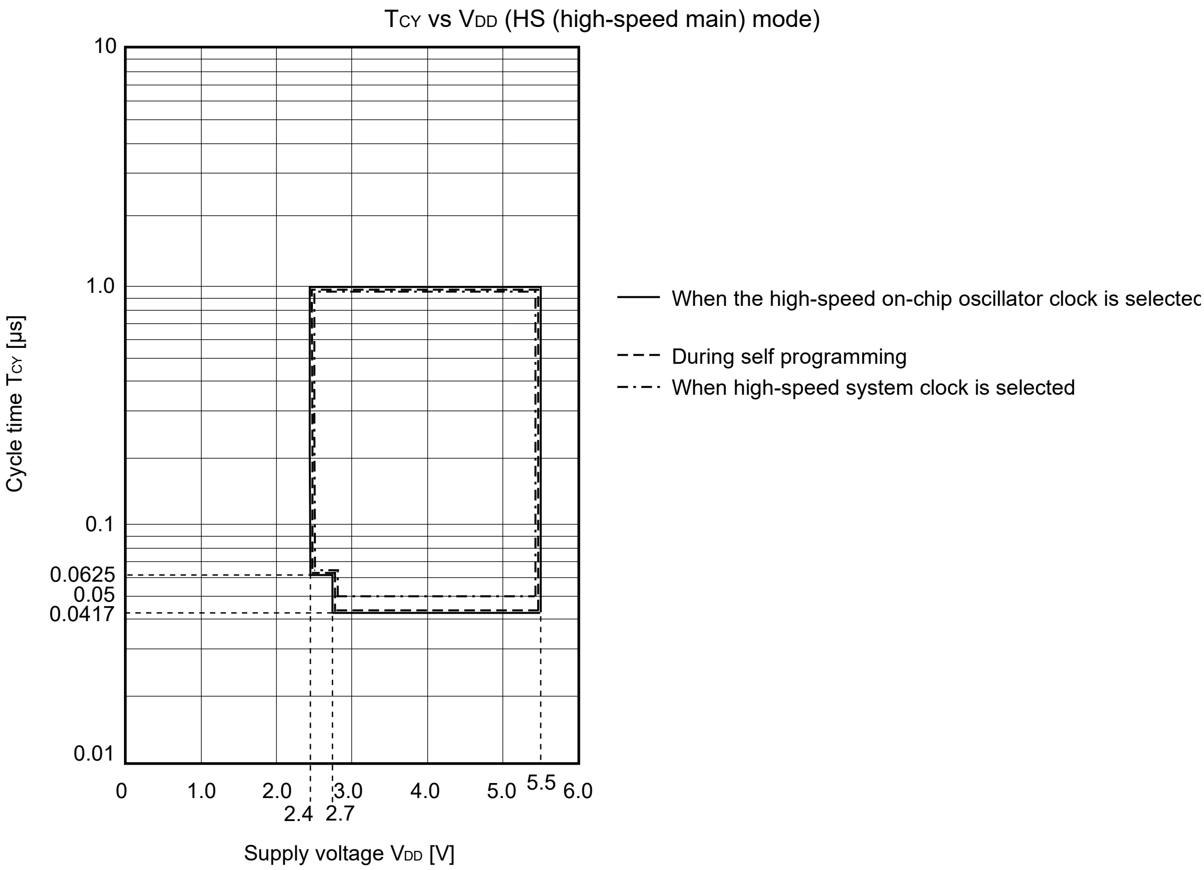
Parameter	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T_{CY}	Main system clock (f_{MAIN}) operation	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.0417		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
			LS (low-speed main) mode	1.8 V ≤ V_{DD} ≤ 5.5 V	0.125		1	μs
			LV (low-voltage main) mode	1.6 V ≤ V_{DD} ≤ 5.5 V	0.25		1	μs
		Subsystem clock (f_{SUB}) operation[Note]		1.8 V ≤ V_{DD} ≤ 5.5 V	28.5	30.5	31.3	μs
		In the self programming mode	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.0417		1	μs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	μs
			LS (low-speed main) mode	1.8 V ≤ V_{DD} ≤ 5.5 V	0.125		1	μs
			LV (low-voltage main) mode	1.8 V ≤ V_{DD} ≤ 5.5 V	0.25		1	μs
External system clock frequency	f_{EX}	2.7 V ≤ V_{DD} ≤ 5.5 V			1.0		20.0	MHz
		2.4 V ≤ V_{DD} < 2.7 V			1.0		16.0	MHz
		1.8 V ≤ V_{DD} < 2.4 V			1.0		8.0	MHz
		1.6 V ≤ V_{DD} < 1.8 V			1.0		4.0	MHz
	f_{EXS}				32		35	kHz
External system clock input high-level width, low-level width	t_{EXH}, t_{EXL}	2.7 V ≤ V_{DD} ≤ 5.5 V			24			ns
		2.4 V ≤ V_{DD} < 2.7 V			30			ns
		1.8 V ≤ V_{DD} < 2.4 V			60			ns
		1.6 V ≤ V_{DD} < 1.8 V			120			ns
	t_{EXHS}, t_{EXLS}				13.7			μs
TI00 to TI07 input high-level width, low-level width	t_{TIH}, t_{TIL}				1/f_{MCK}+10			ns
TO00 to TO07 output frequency	f_{TO}	HS (high-speed main) mode	4.0 V ≤ V_{DD} ≤ 5.5 V				12	MHz
			2.7 V ≤ V_{DD} < 4.0 V				8	MHz
			2.4 V ≤ V_{DD} < 2.7 V				4	MHz
		LV (low-voltage main) mode	1.6 V ≤ V_{DD} ≤ 5.5 V				2	MHz
		LS (low-speed main) mode	1.8 V ≤ V_{DD} ≤ 5.5 V				4	MHz
PCLBUZ0, PCLBUZ1 output frequency	f_{PCL}	HS (high-speed main) mode	4.0 V ≤ V_{DD} ≤ 5.5 V				16	MHz
			2.7 V ≤ V_{DD} < 4.0 V				8	MHz
			2.4 V ≤ V_{DD} < 2.7 V				4	MHz
		LV (low-voltage main) mode	1.8 V ≤ V_{DD} ≤ 5.5 V				4	MHz
			1.6 V ≤ V_{DD} < 1.8 V				2	MHz
		LS (low-speed main) mode	1.8 V ≤ V_{DD} ≤ 5.5 V				4	MHz
Interrupt input high-level width, low-level width	t_{INTH}, t_{INTL}	INTP0 to INTP7	1.6 V ≤ V_{DD} ≤ 5.5 V		1			μs
$\overline{RESET}$ low-level width	t_{RSL}				10			μs

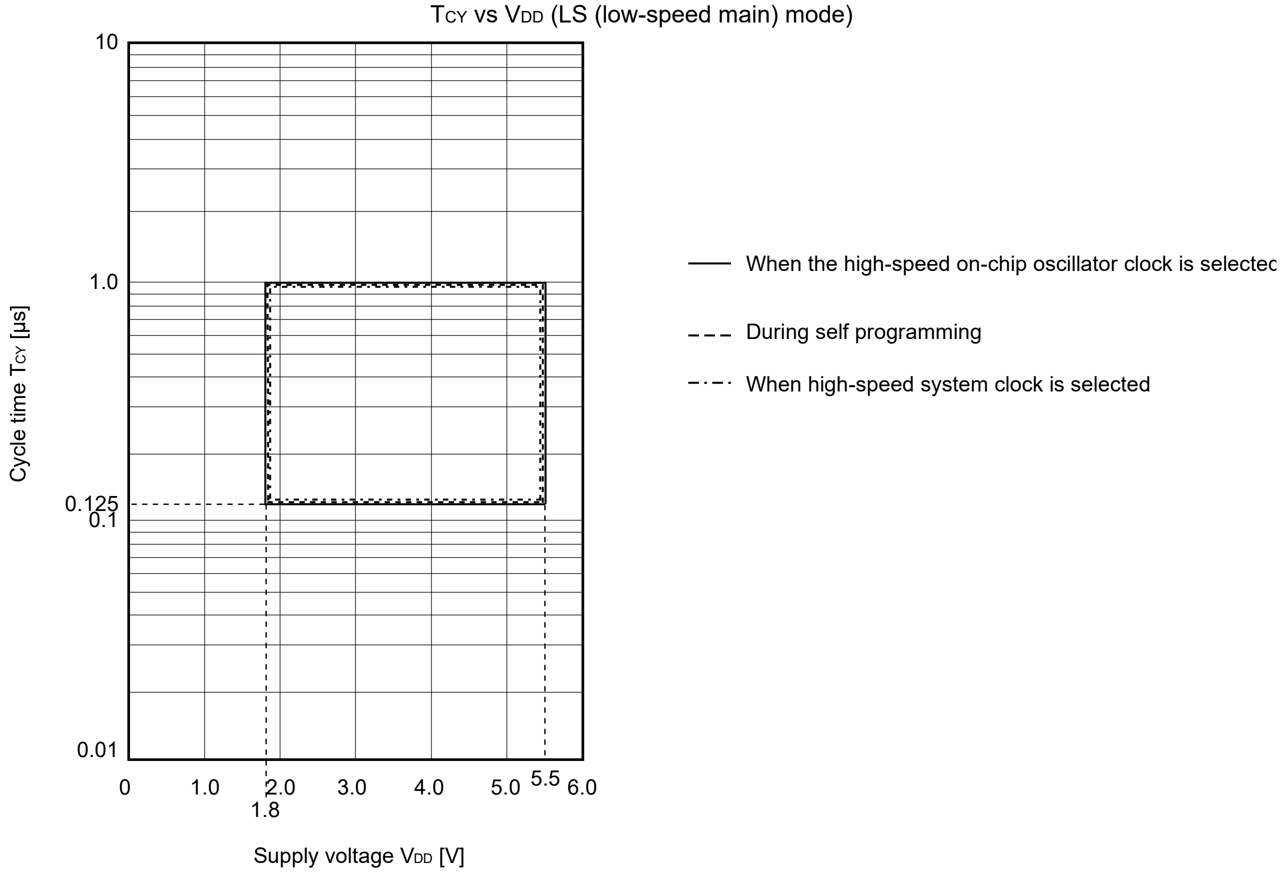
(**Note** and **Remark** are listed on the next page.)

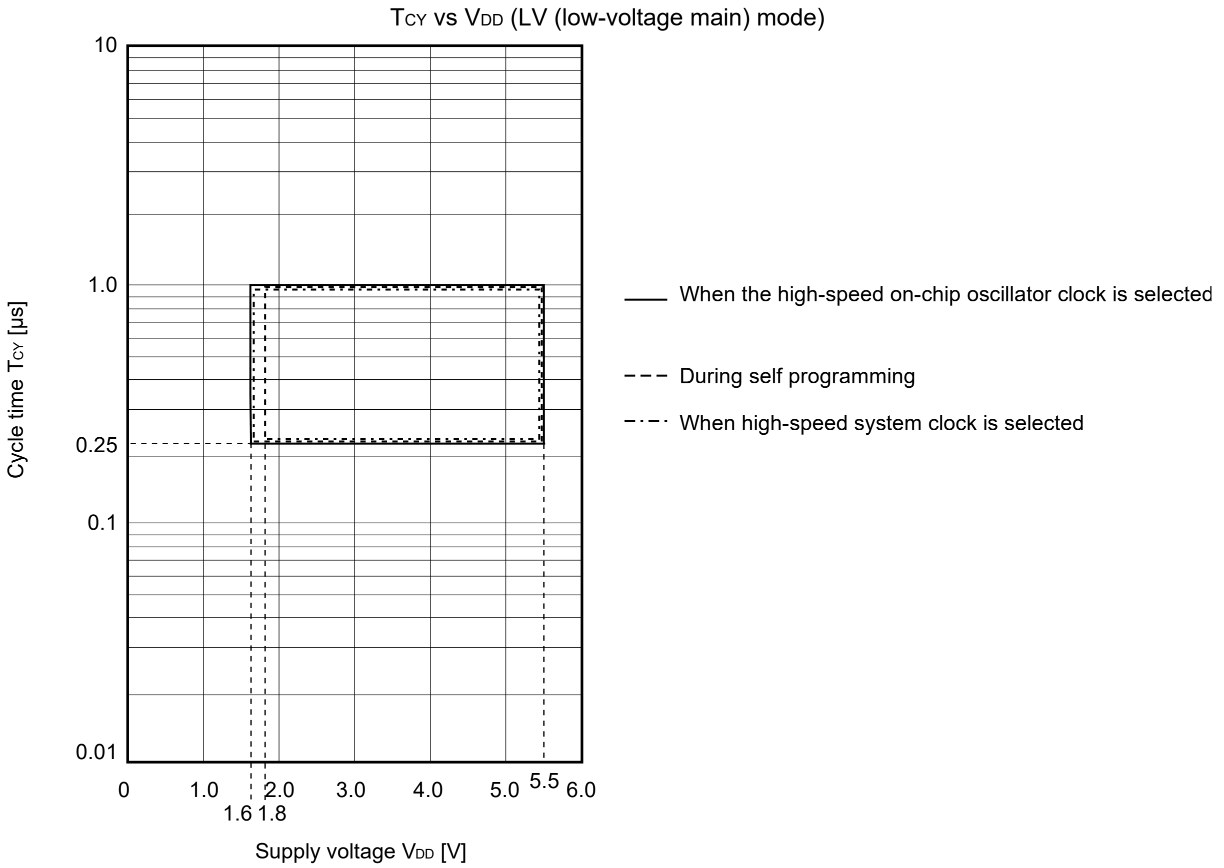
Note Operation is not possible if 1.6 V ≤ V_{DD} < 1.8 V in LV (low-voltage main) mode while the system is operating on the subsystem clock.

Remark f_{MCK}: Timer array unit operation clock frequency
(Operation clock to be set by the CKSmn0, CKSmn1 bits of timer mode register mn (TMRmn)
m: Unit number (m = 0), n: Channel number (n = 0 to 7))

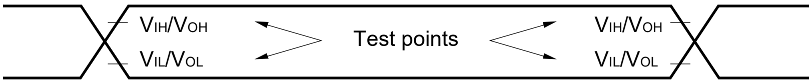
Minimum Instruction Execution Time during Main System Clock Operation



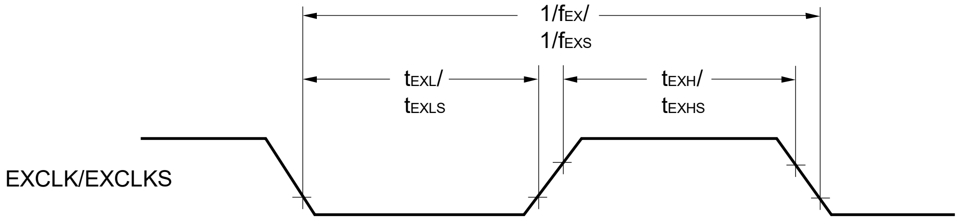

TCY vs VDD (LS (low-speed main) mode)
10
1.0
0.125
0.1
0.01
Cycle time TCY [µs]
0
1.0
2.0
3.0
4.0
5.0
5.5
6.0
1.8
Supply voltage VDD [V]
When the high-speed on-chip oscillator clock is selected
During self programming
When high-speed system clock is selected


TCY vs VDD (LV (low-voltage main) mode)
10
1.0
0.25
0.1
0.01
Cycle time TCY [µs]
0
1.0
2.0
3.0
4.0
5.0
5.5
6.0
1.6
1.8
Supply voltage VDD [V]
When the high-speed on-chip oscillator clock is selected
During self programming
When high-speed system clock is selected

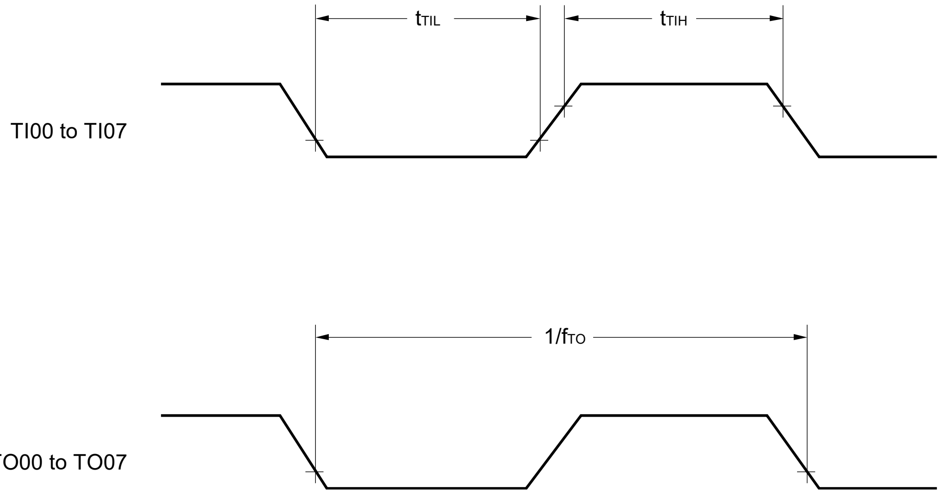
AC Timing Test Points



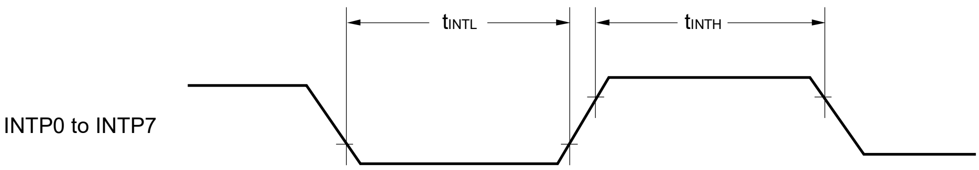
External System Clock Timing



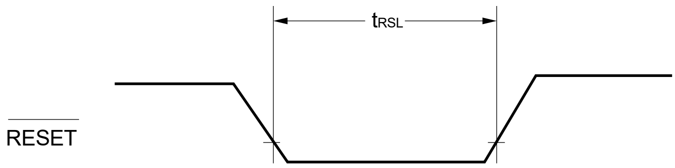
TI/TO Timing



Interrupt Request Input Timing

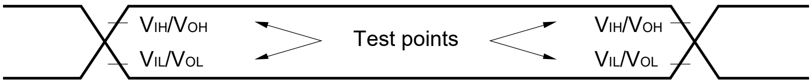


$\overline{\text{RESET}}$ Input Timing



32.5 Peripheral Functions Characteristics

AC Timing Test Points



32.5.1 Serial array unit

(1) During communication at same potential (UART mode)
(T_A = –40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate[Note 1]		2.4 V≤ V_{DD} ≤ 5.5 V		$f_{MCK}/6$		$f_{MCK}/6$		$f_{MCK}/6$	bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$[Note 2]		4.0		1.3		0.6	Mbps
		1.8 V ≤ V_{DD} ≤ 5.5 V		–		$f_{MCK}/6$		$f_{MCK}/6$	bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$[Note 2]		–		1.3		0.6	Mbps
		1.6 V ≤ V_{DD} ≤ 5.5 V		–		–		$f_{MCK}/6$	bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$[Note 2]		–		–		0.6	Mbps

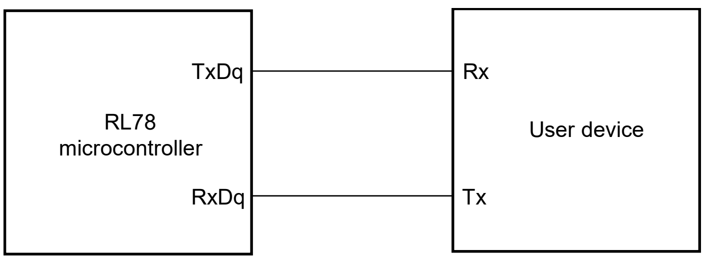
Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:

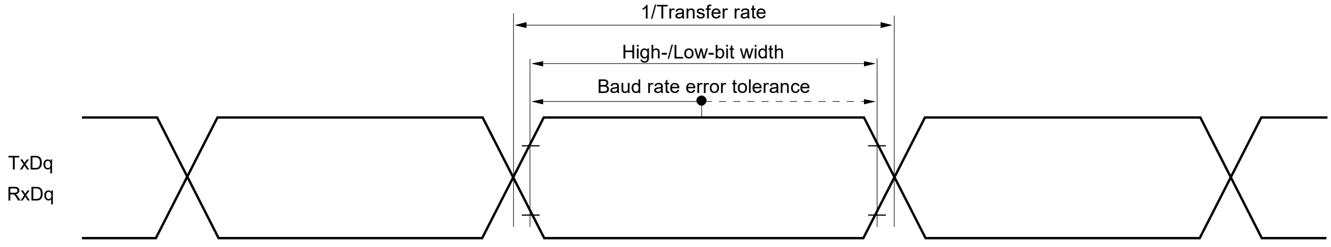
HS (high-speed main) mode: 24 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)
16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)
LS (low-speed main) mode: 8 MHz (1.8 V ≤ V_{DD} ≤ 5.5 V)
LV (low-voltage main) mode: 4 MHz (1.6 V ≤ V_{DD} ≤ 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remarks 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 3)

2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(2) During communication at same potential (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)
(T_A = –40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	2.7 V ≤ V_{DD} ≤ 5.5 V	167[Note 1]		500[Note 1]		1000[Note 1]		ns
		2.4 V ≤ V_{DD} ≤ 5.5 V	250[Note 1]		500[Note 1]		1000[Note 1]		ns
		1.8 V ≤ V_{DD} ≤ 5.5 V	–		500[Note 1]		1000[Note 1]		ns
		1.6 V ≤ V_{DD} ≤ 5.5 V	–		–		1000[Note 1]		ns
SCKp high-/low-level width	t_{KH1}, t_{KL1}	4.0 V ≤ V_{DD} ≤ 5.5 V	t_{KCY1}/2–12		t_{KCY1}/2–50		t_{KCY1}/2–50		ns
		2.7 V ≤ V_{DD} ≤ 5.5 V	t_{KCY1}/2–18		t_{KCY1}/2–50		t_{KCY1}/2–50		ns
		2.4 V ≤ V_{DD} ≤ 5.5 V	t_{KCY1}/2–38		t_{KCY1}/2–50		t_{KCY1}/2–50		ns
		1.8 V ≤ V_{DD} ≤ 5.5 V	–		t_{KCY1}/2–50		t_{KCY1}/2–50		ns
		1.6 V ≤ V_{DD} ≤ 5.5 V	–		–		t_{KCY1}/2–100		ns
SIp setup time (to SCKp↑)[Note 2]	t_{SIK1}	2.7 V ≤ V_{DD} ≤ 5.5 V	44		110		110		ns
		2.4 V ≤ V_{DD} ≤ 5.5 V	75		110		110		ns
		1.8 V ≤ V_{DD} ≤ 5.5 V	–		110		110		ns
		1.6 V ≤ V_{DD} ≤ 5.5 V	–		–		220		ns
SIp hold time (from SCKp↑)[Note 3]	t_{KSI1}	2.4 V ≤ V_{DD} ≤ 5.5 V	19		19		19		ns
		1.8 V ≤ V_{DD} ≤ 5.5 V	–		19		19		ns
		1.6 V ≤ V_{DD} ≤ 5.5 V	–		–		19		ns
Delay time from SCKp↓ to SOp output[Note 4]	t_{KSO1}	C = 30 pF[Note 5], 2.4 V ≤ V_{DD} ≤ 5.5 V		25		25		25	ns
		C = 30 pF[Note 5], 1.8 V ≤ V_{DD} ≤ 5.5 V		–		25		25	ns
		C = 30 pF[Note 5], 1.6 V ≤ V_{DD} ≤ 5.5 V		–		–		25	ns

Notes 1. The value must also be equal to or more than 4/f_{CLK} for CSI00.

2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

5. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM numbers (g = 0, 1)

2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

(3) During communication at same potential (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)
(T_A = –40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time[Note 5]	t_{KCY2}	4.0 V ≤ V_{DD} ≤ 5.5 V	f_{MCK} > 20 MHz	8/f_{MCK}		–		–		ns
			f_{MCK} ≤ 20 MHz	6/f_{MCK}		6/f_{MCK}		6/f_{MCK}		ns
		2.7 V ≤ V_{DD} ≤ 5.5 V	f_{MCK} > 16 MHz	8/f_{MCK}		–		–		ns
			f_{MCK} ≤ 16 MHz	6/f_{MCK}		6/f_{MCK}		6/f_{MCK}		ns
		2.4 V ≤ V_{DD} ≤ 5.5 V		6/f_{MCK} and 500		6/f_{MCK}		6/f_{MCK}		ns
		1.8 V ≤ V_{DD} ≤ 5.5 V		–		6/f_{MCK}		6/f_{MCK}		ns
		1.6 V ≤ V_{DD} ≤ 5.5 V		–		–		6/f_{MCK}		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	4.0 V ≤ V_{DD} ≤ 5.5 V		t_{KCY2}/2–7		t_{KCY2}/2–7		t_{KCY2}/2–7		ns
		2.7 V ≤ V_{DD} ≤ 5.5 V		t_{KCY2}/2–8		t_{KCY2}/2–8		t_{KCY2}/2–8		ns
		2.4 V ≤ V_{DD} ≤ 5.5 V		t_{KCY2}/2–18		t_{KCY2}/2–18		t_{KCY2}/2–18		ns
		1.8 V ≤ V_{DD} ≤ 5.5 V		–		t_{KCY2}/2–18		t_{KCY2}/2–18		ns
		1.6 V ≤ V_{DD} ≤ 5.5 V		–		–		t_{KCY2}/2–66		ns
SIp setup time (to SCKp↑)[Note 1]	t_{SIK2}	2.7 V ≤ V_{DD} ≤ 5.5 V		1/f_{MCK}+20		1/f_{MCK}+30		1/f_{MCK}+30		ns
		2.4 V ≤ V_{DD} ≤ 5.5 V		1/f_{MCK}+30		1/f_{MCK}+30		1/f_{MCK}+30		ns
		1.8 V ≤ V_{DD} ≤ 5.5 V		–		1/f_{MCK}+30		1/f_{MCK}+30		ns
		1.6 V ≤ V_{DD} ≤ 5.5 V		–		–		1/f_{MCK}+40		ns
SIp hold time (from SCKp↑)[Note 2]	t_{KSI2}	2.4 V ≤ V_{DD} ≤ 5.5 V		1/f_{MCK}+31		1/f_{MCK}+31		1/f_{MCK}+31		ns
		1.8 V ≤ V_{DD} ≤ 5.5 V		–		1/f_{MCK}+31		1/f_{MCK}+31		ns
		1.6 V ≤ V_{DD} ≤ 5.5 V		–		–		1/f_{MCK}+250		ns
Delay time from SCKp↓ to SOp output[Note 3]	t_{KSO2}	C = 30 pF[Note 4]	2.7 V ≤ V_{DD} ≤ 5.5 V		2/f_{MCK}+44		2/f_{MCK}+110		2/f_{MCK}+110	ns
			2.4 V ≤ V_{DD} ≤ 5.5 V		2/f_{MCK}+75		2/f_{MCK}+110		2/f_{MCK}+110	ns
			1.8 V ≤ V_{DD} ≤ 5.5 V		–		2/f_{MCK}+110		2/f_{MCK}+110	ns
			1.6 V ≤ V_{DD} ≤ 5.5 V		–		–		2/f_{MCK}+220	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

4. C is the load capacitance of the SOp output lines.

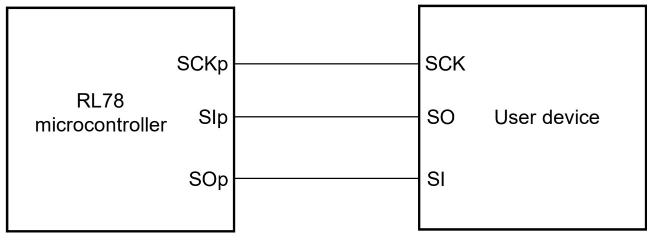
5. Transfer rate in SNOOZE mode: MAX. 1 Mbps

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

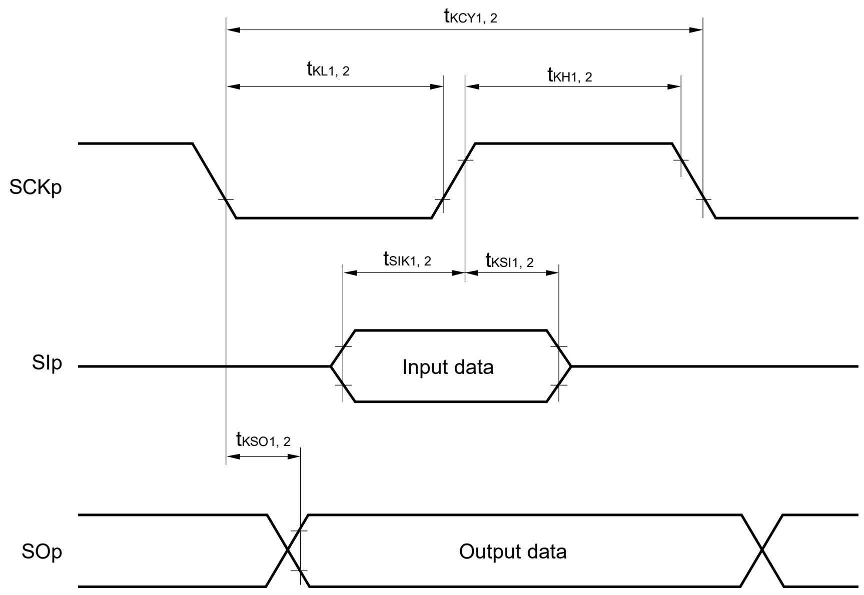
Remarks 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM number (g = 0, 1)

2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

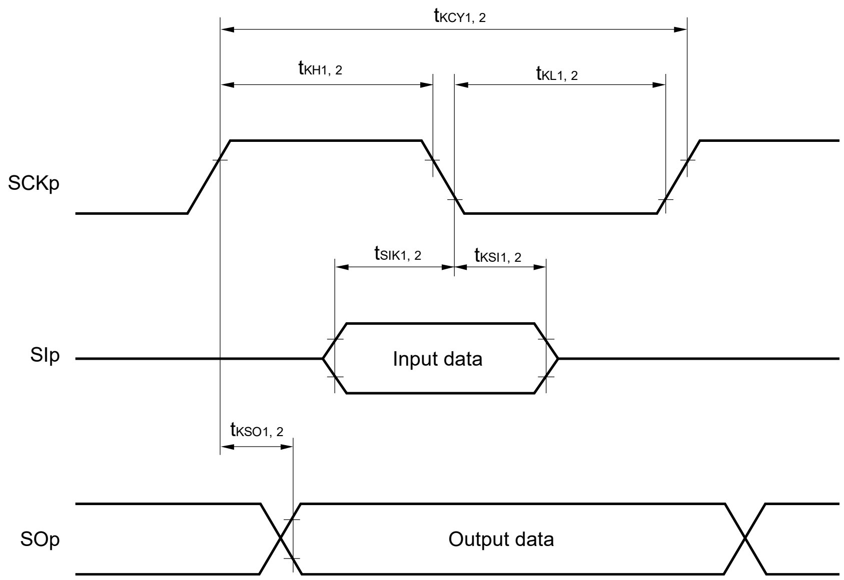
Simplified SPI (CSI) mode connection diagram (during communication at same potential)



Simplified SPI (CSI) mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00)

2. m: Unit number, n: Channel number (mn = 00)

(4) During communication at same potential (simplified I^2C mode)
(T_A = –40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	f_{SCL}	2.7 V ≤ V_{DD} ≤ 5.5 V, C_b = 50 pF, R_b = 2.7 kΩ		1000 Note 1		400 Note 1		400 Note 1	kHz
		1.8 V (2.4 V Note 3) ≤ V_{DD} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ		400 Note 1		400 Note 1		400 Note 1	kHz
		1.8 V (2.4 V Note 3) ≤ V_{DD} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ		300 Note 1		300 Note 1		300 Note 1	kHz
		1.6 V ≤ V_{DD} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ		–		–		250 Note 1	kHz
Hold time when SCLr = "L"	t_{LOW}	2.7 V ≤ V_{DD} ≤ 5.5 V, C_b = 50 pF, R_b = 2.7 kΩ	475		1150		1150		ns
		1.8 V (2.4 V Note 3) ≤ V_{DD} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ	1150		1150		1150		ns
		1.8 V (2.4 V Note 3) ≤ V_{DD} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ	1550		1550		1550		ns
		1.6 V ≤ V_{DD} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	–		–		1850		ns
Hold time when SCLr = "H"	t_{HIGH}	2.7 V ≤ V_{DD} ≤ 5.5 V, C_b = 50 pF, R_b = 2.7 kΩ	475		1150		1150		ns
		1.8 V (2.4 V Note 3) ≤ V_{DD} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ	1150		1150		1150		ns
		1.8 V (2.4 V Note 3) ≤ V_{DD} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ	1550		1550		1550		ns
		1.6 V ≤ V_{DD} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	–		–		1850		ns
Data setup time (reception)	$t_{SU:DAT}$	2.7 V ≤ V_{DD} ≤ 5.5 V, C_b = 50 pF, R_b = 2.7 kΩ	$1/f_{MCK}$+ 85 Note 2		$1/f_{MCK}$+ 145 Note 2		$1/f_{MCK}$+ 145 Note 2		ns
		1.8 V (2.4 V Note 3) ≤ V_{DD} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ	$1/f_{MCK}$+ 145 Note 2		$1/f_{MCK}$+ 145 Note 2		$1/f_{MCK}$+ 145 Note 2		ns
		1.8 V (2.4 V Note 3) ≤ V_{DD} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ	$1/f_{MCK}$+ 230 Note 2		$1/f_{MCK}$+ 230 Note 2		$1/f_{MCK}$+ 230 Note 2		ns
		1.6 V ≤ V_{DD} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	–		–		$1/f_{MCK}$+ 290 Note 2		ns
Data hold time (transmission)	$t_{HD:DAT}$	2.7 V ≤ V_{DD} ≤ 5.5 V, C_b = 50 pF, R_b = 2.7 kΩ	0	305	0	305	0	305	ns
		1.8 V (2.4 V Note 3) ≤ V_{DD} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ	0	355	0	355	0	355	ns
		1.8 V (2.4 V Note 3) ≤ V_{DD} < 2.7 V, C_b = 100 pF, R_b = 5 kΩ	0	405	0	405	0	405	ns
		1.6 V ≤ V_{DD} < 1.8 V, C_b = 100 pF, R_b = 5 kΩ	–	–	–	–	0	405	ns

(**Notes**, **Caution**, and **Remarks** are listed on the next page.)

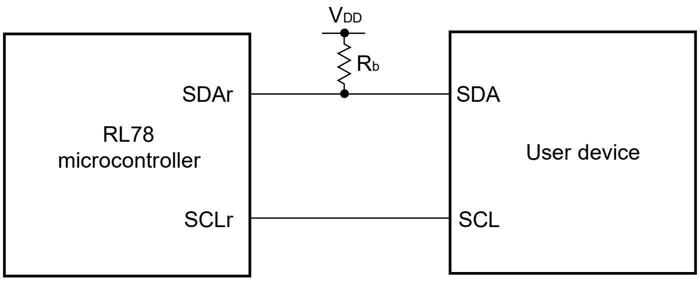
Notes 1. The value must also be equal to or less than $f_{MCK}/4$.

2. Set the f_{MCK} value to keep the hold time of SCLr = "L" and SCLr = "H".

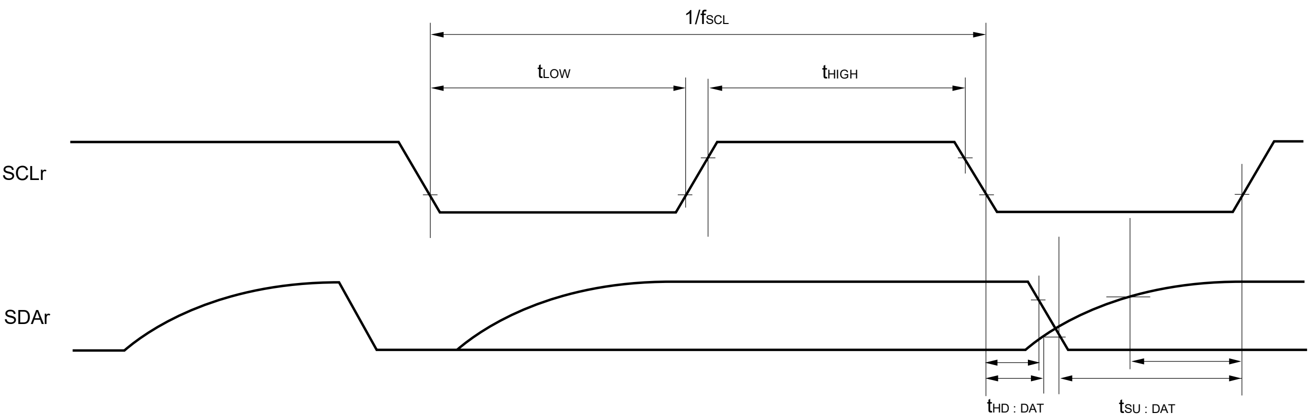
3. Condition in the HS (high-speed main) mode

Caution Select the normal input buffer and the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



Remarks 1. R_b[Ω]: Communication line (SDAr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance

2. r: IIC number (r = 00, 10), g: PIM and POM number (g = 0, 1)

3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0), n: Channel number (n = 0, 2), mn = 00, 02)

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)
(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Reception	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V		f_{MCK}/6 Note 1		f_{MCK}/6 Note 1		f_{MCK}/6 Note 1	bps
			Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 3		4.0		1.3		0.6	Mbps
			2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		f_{MCK}/6 Note 1		f_{MCK}/6 Note 1		f_{MCK}/6 Note 1	bps
			Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 3		4.0		1.3		0.6	Mbps
			1.8 V (2.4 V Note 4) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		f_{MCK}/6 Note s1, 2		f_{MCK}/6 Notes 1, 2		f_{MCK}/6 Notes 1, 2	bps
			Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 3		4.0		1.3		0.6	Mbps

Notes 1. Transfer rate in SNOOZE mode is 4800 bps only.

2. Use it with V_{DD} ≥ V_b.

3. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:

HS (high-speed main) mode: 24 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)
16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)
LS (low-speed main) mode: 8 MHz (1.8 V ≤ V_{DD} ≤ 5.5 V)
LV (low-voltage main) mode: 4 MHz (1.6 V ≤ V_{DD} ≤ 5.5 V)

4. Condition in the HS (high-speed main) mode

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remarks 1. V_b[V]: Communication line voltage

2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 3)

3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)
(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode MIN.	HS (high-speed main) Mode MAX.	LS (low-speed main) Mode MIN.	LS (low-speed main) Mode MAX.	LV (low-voltage main) Mode MIN.	LV (low-voltage main) Mode MAX.	Unit
Transfer rate		Trans mission	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V		**Note 1**		**Note 1**		**Note 1**	bps
			Theoretical value of the maximum transfer rate (C_b = 50 pF, R_b = 1.4 kΩ, V_b = 2.7 V)		2.8 Note 2		2.8 Note 2		2.8 Note 2	Mbps
			2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		**Note 3**		**Note 3**		**Note 3**	bps
			Theoretical value of the maximum transfer rate (C_b = 50 pF, R_b = 2.7 kΩ, V_b = 2.3 V)		1.2 Note 4		1.2 Note 4		1.2 Note 4	Mbps
			1.8 V (2.4 V Note 8) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		**Notes 5, 6**		**Notes 5, 6**		**Notes 5, 6**	bps
			Theoretical value of the maximum transfer rate (C_b = 50 pF, R_b = 5.5 kΩ, V_b = 1.6 V)		0.43 Note 7		0.43 Note 7		0.43 Note 7	Mbps

Notes 1. The smaller maximum transfer rate derived by using $f_{MCK}/6$ or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V ≤ V_{DD} ≤ 5.5 V and 2.7 V ≤ V_b ≤ 4.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

2. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 1** above to calculate the maximum transfer rate under conditions of the customer.

3. The smaller maximum transfer rate derived by using $f_{MCK}/6$ or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V ≤ V_{DD} < 4.0 V and 2.3 V ≤ V_b ≤ 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

4. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 3** above to calculate the maximum transfer rate under conditions of the customer.

5. Use it with V_{DD} ≥ V_b.

Notes 6. The smaller maximum transfer rate derived by using $f_{MCK}/6$ or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 1.8 V (2.4 V**Note 8**) ≤ V_{DD} < 3.3 V and 1.6 V ≤ V_b ≤ 2.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

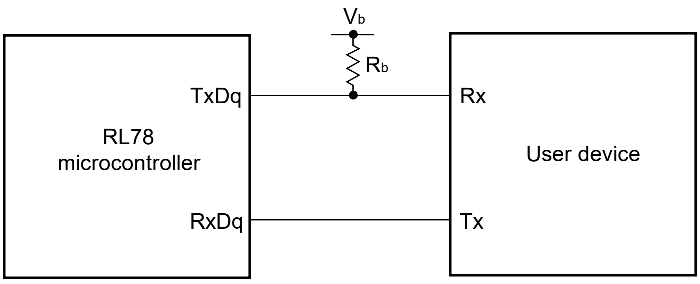
* This value is the theoretical value of the relative difference between the transmission and reception sides.

7. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 6** above to calculate the maximum transfer rate under conditions of the customer.

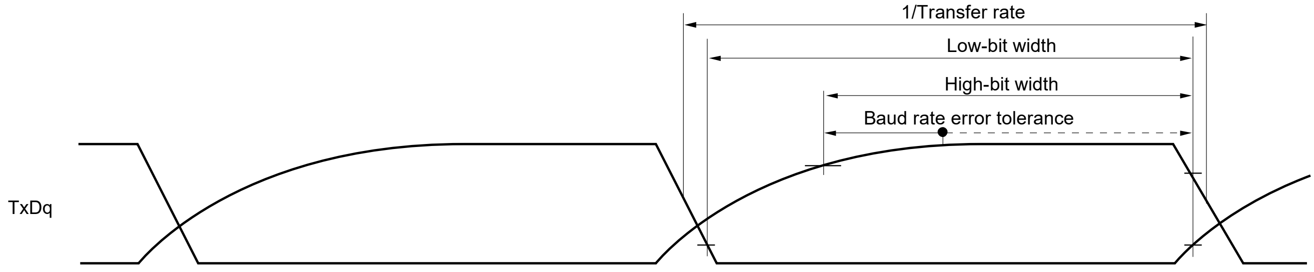
8. Condition in the HS (high-speed main) mode

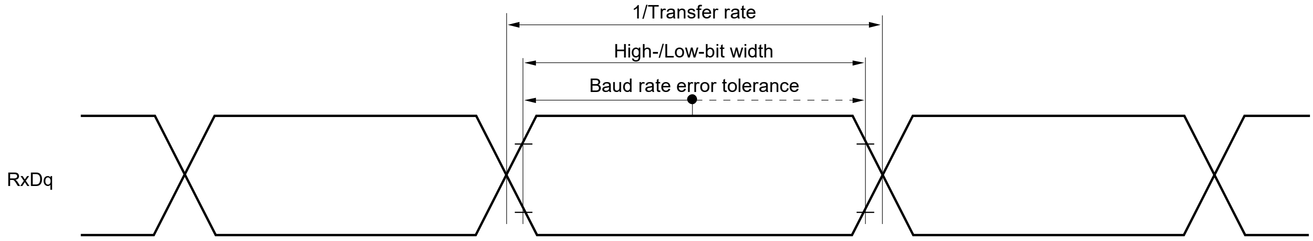
Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





Remarks 1. R_b[Ω]: Communication line (TxDq) pull-up resistance, C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage

2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 3)

3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(6) Communication at different potential (2.5 V, 3 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)
(T_A = –40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	t_{KCY1} ≥ 2/f_{CLK}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ	200		1150		1150		ns
			2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ	300		1150		1150		ns
SCKp high-level width	t_{KH1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		t_{KCY1}/2 – 50		t_{KCY1}/2 – 50		t_{KCY1}/2 – 50		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		t_{KCY1}/2 – 120		t_{KCY1}/2 – 120		t_{KCY1}/2 – 120		ns
SCKp low-level width	t_{KL1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		t_{KCY1}/2 – 7		t_{KCY1}/2 – 50		t_{KCY1}/2 – 50		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		t_{KCY1}/2 – 10		t_{KCY1}/2 – 50		t_{KCY1}/2 – 50		ns
SIp setup time (to SCKp↑)Note 1	t_{SIK1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		58		479		479		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		121		479		479		ns
SIp hold time (from SCKp↑)Note 1	t_{KSI1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		10		10		10		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		10		10		10		ns
Delay time from SCKp↓ to SOp outputNote 1	t_{KSO1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ			60		60		60	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ			130		130		130	ns
SIp setup time (to SCKp↓)Note 2	t_{SIK1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		23		110		110		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		33		110		110		ns
SIp hold time (from SCKp↓)Note 2	t_{KSI1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		10		10		10		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		10		10		10		ns
Delay time from SCKp↑ to SOp outputNote 2	t_{KSO1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ			10		10		10	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ			10		10		10	ns

(**Notes**, **Caution** and **Remarks** are listed on the next page.)

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remarks 1. R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage

2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 0, 1)

3. f_{MCK}: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

4. This specification is valid only when CSI00’s peripheral I/O redirect function is not used.

(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output) (1/2)

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	t_{KCY1} ≥ 4/f_{CLK}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	300		1150		1150		ns
			2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	500		1150		1150		ns
			1.8 V (2.4 V[Note 1]) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 1.8 V[Note 2], C_b = 30 pF, R_b = 5.5 kΩ	1150		1150		1150		ns
SCKp high-level width	t_{KH1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		t_{KCY1}/2 – 75		t_{KCY1}/2 – 75		t_{KCY1}/2 – 75		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 – 170		t_{KCY1}/2 – 170		t_{KCY1}/2 – 170		ns
		1.8 V (2.4 V[Note 1]) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V[Note 2], C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 – 458		t_{KCY1}/2 – 458		t_{KCY1}/2 – 458		ns
SCKp low-level width	t_{KL1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		t_{KCY1}/2 – 12		t_{KCY1}/2 – 50		t_{KCY1}/2 – 50		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 – 18		t_{KCY1}/2 – 50		t_{KCY1}/2 – 50		ns
		1.8 V (2.4 V[Note 1]) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V[Note 2], C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 – 50		t_{KCY1}/2 – 50		t_{KCY1}/2 – 50		ns
SIp setup time (to SCKp↑)[Note 3]	t_{SIK1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		81		479		479		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		177		479		479		ns
		1.8 V (2.4 V[Note 1]) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V[Note 2], C_b = 30 pF, R_b = 5.5 kΩ		479		479		479		ns
SIp hold time (from SCKp↑)[Note 3]	t_{KSI1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		19		19		19		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		19		19		19		ns
		1.8 V (2.4 V[Note 1]) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V[Note 2], C_b = 30 pF, R_b = 5.5 kΩ		19		19		19		ns
Delay time from SCKp↓ to SOp output[Note 3]	t_{KSO1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ			100		100		100	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ			195		195		195	ns
		1.8 V (2.4 V[Note 1]) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V[Note 2], C_b = 30 pF, R_b = 5.5 kΩ			483		483		483	ns

(**Notes** and **Caution** are listed on the next page, and **Remarks** are listed on the page after the next page.)

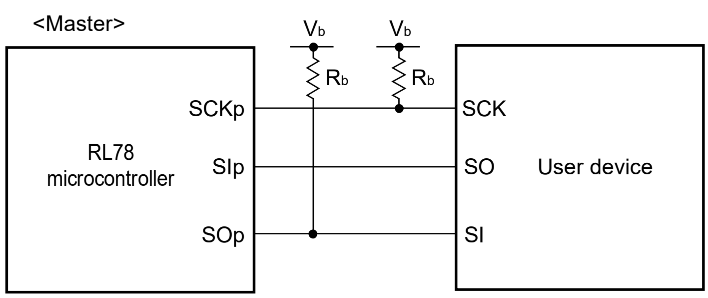
(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output) (2/2)
(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓)Note 4	t_{SIK1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	44		110		110		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	44		110		110		ns
		1.8 V (2.4 V Note 1) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 30 pF, R_b = 5.5 kΩ	110		110		110		ns
SIp hold time (from SCKp↓)Note 4	t_{KSI1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	19		19		19		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	19		19		19		ns
		1.8 V (2.4 V Note 1) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 30 pF, R_b = 5.5 kΩ	19		19		19		ns
Delay time from SCKp↑ to SOp outputNote 4	t_{KSO1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		25		25		25	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		25		25		25	ns
		1.8 V (2.4 V Note 1) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 30 pF, R_b = 5.5 kΩ		25		25		25	ns

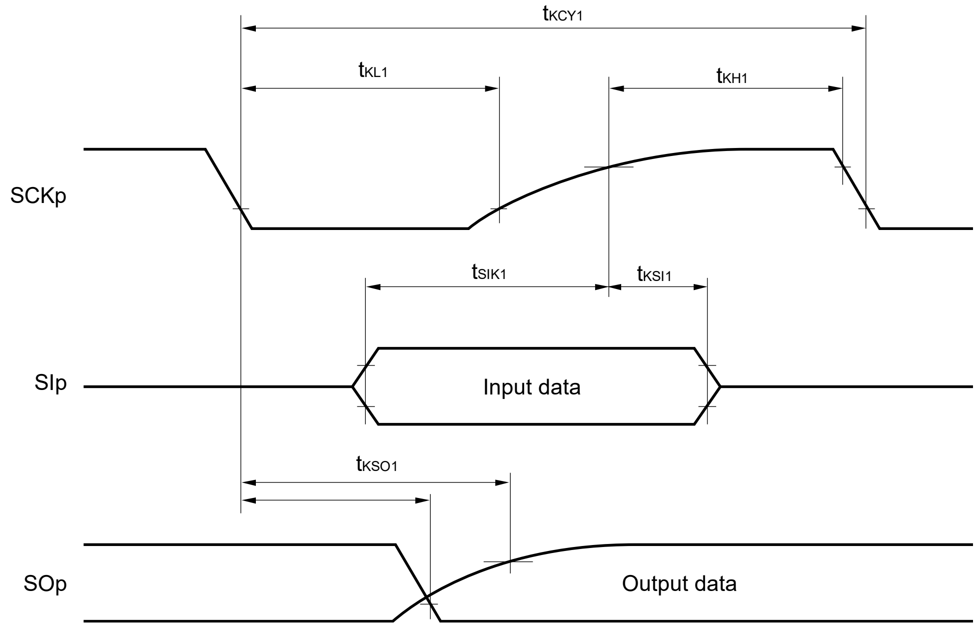
Notes 1. Condition in HS (high-speed main) mode
2. Use it with V_{DD} ≥ V_b.
3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
4. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

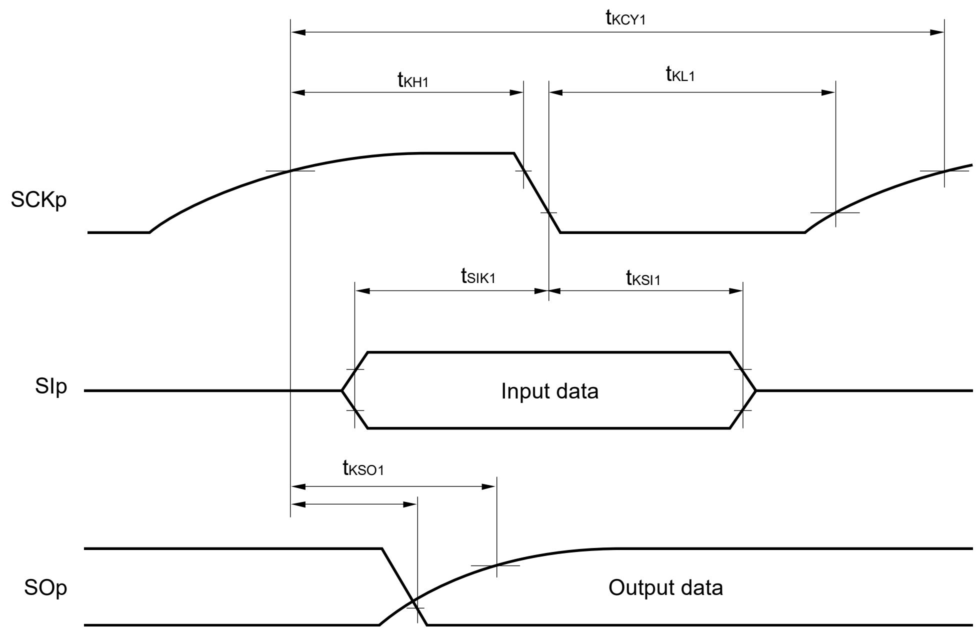
Simplified SPI (CSI) mode connection diagram (during communication at different potential)



Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage

2. p: CSI number (p = 00), m: Unit number , n: Channel number (mn = 00), g: PIM and POM number (g = 0, 1)

3. f_{MCK}: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)
(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time[Note 1]	t_{KCY2}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V	20 MHz < f_{MCK}	12/f_{MCK}		–		–		ns
			8 MHz < f_{MCK} ≤ 20 MHz	10/f_{MCK}		–		–		ns
			4 MHz < f_{MCK} ≤ 8 MHz	8/f_{MCK}		16/f_{MCK}		–		ns
			f_{MCK} ≤ 4 MHz	6/f_{MCK}		10/f_{MCK}		10/f_{MCK}		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V	20 MHz < f_{MCK}	16/f_{MCK}		–		–		ns
			16 MHz < f_{MCK} ≤ 20 MHz	14/f_{MCK}		–		–		ns
			8 MHz < f_{MCK} ≤ 16 MHz	12/f_{MCK}		–		–		ns
			4 MHz < f_{MCK} ≤ 8 MHz	8/f_{MCK}		16/f_{MCK}		–		ns
			f_{MCK} ≤ 4 MHz	6/f_{MCK}		10/f_{MCK}		10/f_{MCK}		ns
		1.8 V (2.4 V[Note 2]) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V[Note 3]	20 MHz < f_{MCK}	36/f_{MCK}		–		–		ns
			16 MHz < f_{MCK} ≤ 20 MHz	32/f_{MCK}		–		–		ns
			8 MHz < f_{MCK} ≤ 16 MHz	26/f_{MCK}		–		–		ns
			4 MHz < f_{MCK} ≤ 8 MHz	16/f_{MCK}		16/f_{MCK}		–		ns
			f_{MCK} ≤ 4 MHz	10/f_{MCK}		10/f_{MCK}		10/f_{MCK}		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V		t_{KCY2}/2 – 12		t_{KCY2}/2 – 50		t_{KCY2}/2 – 50		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		t_{KCY2}/2 – 18		t_{KCY2}/2 – 50		t_{KCY2}/2 – 50		ns
		1.8 V (2.4 V[Note 2]) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V[Note 3]		t_{KCY2}/2 – 50		t_{KCY2}/2 – 50		t_{KCY2}/2 – 50		ns
SIp setup time (to SCKp↑)[Note 4]	t_{SIK2}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V		1/f_{MCK} + 20		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		1/f_{MCK} + 20		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		1.8 V (2.4 V[Note 2]) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V[Note 3]		1/f_{MCK} + 30		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
SIp hold time (from SCKp↑)[Note 5]	t_{KSI2}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V		1/f_{MCK} + 31		1/f_{MCK} + 31		1/f_{MCK} + 31		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		1/f_{MCK} + 31		1/f_{MCK} + 31		1/f_{MCK} + 31		ns
		1.8 V (2.4 V[Note 2]) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V[Note 3]		1/f_{MCK} + 31		1/f_{MCK} + 31		1/f_{MCK} + 31		ns
Delay time from SCKp↓ to SOp output[Note 6]	t_{KSO2}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ			2/f_{MCK} + 120		2/f_{MCK} + 573		2/f_{MCK} + 573	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ			2/f_{MCK} + 214		2/f_{MCK} + 573		2/f_{MCK} + 573	ns
		1.8 V (2.4 V[Note 2]) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V[Note 3], C_b = 30 pF, R_b = 5.5 kΩ			2/f_{MCK} + 573		2/f_{MCK} + 573		2/f_{MCK} + 573	ns

(**Notes** and **Caution** are listed on the next page, and **Remarks** are listed on the page after the next page.)

Notes 1. Transfer rate in SNOOZE mode: MAX. 1 Mbps

2. Condition in HS (high-speed main) mode

3. Use it with $V_{DD} \geq V_b$.

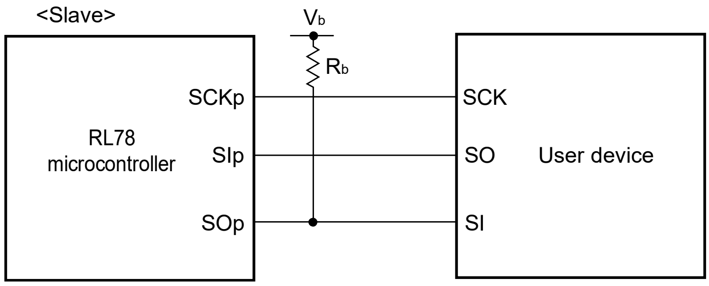
4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

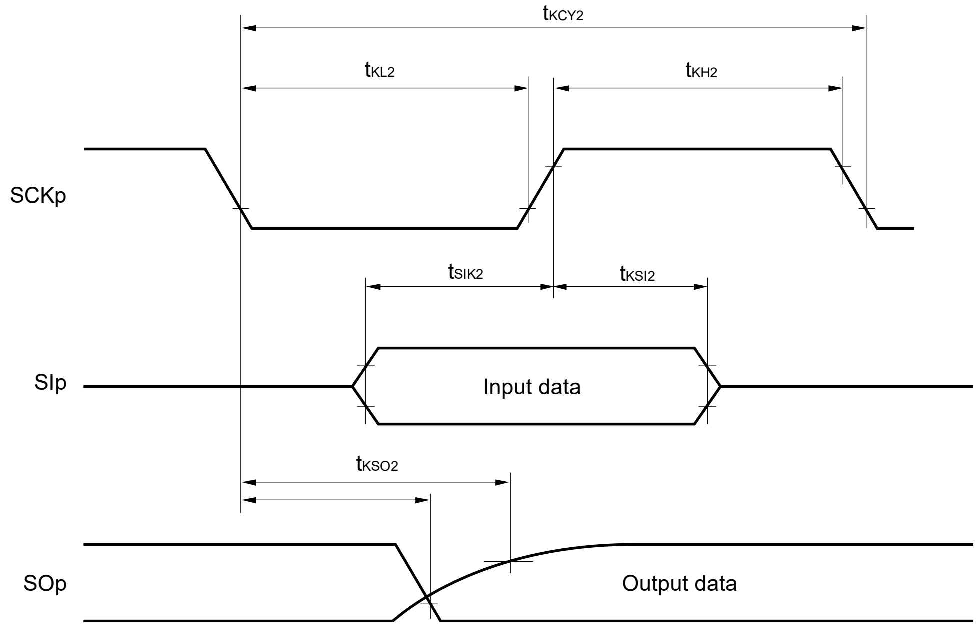
6. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (V_{DD} tolerance) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

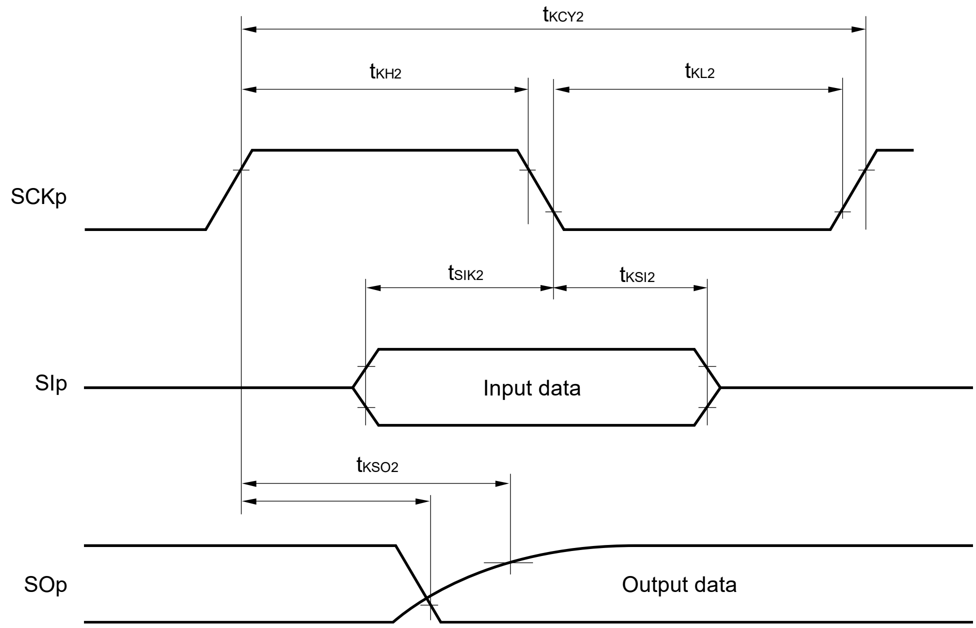
Simplified SPI (CSI) mode connection diagram (during communication at different potential)



Simplified SPI (CSI) mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. R_b[Ω]: Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, V_b[V]: Communication line voltage

2. p: CSI number (p = 00), m: Unit number, n: Channel number (mn = 00), g: PIM and POM number (g = 0, 1)

3. f_{MCK}: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn) m: Unit number, n: Channel number (mn = 00))

(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (1/2)
(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	f_{SCL}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 50 pF, R_b = 2.7 kΩ		1000 Note 1		300 Note 1		300 Note 1	kHz
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ		1000 Note 1		300 Note 1		300 Note 1	kHz
		4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ		400 Note 1		300 Note 1		300 Note 1	kHz
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ		400 Note 1		300 Note 1		300 Note 1	kHz
		1.8 V (2.4 V Note 2) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 100 pF, R_b = 5.5 kΩ		300 Note 1		300 Note 1		300 Note 1	kHz
Hold time when SCLr = "L"	t_{LOW}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 50 pF, R_b = 2.7 kΩ	475		1550		1550		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	475		1550		1550		ns
		4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	1150		1550		1550		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	1150		1550		1550		ns
		1.8 V (2.4 V Note 2) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 100 pF, R_b = 5.5 kΩ	1550		1550		1550		ns
Hold time when SCLr = "H"	t_{HIGH}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 50 pF, R_b = 2.7 kΩ	245		610		610		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	200		610		610		ns
		4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	675		610		610		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	600		610		610		ns
		1.8 V (2.4 V Note 2) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 100 pF, R_b = 5.5 kΩ	610		610		610		ns

(**Notes** and **Caution** are listed on the next page, and **Remarks** are listed on the page after the next page.)

(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (2/2)
(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

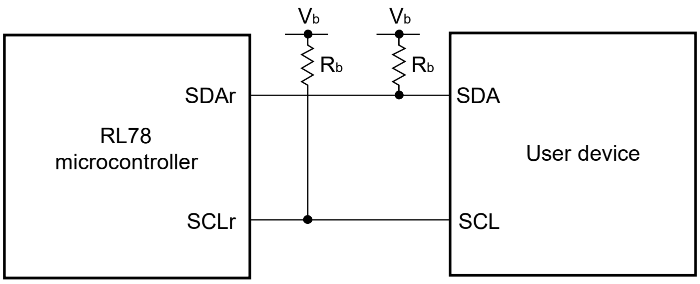
Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	$t_{SU:DAT}$	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 50 pF, R_b = 2.7 kΩ	1/f_{MCK}+ 135 Note 4		1/f_{MCK}+ 190 Note 4		1/f_{MCK}+ 190 Note 4		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	1/f_{MCK}+ 135 Note 4		1/f_{MCK}+ 190 Note 4		1/f_{MCK}+ 190 Note 4		ns
		4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	1/f_{MCK}+ 190 Note 4		1/f_{MCK}+ 190 Note 4		1/f_{MCK}+ 190 Note 4		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	1/f_{MCK}+ 190 Note 4		1/f_{MCK}+ 190 Note 4		1/f_{MCK}+ 190 Note 4		ns
		1.8 V (2.4 V Note 2) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 100 pF, R_b = 5.5 kΩ	1/f_{MCK}+ 190 Note 4		1/f_{MCK}+ 190 Note 4		1/f_{MCK}+ 190 Note 4		ns
Data hold time (transmission)	$t_{HD:DAT}$	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 50 pF, R_b = 2.7 kΩ	0	305	0	305	0	305	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	0	305	0	305	0	305	ns
		4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	0	355	0	355	0	355	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	0	355	0	355	0	355	ns
		1.8 V (2.4 V Note 2) ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 3, C_b = 100 pF, R_b = 5.5 kΩ	0	405	0	405	0	405	ns

Notes 1. The value must also be equal to or less than f_{MCK}/4.
2. Condition in HS (high-speed main) mode
3. Use it with V_{DD} ≥ V_b.
4. Set the f_{MCK} value to keep the hold time of SCLr = "L" and SCLr = "H".

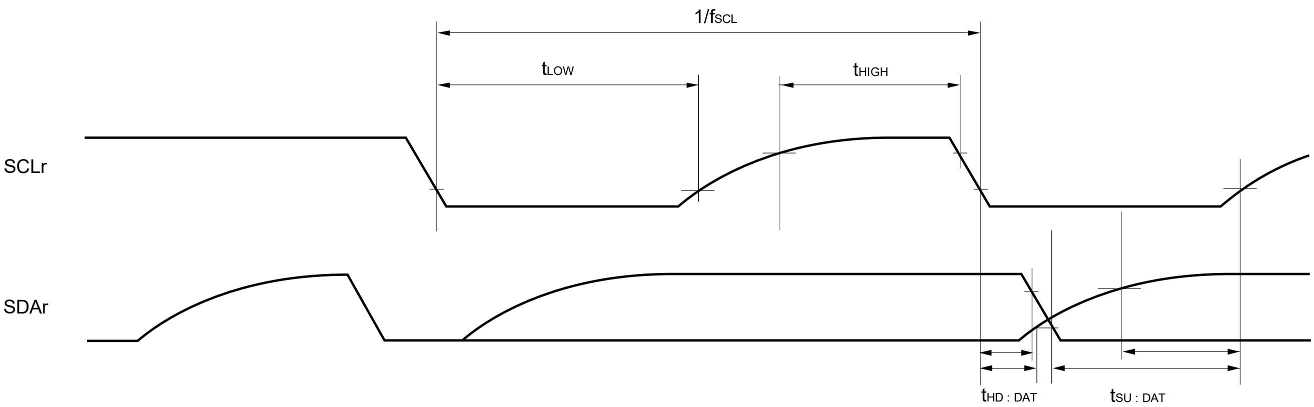
Caution Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



Remarks 1. R_b[Ω]: Communication line (SDAr, SCLr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance, V_b[V]: Communication line voltage

2. r: IIC number (r = 00, 10), g: PIM, POM number (g = 0, 1)

3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number, n: Channel number (mn = 00, 02))

32.5.2 Serial interface IICA

(1) I²C standard mode (1/2)

(T_A = –40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f_{SCL}	Normal mode: f_{CLK} ≥ 1 MHz	2.7 V ≤ V_{DD} ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.8 V (2.4 V Note 3) ≤ V_{DD} ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.6 V ≤ V_{DD} ≤ 5.5 V	–	–	–	–	0	100	kHz
Setup time of restart condition	$t_{SU:STA}$	2.7 V ≤ V_{DD} ≤ 5.5 V		4.7		4.7		4.7		μs
		1.8 V (2.4 V Note 3) ≤ V_{DD} ≤ 5.5 V		4.7		4.7		4.7		μs
		1.6 V ≤ V_{DD} ≤ 5.5 V		–	–	–	–	4.7		μs
Hold time Note 1	$t_{HD:STA}$	2.7 V ≤ V_{DD} ≤ 5.5 V		4.0		4.0		4.0		μs
		1.8 V (2.4 V Note 3) ≤ V_{DD} ≤ 5.5 V		4.0		4.0		4.0		μs
		1.6 V ≤ V_{DD} ≤ 5.5 V		–	–	–	–	4.0		μs
Hold time when SCLA0 = "L"	t_{LOW}	2.7 V ≤ V_{DD} ≤ 5.5 V		4.7		4.7		4.7		μs
		1.8 V (2.4 V Note 3) ≤ V_{DD} ≤ 5.5 V		4.7		4.7		4.7		μs
		1.6 V ≤ V_{DD} ≤ 5.5 V		–	–	–	–	4.7		μs
Hold time when SCLA0 = "H"	t_{HIGH}	2.7 V ≤ V_{DD} ≤ 5.5 V		4.0		4.0		4.0		μs
		1.8 V (2.4 V Note 3) ≤ V_{DD} ≤ 5.5 V		4.0		4.0		4.0		μs
		1.6 V ≤ V_{DD} ≤ 5.5 V		–	–	–	–	4.0		μs

(**Notes**, **Caution** and **Remark** are listed on the next page.)

(1) I²C standard mode (2/2)

(T_A = –40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	$t_{SU:DAT}$	2.7 V ≤ V_{DD} ≤ 5.5 V	250		250		250		ns
		1.8 V (2.4 V Note 3) ≤ V_{DD} ≤ 5.5 V	250		250		250		ns
		1.6 V ≤ V_{DD} ≤ 5.5 V	–	–	–	–	250		ns
Data hold time (transmission) Note 2	$t_{HD:DAT}$	2.7 V ≤ V_{DD} ≤ 5.5 V	0	3.45	0	3.45	0	3.45	μs
		1.8 V (2.4 V Note 3) ≤ V_{DD} ≤ 5.5 V	0	3.45	0	3.45	0	3.45	μs
		1.6 V ≤ V_{DD} ≤ 5.5 V	–	–	–	–	0	3.45	μs
Setup time of stop condition	$t_{SU:STO}$	2.7 V ≤ V_{DD} ≤ 5.5 V	4.0		4.0		4.0		μs
		1.8 V (2.4 V Note 3) ≤ V_{DD} ≤ 5.5 V	4.0		4.0		4.0		μs
		1.6 V ≤ V_{DD} ≤ 5.5 V	–	–	–	–	4.0		μs
Bus-free time	t_{BUF}	2.7 V ≤ V_{DD} ≤ 5.5 V	4.7		4.7		4.7		μs
		1.8 V (2.4 V Note 3) ≤ V_{DD} ≤ 5.5 V	4.7		4.7		4.7		μs
		1.6 V ≤ V_{DD} ≤ 5.5 V	–	–	–	–	4.7		μs

Notes
1. The first clock pulse is generated after this period when the start/restart condition is detected.
2. The maximum value (MAX.) of $t_{HD:DAT}$ is during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.
3. Condition in HS (high-speed main) mode

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: C_b = 400 pF, R_b = 2.7 kΩ

(2) I^{2}C fast mode

(T_A = –40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f_{SCL}	Fast mode: f_{CLK} ≥ 3.5 MHz	2.7 V ≤ V_{DD} ≤ 5.5 V	0	400	0	400	0	400	kHz
			1.8 V (2.4 V Note 3) ≤ V_{DD} ≤ 5.5 V	0	400	0	400	0	400	kHz
Setup time of restart condition	$t_{SU:STA}$	2.7 V ≤ V_{DD} ≤ 5.5 V		0.6		0.6		0.6		μs
		1.8 V (2.4 V Note 3) ≤ V_{DD} ≤ 5.5 V		0.6		0.6		0.6		μs
Hold time Note 1	$t_{HD:STA}$	2.7 V ≤ V_{DD} ≤ 5.5 V		0.6		0.6		0.6		μs
		1.8 V (2.4 V Note 3) ≤ V_{DD} ≤ 5.5 V		0.6		0.6		0.6		μs
Hold time when SCLA0 ="L"	t_{LOW}	2.7 V ≤ V_{DD} ≤ 5.5 V		1.3		1.3		1.3		μs
		1.8 V (2.4 V Note 3) ≤ V_{DD} ≤ 5.5 V		1.3		1.3		1.3		μs
Hold time when SCLA0 ="H"	t_{HIGH}	2.7 V ≤ V_{DD} ≤ 5.5 V		0.6		0.6		0.6		μs
		1.8 V (2.4 V Note 3) ≤ V_{DD} ≤ 5.5 V		0.6		0.6		0.6		μs
Data setup time (reception)	$t_{SU:DAT}$	2.7 V ≤ V_{DD} ≤ 5.5 V		100		100		100		ns
		1.8 V (2.4 V Note 3) ≤ V_{DD} ≤ 5.5 V		100		100		100		ns
Data hold time (transmission) Note 2	$t_{HD:DAT}$	2.7 V ≤ V_{DD} ≤ 5.5 V		0	0.9	0	0.9	0	0.9	μs
		1.8 V (2.4 V Note 3) ≤ V_{DD} ≤ 5.5 V		0	0.9	0	0.9	0	0.9	μs
Setup time of stop condition	$t_{SU:STO}$	2.7 V ≤ V_{DD} ≤ 5.5 V		0.6		0.6		0.6		μs
		1.8 V (2.4 V Note 3) ≤ V_{DD} ≤ 5.5 V		0.6		0.6		0.6		μs
Bus-free time	t_{BUF}	2.7 V ≤ V_{DD} ≤ 5.5 V		1.3		1.3		1.3		μs
		1.8 V (2.4 V Note 3) ≤ V_{DD} ≤ 5.5 V		1.3		1.3		1.3		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of $t_{HD:DAT}$ is during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.

3. Condition in HS (high-speed main) mode

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode: C_b = 320 pF, R_b = 1.1 kΩ

(3) I²C fast mode plus

(T_A = –40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f_{SCL}	Fast mode plus: f_{CLK} ≥ 10 MHz	2.7 V ≤ V_{DD} ≤ 5.5 V	0	1000	–		–		kHz
Setup time of restart condition	$t_{SU:STA}$	2.7 V ≤ V_{DD} ≤ 5.5 V		0.26		–		–		μs
Hold time[Note 1]	$t_{HD:STA}$	2.7 V ≤ V_{DD} ≤ 5.5 V		0.26		–		–		μs
Hold time when SCLA0 ="L"	t_{LOW}	2.7 V ≤ V_{DD} ≤ 5.5 V		0.5		–		–		μs
Hold time when SCLA0 ="H"	t_{HIGH}	2.7 V ≤ V_{DD} ≤ 5.5 V		0.26		–		–		μs
Data setup time (reception)	$t_{SU:DAT}$	2.7 V ≤ V_{DD} ≤ 5.5 V		50		–		–		ns
Data hold time (transmission)[Note 2]	$t_{HD:DAT}$	2.7 V ≤ V_{DD} ≤ 5.5 V		0	0.45	–		–		μs
Setup time of stop condition	$t_{SU:STO}$	2.7 V ≤ V_{DD} ≤ 5.5 V		0.26		–		–		μs
Bus-free time	t_{BUF}	2.7 V ≤ V_{DD} ≤ 5.5 V		0.5		–		–		μs

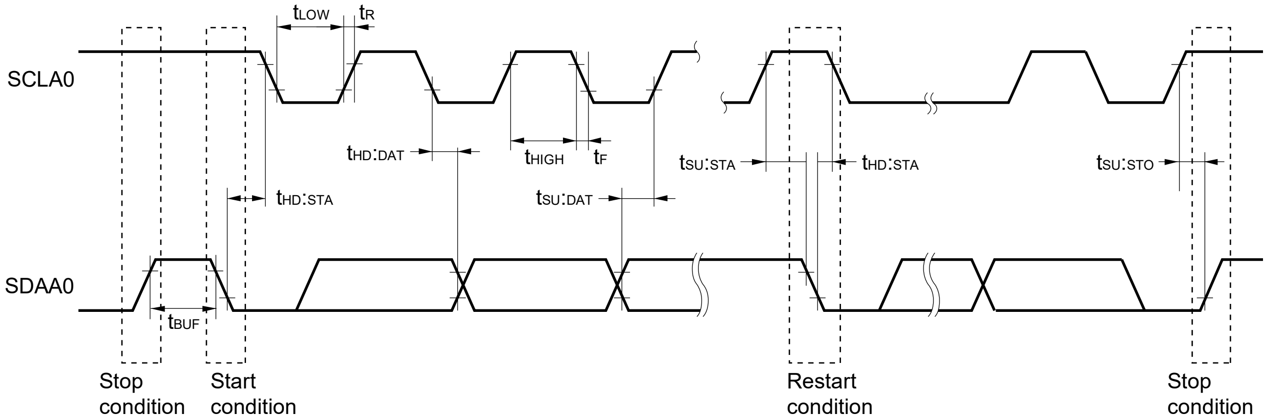
Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of $t_{HD:DAT}$ is during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode plus: C_b = 120 pF, R_b = 1.1 kΩ

IICA serial transfer timing



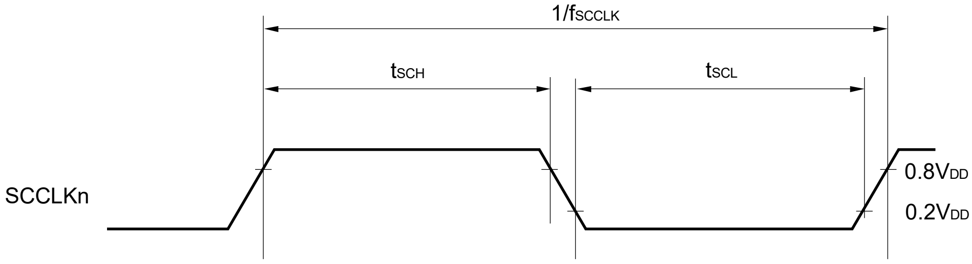
32.5.3 Smart card interface (SMCI)

(T_A = –40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCCLKn clock frequency	f_{SCCLK}	2.7 V ≤ V_{DD} ≤ 5.5 V	Complies with the ISO/IEC 7816-3 standards	6	Complies with the ISO/IEC 7816-3 standards	2	Complies with the ISO/IEC 7816-3 standards	1	MHz
		2.4 V ≤ V_{DD} ≤ 5.5 V		4		2		1	
		1.8 V ≤ V_{DD} ≤ 5.5 V		–		2		1	
		1.6 V ≤ V_{DD} ≤ 5.5 V		–	–	–		1	
SCCLKn high-/low-level width	t_{SCH}, t_{SCL}	4.0 V ≤ V_{DD} ≤ 5.5 V	1/(f_{SCCLK} × 2) – 12		1/(f_{SCCLK} × 2) – 50		1/(f_{SCCLK} × 2) – 50		ns
		2.7 V ≤ V_{DD} ≤ 5.5 V	1/(f_{SCCLK} × 2) – 18						
		2.4 V ≤ V_{DD} ≤ 5.5 V	1/(f_{SCCLK} × 2) – 38						
		1.8 V ≤ V_{DD} ≤ 5.5 V	–	–					
		1.6 V ≤ V_{DD} ≤ 5.5 V	–	–	–	–	1/(f_{SCCLK} × 2) – 100		

Remark n: Channel number (n = 0, 1)

SMCI timing



32.6 Analog Characteristics

32.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Reference Voltage / Input channel	Reference voltage (+) = AV_{REFP} Reference voltage (–) = AV_{REFM}	Reference voltage (+) = V_{DD} Reference voltage (–) = V_{SS}	Reference voltage (+) = V_{BGR} Reference voltage (–) = AV_{REFM}
ANI0, ANI1	–	See **32.6.1 (2)**.	See **32.6.1 (3)**.
ANI16, ANI17	See **32.6.1 (1)**.		
Internal reference voltage Temperature sensor output voltage	See **32.6.1 (1)**.		–

(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (–) = AV_{REFM}/ANI1 (ADREFM = 1), target pins: ANI16, ANI17, internal reference voltage, and temperature sensor output voltage

(T_A = –40 to +85°C, 1.6 V ≤ AV_{REFP} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (–) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error[Note 1]	AINL	10-bit resolution AV_{REFP} = V_{DD}[Note 3]	1.8 V ≤ AV_{REFP} ≤ 5.5 V		1.2	±5.0	LSB
			1.6 V ≤ AV_{REFP} ≤ 5.5 V[Note 4]		1.2	±8.5	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI16, ANI17	3.6 V ≤ V_{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
			1.6 V ≤ V_{DD} ≤ 5.5 V	57		95	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V_{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error[Notes 1, 2]	E_{ZS}	10-bit resolution AV_{REFP} = V_{DD}[Note 3]	1.8 V ≤ AV_{REFP} ≤ 5.5 V			±0.35	%FSR
			1.6 V ≤ AV_{REFP} ≤ 5.5 V[Note 4]			±0.60	%FSR
Full-scale error[Notes 1, 2]	E_{FS}	10-bit resolution AV_{REFP} = V_{DD}[Note 3]	1.8 V ≤ AV_{REFP} ≤ 5.5 V			±0.35	%FSR
			1.6 V ≤ AV_{REFP} ≤ 5.5 V[Note 4]			±0.60	%FSR
Integral linearity error[Note 1]	ILE	10-bit resolution AV_{REFP} = V_{DD}[Note 3]	1.8 V ≤ AV_{REFP} ≤ 5.5 V			±3.5	LSB
			1.6 V ≤ AV_{REFP} ≤ 5.5 V[Note 4]			±6.0	LSB
Differential linearity error[Note 1]	DLE	10-bit resolution AV_{REFP} = V_{DD}[Note 3]	1.8 V ≤ AV_{REFP} ≤ 5.5 V			±2.0	LSB
			1.6 V ≤ AV_{REFP} ≤ 5.5 V[Note 4]			±2.5	LSB
Analog input voltage	V_{AIN}	ANI16, ANI17		0		AV_{REFP}	V
		Internal reference voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode))		V_{BGR}[Note 5]			V
		Temperature sensor output voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode))		V_{TMPS25}[Note 5]			V

(**Notes** are listed on the next page.)

Notes **1.** Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When AV_{REFP} < V_{DD}, the MAX. values are as follows.

Overall error:	Add ±4 LSB to the MAX. value when AV_{REFP} = V_{DD}.
Zero-scale error/Full-scale error:	Add ±0.2%FSR to the MAX. value when AV_{REFP} = V_{DD}.
Integral linearity error/ Differential linearity error:	Add ±2 LSB to the MAX. value when AV_{REFP} = V_{DD}.

4. Values when the conversion time is set to 57 μs (min.) and 95 μs (max.).

5. See **32.6.2 Temperature sensor/internal reference voltage characteristics**.

(2) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (–) = V_{SS} (ADREFM = 0), target pins: ANI0, ANI1, ANI16, ANI17, internal reference voltage, and temperature sensor output voltage

(T_A = –40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = V_{DD}, Reference voltage (–) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error[Notes 1, 2]	AINL	10-bit resolution	1.8 V ≤ V_{DD} ≤ 5.5 V		1.2	±7.0	LSB
			1.6 V ≤ V_{DD} ≤ 5.5 V[Note 3]		1.2	±10.5	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI0, ANI1, ANI16, ANI17[Note 3]	3.6 V ≤ V_{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
			1.6 V ≤ V_{DD} ≤ 5.5 V	57		95	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V_{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error[Notes 1, 2]	E_{ZS}	10-bit resolution	1.8 V ≤ V_{DD} ≤ 5.5 V			±0.60	%FSR
			1.6 V ≤ V_{DD} ≤ 5.5 V[Note 3]			±0.85	%FSR
Full-scale error[Notes 1, 2]	E_{FS}	10-bit resolution	1.8 V ≤ V_{DD} ≤ 5.5 V			±0.60	%FSR
			1.6 V ≤ V_{DD} ≤ 5.5 V[Note 3]			±0.85	%FSR
Integral linearity error[Note 1]	ILE	10-bit resolution	1.8 V ≤ V_{DD} ≤ 5.5 V			±4.0	LSB
			1.6 V ≤ V_{DD} ≤ 5.5 V[Note 3]			±6.5	LSB
Differential linearity error[Note 1]	DLE	10-bit resolution	1.8 V ≤ V_{DD} ≤ 5.5 V			±2.0	LSB
			1.6 V ≤ V_{DD} ≤ 5.5 V[Note 3]			±2.5	LSB
Analog input voltage	V_{AIN}	ANI0, ANI1, ANI16, ANI17		0		V_{DD}	V
		Internal reference voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode))		V_{BGR}[Note 4]			V
		Temperature sensor output voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode))		V_{TMPS25}[Note 4]			V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Values when the conversion time is set to 57 μs (min.) and 95 μs (max.).

4. See **32.6.2 Temperature sensor/internal reference voltage characteristics**.

(3) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (–) = AVREFM/ANI1 (ADREFM = 1), target pins: ANI0, ANI16, ANI17

(T_A = –40 to +85°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = V_{BGR} Note 3, Reference voltage (–) = AV_{REFM} Note 4 = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES				8		bit
Conversion time	t_{CONV}	8-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error Notes 1, 2	E_{ZS}	8-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±0.60	%FSR
Integral linearity error Note 1	ILE	8-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	2.4 V ≤ V_{DD} ≤ 5.5 V			±1.0	LSB
Analog input voltage	V_{AIN}			0		V_{BGR} Note 3	V

Notes 1. Excludes quantization error (±1/2 LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. See **32.6.2 Temperature sensor/internal reference voltage characteristics**.

4. When reference voltage (–) = V_{SS}, the MAX. values are as follows.

Zero-scale error: Add ±0.35%FSR to the AV_{REFM} MAX. value.

Integral linearity error: Add ±0.5 LSB to the AV_{REFM} MAX. value.

Differential linearity error: Add ±0.2 LSB to the AV_{REFM} MAX. value.

32.6.2 Temperature sensor/internal reference voltage characteristics

(T_A = –40 to +85°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V_{TMPS25}	ADS register = 80H, T_A = +25°C		1.05		V
Internal reference output voltage	V_{BGR}	ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	F_{VTMPS}	Temperature sensor that depends on the temperature		–3.6		mV/°C
Operation stabilization wait time	t_{AMP}		5			μs

32.6.3 Comparator characteristics

(T_A = –40 to +85°C, 1.6 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage range	Ivref			0		V_{DD} – 1.4	V
	Ivcmp			–0.3		V_{DD} + 0.3	V
Output delay	td	V_{DD} = 3.0 V Input slew rate > 50 mV/μs	Comparator high-speed mode, standard mode			1.2	μs
			Comparator high-speed mode, window mode			2.0	μs
			Comparator low-speed mode, standard mode		3.0	5.0	μs
High-electric-potential reference voltage	VTW+	Comparator high-speed mode, window mode		0.66V_{DD}	0.76V_{DD}	0.86V_{DD}	V
Low-electric-potential reference voltage	VTW–	Comparator high-speed mode, window mode		0.14V_{DD}	0.24V_{DD}	0.34V_{DD}	V
Operation stabilization wait time	t_{CMP}			100			μs
Internal reference output voltage[Note]	V_{BGR}	2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode		1.38	1.45	1.50	V

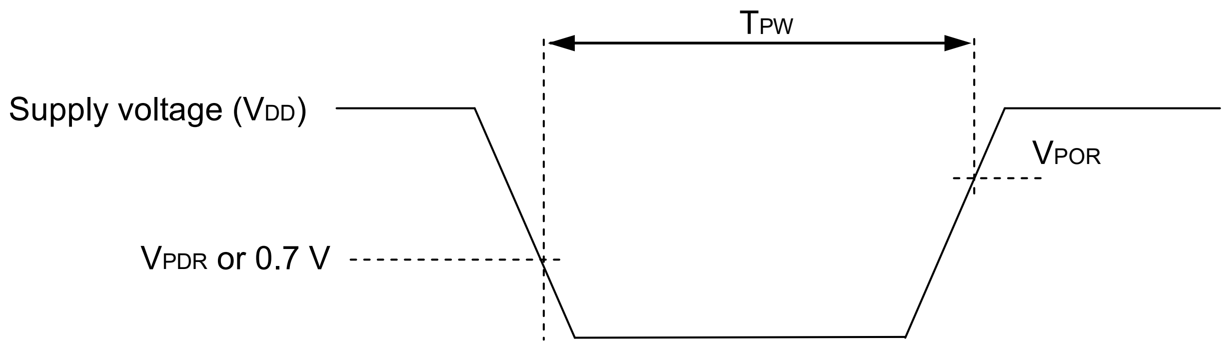
Note Cannot be used in LS (low-speed main) mode, LV (low-voltage main) mode, subsystem clock operation, and STOP mode.

32.6.4 POR circuit characteristics

(T_A = –40 to +85°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V_{POR}	When power supply rises	1.47	1.51	1.55	V
	V_{PDR}	When power supply falls	1.46	1.50	1.54	V
Minimum pulse width[Note]	T_{PW}		300			μs

Note This is the time required for the POR circuit to execute a reset operation when V_{DD} falls below V_{PDR}. When the microcontroller enters STOP mode and when the main system clock (f_{MAIN}) has been stopped by setting bit 0 (HIOSTOP) and bit 7 (MSTOP) of the clock operation status control register (CSC), this is the time required for the POR circuit to execute a reset operation between when V_{DD} falls below 0.7 V and when V_{DD} rises to V_{POR} or higher.



32.6.5 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

(T_A = –40 to +85°C, V_{PDR} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	Supply voltage level	V_{LVD0}	When power supply rises	3.98	4.06	4.14	V
			When power supply falls	3.90	3.98	4.06	V
		V_{LVD1}	When power supply rises	3.68	3.75	3.82	V
			When power supply falls	3.60	3.67	3.74	V
		V_{LVD2}	When power supply rises	3.07	3.13	3.19	V
			When power supply falls	3.00	3.06	3.12	V
		V_{LVD3}	When power supply rises	2.96	3.02	3.08	V
			When power supply falls	2.90	2.96	3.02	V
		V_{LVD4}	When power supply rises	2.86	2.92	2.97	V
			When power supply falls	2.80	2.86	2.91	V
		V_{LVD5}	When power supply rises	2.76	2.81	2.87	V
			When power supply falls	2.70	2.75	2.81	V
		V_{LVD6}	When power supply rises	2.66	2.71	2.76	V
			When power supply falls	2.60	2.65	2.70	V
		V_{LVD7}	When power supply rises	2.56	2.61	2.66	V
			When power supply falls	2.50	2.55	2.60	V
		V_{LVD8}	When power supply rises	2.45	2.50	2.55	V
			When power supply falls	2.40	2.45	2.50	V
		V_{LVD9}	When power supply rises	2.05	2.09	2.13	V
			When power supply falls	2.00	2.04	2.08	V
		V_{LVD10}	When power supply rises	1.94	1.98	2.02	V
			When power supply falls	1.90	1.94	1.98	V
		V_{LVD11}	When power supply rises	1.84	1.88	1.91	V
			When power supply falls	1.80	1.84	1.87	V
		V_{LVD12}	When power supply rises	1.74	1.77	1.81	V
			When power supply falls	1.70	1.73	1.77	V
		V_{LVD13}	When power supply rises	1.64	1.67	1.70	V
			When power supply falls	1.60	1.63	1.66	V
Minimum pulse width		t_{LW}		300			μs
Detection delay time						300	μs

LVD Detection Voltage of Interrupt & Reset Mode

(T_A = –40 to +85°C, V_{PDR} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Interrupt and reset mode	V_{LVD13}	V_{POC2}, V_{POC1}, V_{POC0} = 0, 0, 0, falling reset voltage			1.60	1.63	1.66	V
	V_{LVD12}		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.74	1.77	1.81	V
				Falling interrupt voltage	1.70	1.73	1.77	V
	V_{LVD11}		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	1.84	1.88	1.91	V
				Falling interrupt voltage	1.80	1.84	1.87	V
	V_{LVD4}		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	V_{LVD11}	V_{POC2}, V_{POC1}, V_{POC0} = 0, 0, 1, falling reset voltage			1.80	1.84	1.87	V
	V_{LVD10}		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.94	1.98	2.02	V
				Falling interrupt voltage	1.90	1.94	1.98	V
	V_{LVD9}		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.05	2.09	2.13	V
				Falling interrupt voltage	2.00	2.04	2.08	V
	V_{LVD2}		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.07	3.13	3.19	V
				Falling interrupt voltage	3.00	3.06	3.12	V
	V_{LVD8}	V_{POC2}, V_{POC1}, V_{POC0} = 0, 1, 0, falling reset voltage			2.40	2.45	2.50	V
	V_{LVD7}		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.56	2.61	2.66	V
				Falling interrupt voltage	2.50	2.55	2.60	V
	V_{LVD6}		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.66	2.71	2.76	V
				Falling interrupt voltage	2.60	2.65	2.70	V
	V_{LVD1}		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.68	3.75	3.82	V
				Falling interrupt voltage	3.60	3.67	3.74	V
	V_{LVD5}	V_{POC2}, V_{POC1}, V_{POC0} = 0, 1, 1, falling reset voltage			2.70	2.75	2.81	V
	V_{LVD4}		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	V_{LVD3}		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.96	3.02	3.08	V
				Falling interrupt voltage	2.90	2.96	3.02	V
	V_{LVD0}		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.98	4.06	4.14	V
				Falling interrupt voltage	3.90	3.98	4.06	V

32.6.6 Supply voltage rising slope characteristics

(T_A = –40 to +85°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
V_{DD} rising slope	SV_{DD}				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 32.4 AC Characteristics.

32.7 LCD Characteristics

32.7.1 External resistance division method

(1) Static display mode

(T_A = –40 to +85°C, V_{L4} (MIN.) ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	V_{L4}		2.0		V_{DD}	V

(2) 1/2 bias method, 1/4 bias method

(T_A = –40 to +85°C, V_{L4} (MIN.) ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	V_{L4}		2.7		V_{DD}	V

(3) 1/3 bias method

(T_A = –40 to +85°C, V_{L4} (MIN.) ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
LCD drive voltage	V_{L4}		2.5		V_{DD}	V

32.7.2 Internal voltage boosting method

(1) 1/3 bias method

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
LCD output voltage variation range	V_{L1}	C1 to C4 Note 1 = 0.47 μF Note 2	VLCD = 04H	0.90	1.00	1.08	V
			VLCD = 05H	0.95	1.05	1.13	V
			VLCD = 06H	1.00	1.10	1.18	V
			VLCD = 07H	1.05	1.15	1.23	V
			VLCD = 08H	1.10	1.20	1.28	V
			VLCD = 09H	1.15	1.25	1.33	V
			VLCD = 0AH	1.20	1.30	1.38	V
			VLCD = 0BH	1.25	1.35	1.43	V
			VLCD = 0CH	1.30	1.40	1.48	V
			VLCD = 0DH	1.35	1.45	1.53	V
			VLCD = 0EH	1.40	1.50	1.58	V
			VLCD = 0FH	1.45	1.55	1.63	V
			VLCD = 10H	1.50	1.60	1.68	V
			VLCD = 11H	1.55	1.65	1.73	V
			VLCD = 12H	1.60	1.70	1.78	V
			VLCD = 13H	1.65	1.75	1.83	V
Doubler output voltage	V_{L2}	C1 to C4 Note 1 = 0.47 μF		2 V_{L1} – 0.10	2 V_{L1}	2 V_{L1}	V
<R> Tripler output voltage	V_{L4}	C1 to C4 Note 1 = 0.47 μF		3 V_{L1} – 0.15	3 V_{L1}	3 V_{L1}	V
Reference voltage setup time Note 2	t_{VWAIT1}			5			ms
Voltage boost wait time Note 3	t_{VWAIT2}	C1 to C4 Note 1 = 0.47 μF		500			ms

Notes 1. This is a capacitor that is connected between voltage pins used to drive the LCD.

C1: A capacitor connected between CAPH and CAPL

C2: A capacitor connected between V_{L1} and GND

C3: A capacitor connected between V_{L2} and GND

C4: A capacitor connected between V_{L4} and GND

C1 = C2 = C3 = C4 = 0.47 μF ± 30 %

2. This is the time required to wait from when the reference voltage is specified by using the VLCD register (or when the internal voltage boosting method is selected (by setting the MDSET1 and MDSET0 bits of the LCDM0 register to 01B) if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).

3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).

(2) 1/4 bias method

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
LCD output voltage variation range	V_{L1}	C1 to C5[Note 1] = 0.47 µF[Note 2]	VLCD = 04H	0.90	1.00	1.08	V
			VLCD = 05H	0.95	1.05	1.13	V
			VLCD = 06H	1.00	1.10	1.18	V
			VLCD = 07H	1.05	1.15	1.23	V
			VLCD = 08H	1.10	1.20	1.28	V
			VLCD = 09H	1.15	1.25	1.33	V
			VLCD = 0AH	1.20	1.30	1.38	V
Doubler output voltage	V_{L2}	C1 to C5[Note 1] = 0.47 µF		2 V_{L1}–0.08	2 V_{L1}	2 V_{L1}	V
Tripler output voltage	V_{L3}	C1 to C5[Note 1] = 0.47 µF		3 V_{L1}–0.12	3 V_{L1}	3 V_{L1}	V
Quadruply output voltage	V_{L4}	C1 to C5[Note 1] = 0.47 µF		4 V_{L1}–0.16	4 V_{L1}	4 V_{L1}	V
Reference voltage setup time[Note 2]	t_{VWAIT1}			5			ms
Voltage boost wait time[Note 3]	t_{VWAIT2}	C1 to C5[Note 1] = 0.47 µF		500			ms

Notes 1. This is a capacitor that is connected between voltage pins used to drive the LCD.
C1: A capacitor connected between CAPH and CAPL
C2: A capacitor connected between V_{L1} and GND
C3: A capacitor connected between V_{L2} and GND
C4: A capacitor connected between V_{L3} and GND
C5: A capacitor connected between V_{L4} and GND
C1 = C2 = C3 = C4 = C5 = 0.47 µF ± 30%

2. This is the time required to wait from when the reference voltage is specified by using the VLCD register (or when the internal voltage boosting method is selected (by setting the MDSET1 and MDSET0 bits of the LCDM0 register to 01B) if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).

3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).

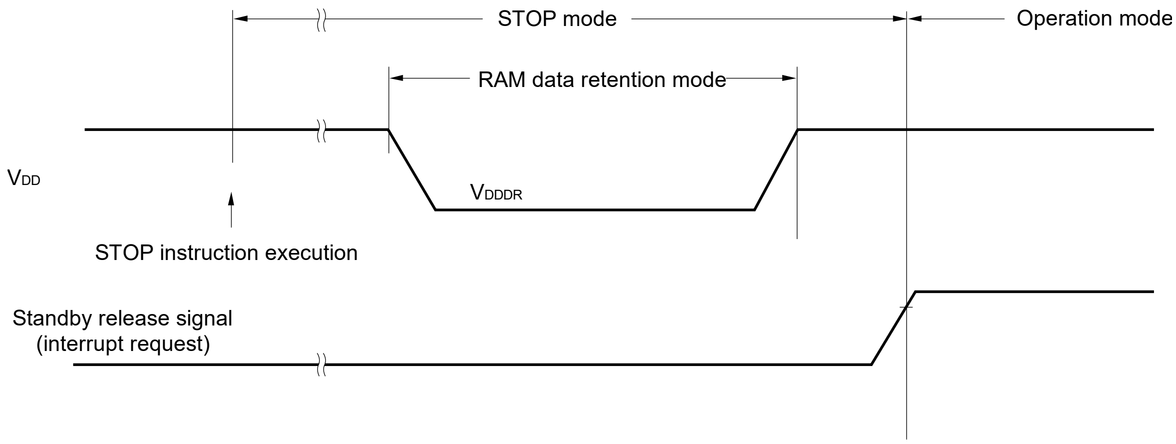
32.8 RAM Data Retention Characteristics

(T_A = –40 to +85°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.46[Note]		5.5	V

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.

Caution Data in RAM are not retained if the CPU operates outside the specified operating voltage range. Therefore, place the CPU in STOP mode before the operating voltage drops below the specified range.



32.9 Flash Memory Programming Characteristics

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	f_{CLK}	1.8 V ≤ V_{DD} ≤ 5.5 V	1		24	MHz
Number of flash rewrites[Notes 1, 2, 3]	C_{erwr}	Retained for 20 years T_A = 85°C	1,000			Times

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

2. When using flash memory programmer and Renesas Electronics self programming library

3. This characteristic indicates the flash memory characteristic and based on Renesas Electronics reliability test.

Remark When updating data multiple times, use the flash memory as one for updating data.

32.10 Dedicated Flash Memory Programmer Communication (UART)

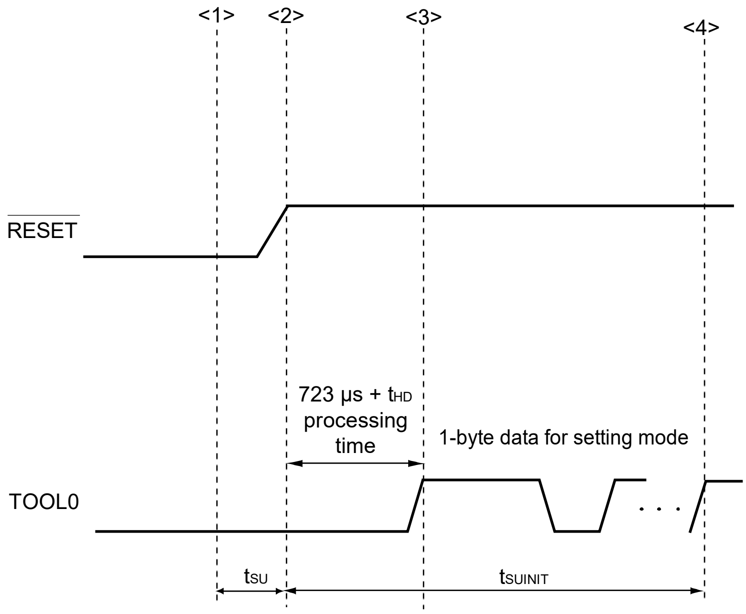
(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

32.11 Timing of Entry to Flash Memory Programming Modes

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	t_{SUINIT}	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	t_{SU}	POR and LVD reset must be released before the external reset is released.	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	t_{HD}	POR and LVD reset must be released before the external reset is released.	1			ms



<1> The low level is input to the TOOL0 pin.

<2> The external reset is released (POR and LVD reset must be released before the external reset is released.).

<3> The TOOL0 pin is set to the high level.

<4> Setting of the flash memory programming mode by UART reception and completion the baud rate setting.

Remark t_{SUINIT}: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

t_{SU}: Time to release the external reset after the TOOL0 pin is set to the low level

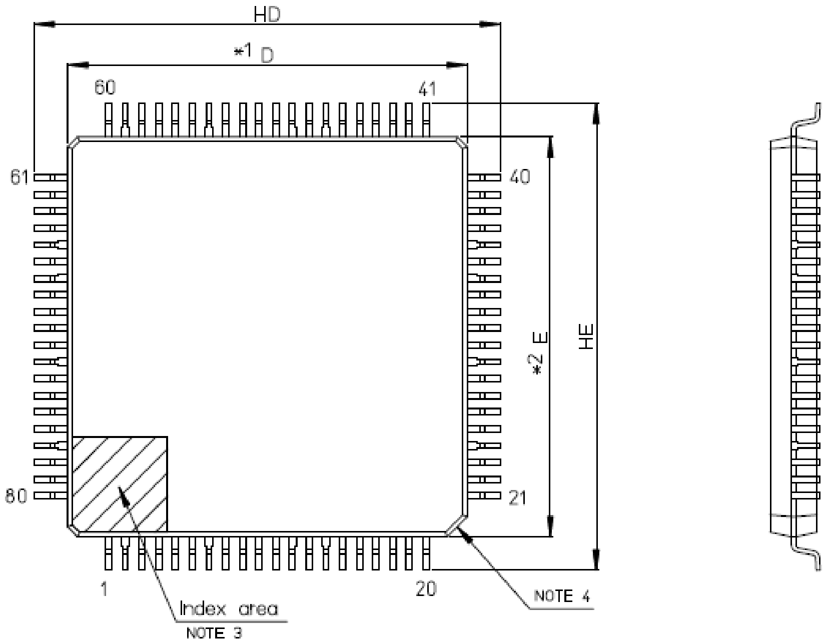
t_{HD}: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

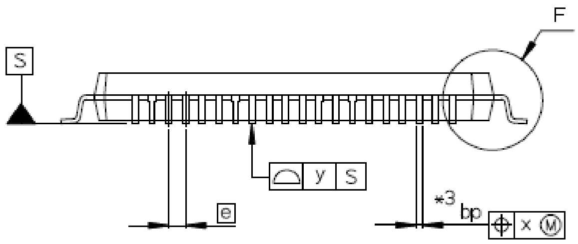
CHAPTER 33 PACKAGE DRAWINGS

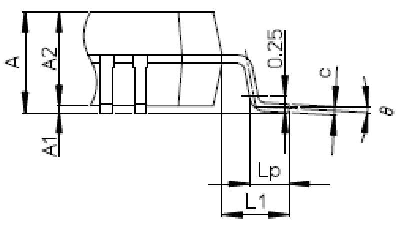
R7F0C020M2DFB

<R>

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP80-12x12-0.50	PLQP0080KB-B	—	0.5







Detail F

NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.
3. PIN 1 VISUAL INDEX FEATURE MAY VARY, BUT MUST BE LOCATED WITHIN THE HATCHED AREA.
4. CHAMFERS AT CORNERS ARE OPTIONAL; SIZE MAY VARY.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	11.9	12.0	12.1
E	11.9	12.0	12.1
A2	—	1.4	—
HD	13.8	14.0	14.2
HE	13.8	14.0	14.2
A	—	—	1.7
A1	0.05	—	0.15
bp	0.15	0.20	0.27
c	0.09	—	0.20
θ	0°	3.5°	8°
e	—	0.5	—
x	—	—	0.08
y	—	—	0.08
Lp	0.45	0.6	0.75
L1	—	1.0	—

APPENDIX A REVISION HISTORY

A.1 Major Revisions in This Edition

(1/1)

Page	Description	Classification
ALL		
	Modification of CSI to Simplified SPI (CSI)	(c)
	Modification of wait of IICA to clock stretch	(c)
CHAPTER 1 OUTLINE		
p.2	Addition of Notes 1 in **1.1 Features**	(c)
p.2	Modification of Notes 1 to Notes 2	(c)
p.2	Modification of Notes 2 to Notes 3	(c)
p.4	Modification of **Figure 1-1. Part Number, Memory Size, and Package**	(d)
p.4	Modification of **Table 1-1. List of Ordering Part Numbers**	(d)
CHAPTER 32 ELECTRICAL SPECIFICATIONS		
p.74	Modification of Notes 1 and 4 in **32.3.2 Supply current characteristics**	(c)
p.76	Modification of Notes 1 and 5 in **32.3.2 Supply current characteristics**	(c)
p.76	Deletion of Notes 6 in **32.3.2 Supply current characteristics**	(c)
p.120	Modification of **32.7.2 Internal voltage boosting method**	(a)
CHAPTER 33 PACKAGE DRAWINGS		
p.124	Addition of PLQP0080KB-B	(d)

Remark "Classification" in the above table classifies revisions as follows.
(a): Error correction, (b): Addition/change of specifications, (c): Addition/change of description or note, (d): Addition/change of package, part number, or management division, (e): Addition/change of related documents

A.2 Revision History of Preceding Editions

Here is the revision history of the preceding editions. Chapter indicates the chapter of each edition.

Edition	Description	Chapter
Rev.1.00	Modification of **32.3.2 Supply current characteristics**	**CHAPTER 32 ELECTRICAL SPECIFICATIONS**
Rev.0.50	First Edition issued	Throughout

R7F0C020M2DFB User's Manual: Hardware

Publication Date: Rev.0.50 Jul 26, 2017
Rev.1.10 Jul 31, 2024

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R7F0C020M2DFB

Renesas Electronics Corporation